S71JL128HC0/128HB0/064HB0/ 064HA0/064H80

Stacked Multi-Chip Product (MCP) Flash Memory and pSRAM CMOS 3.0 Volt-only, Simultaneous Operation Flash Memories and Static RAM/Pseudo-static RAM

PRELIMINARY

DISTINCTIVE CHARACTERISTICS

MCP Features

- **Operating Voltage Range of 2.7 to 3.3 V**
- **High Performance**
  - Access time as fast as 55 ns
- **Packages**
  - 73-ball FBGA—8 x 11.6 mm
  - 88-ball FBGA—8 x 11.6 mm
- **Operating Temperatures**
  - Wireless: –25°C to +85°C
  - Industrial: –40°C to +85°C

GENERAL DESCRIPTION

The S71JLxxxH Series is a product line of stacked Multi-Chip Products (MCP) and consists of

- **One or more S29JL064H Flash devices**
- **SRAM or pSRAM options**
  - 8Mb x 8/x 16 SRAM
  - 16Mb x 16-only SRAM
  - pSRAM x 16 only:
    8Mb pSRAM
    16Mb pSRAM
    32Mb pSRAM
    64Mb pSRAM

The products covered by this document are listed below. For details about their specifications, please refer to the individual constituent data sheets for further details.

MCP	Number of S29JL064H	Total Flash Density	SRAM/pSRAM Density
S71JL064H80	1	64Mb	8Mb
S71JL064HA0	1	64Mb	16Mb
S71JL064HB0	1	64Mb	32Mb
S71JL128HB0	2	128Mb	32Mb
S71JL128HC0	2	128Mb	64Mb

Notes:

1. *This MCP is only guaranteed to operate @ 2.7 - 3.3 V regardless of component operating ranges.*
2. *BYTE# operation is only supported on the S71JL064H80xx0x.*

Product Selector Guide

Device-Model #	SRAM/pSRAM Density	SRAM/pSRAM Type	Supplier	Flash Access Time (ns)	RAM Access Time (ns)	Packages
S71JL064H80Bxx01	8Mb	SRAM - x8/x16	Supplier 1	70	70	FLB073
S71JL064H80Bxx02	8Mb	SRAM - x8/x16	Supplier 1	85	85	FLB073
S71JL064H80Bxx10	8Mb	pSRAM - x16	Supplier 2	55	55	FLJ073
S71JL064H80Bxx11	8Mb	pSRAM - x16	Supplier 2	70	70	FLJ073
S71JL064H80Bxx12	8Mb	pSRAM - x16	Supplier 2	85	85	FLJ073
S71JL064HA0Bxx01	16Mb	SRAM - x16	Supplier 1	70	70	FLB073
S71JL064HA0Bxx02	16Mb	SRAM - x16	Supplier 1	85	85	FLB073
S71JL064HA0Bxx10	16Mb	pSRAM - x16	Supplier 2	55	55	FLJ073
S71JL064HA0Bxx11	16Mb	pSRAM - x16	Supplier 2	70	70	FLJ073
S71JL064HA0Bxx12	16Mb	pSRAM - x16	Supplier 2	85	85	FLJ073
S71JL064HA0Bxx62	16Mb	pSRAM - x16	Supplier 4	70	70	FLJ073
S71JL128HB0Bxx01	32Mb	pSRAM - x16	Supplier 3	70	70	FTA073
S71JL128HB0Bxx02	32Mb	pSRAM - x16	Supplier 3	85	85	FTA073
S71JL128HC0Bxx01	64Mb	pSRAM - x16	Supplier 3	70	70	FTA088
S71JL128HC0Bxx02	64Mb	pSRAM - x16	Supplier 3	85	85	FTA088

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S71JLI28HC0/I28HB0/064HB0/064HA0/064H80

S29JL064H

8 Mb SRAM (supplier I)

16 Mb SRAM (supplier I)

8 Mb pSRAM (supplier 2)

16 Mb pSRAM (supplier 2)

16 Mb pSRAM (supplier 4)

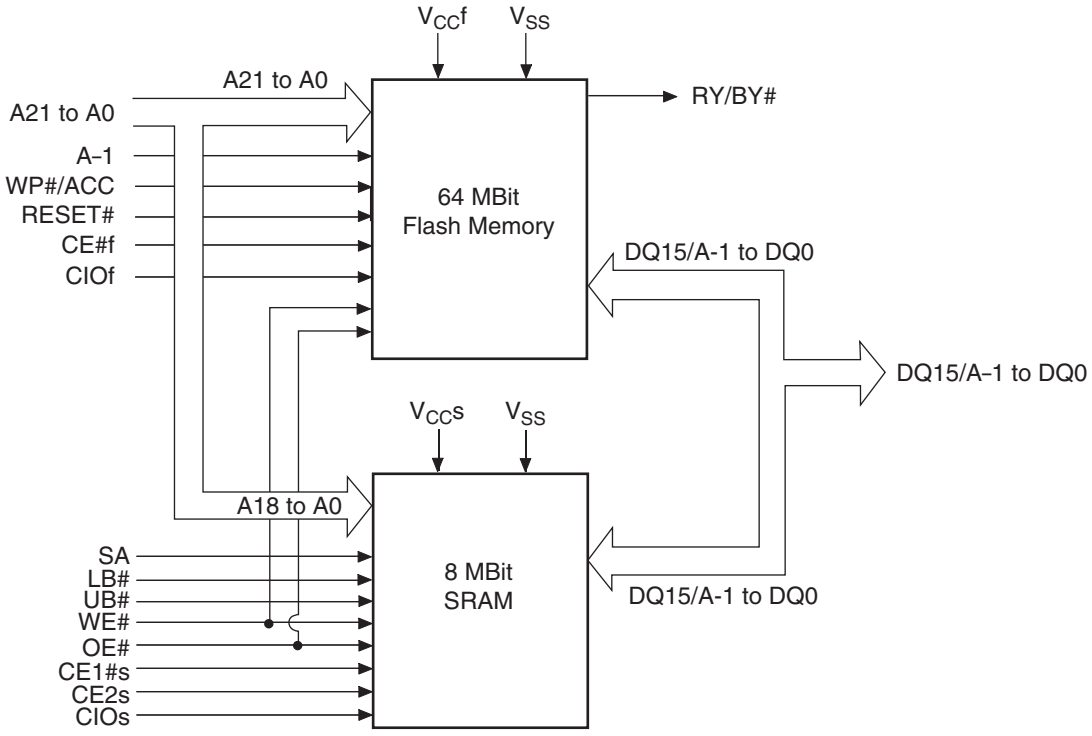
32 Mb pSRAM (Supplier 3)

64 Mb pSRAM (supplier 3)

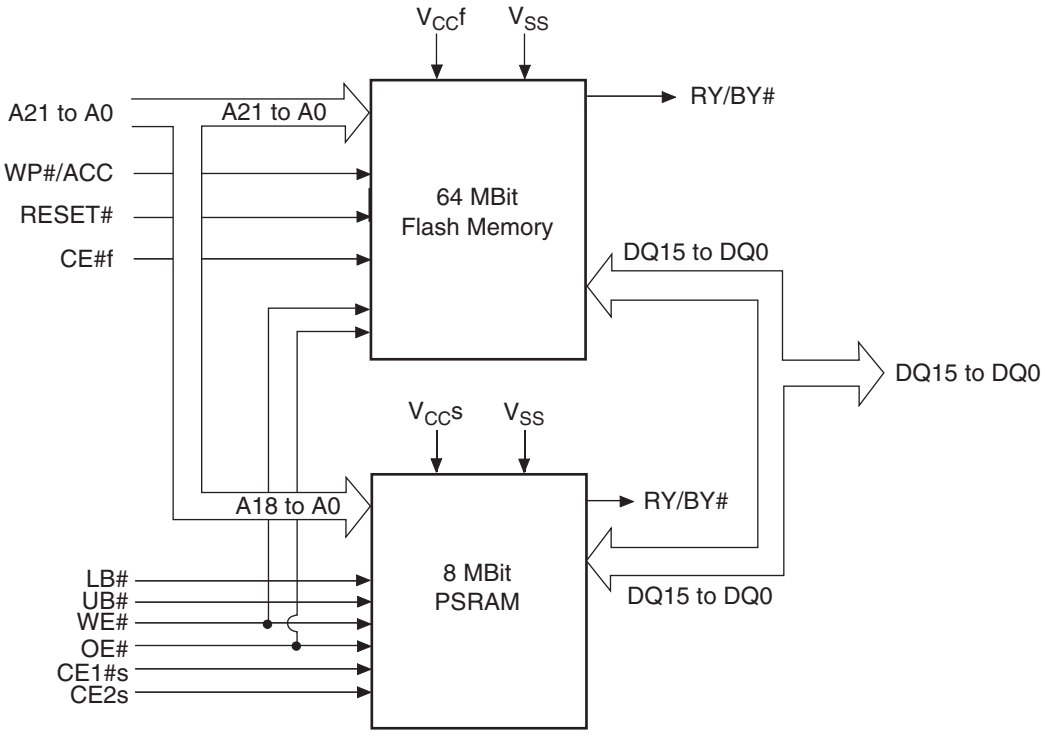
Revision Summary

Block Diagrams

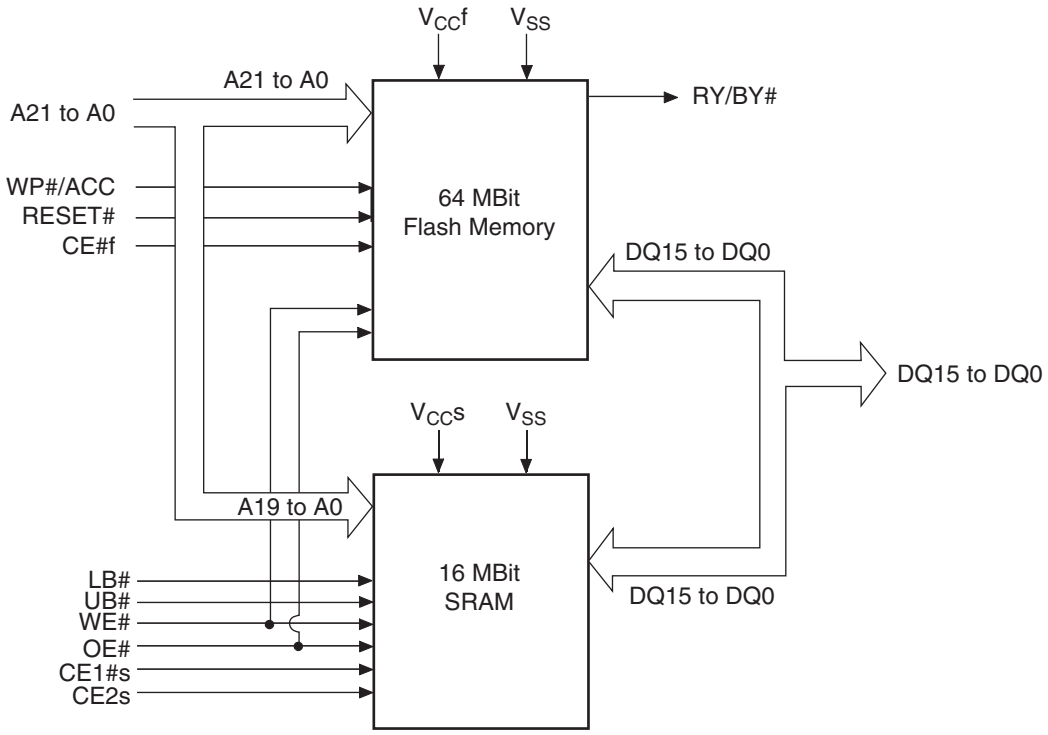
MCP Block Diagram of S71JL064H80, Model Numbers 0I/02



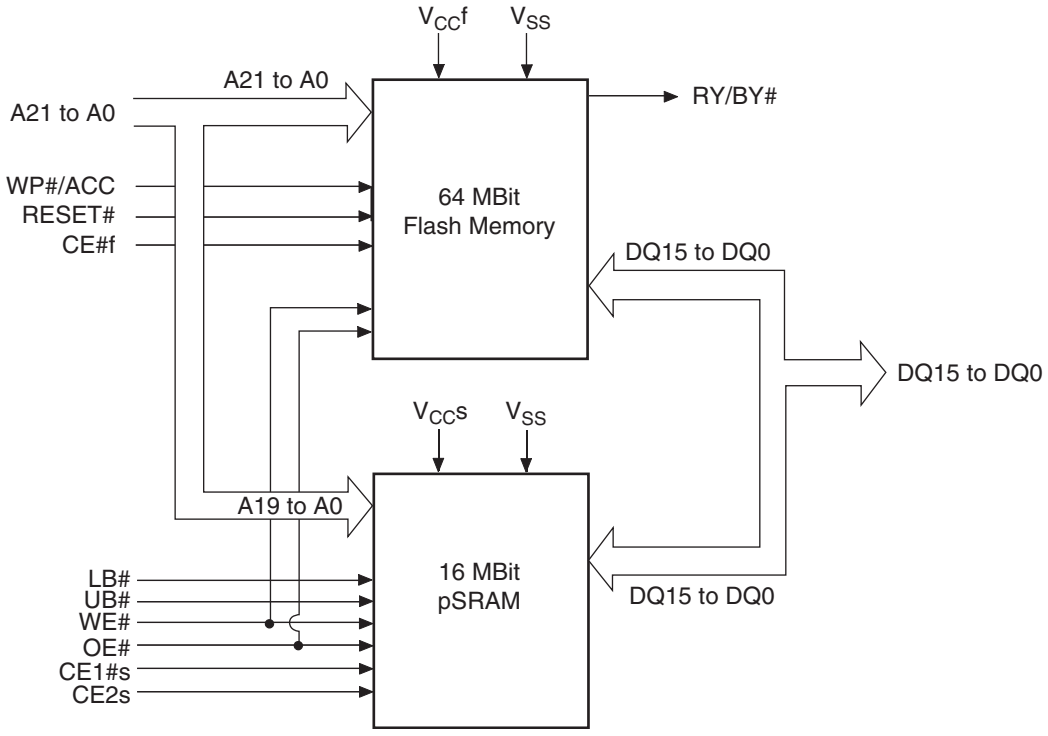
MCP Block Diagram of S71JL064H80, Model Numbers I0/I1/I2



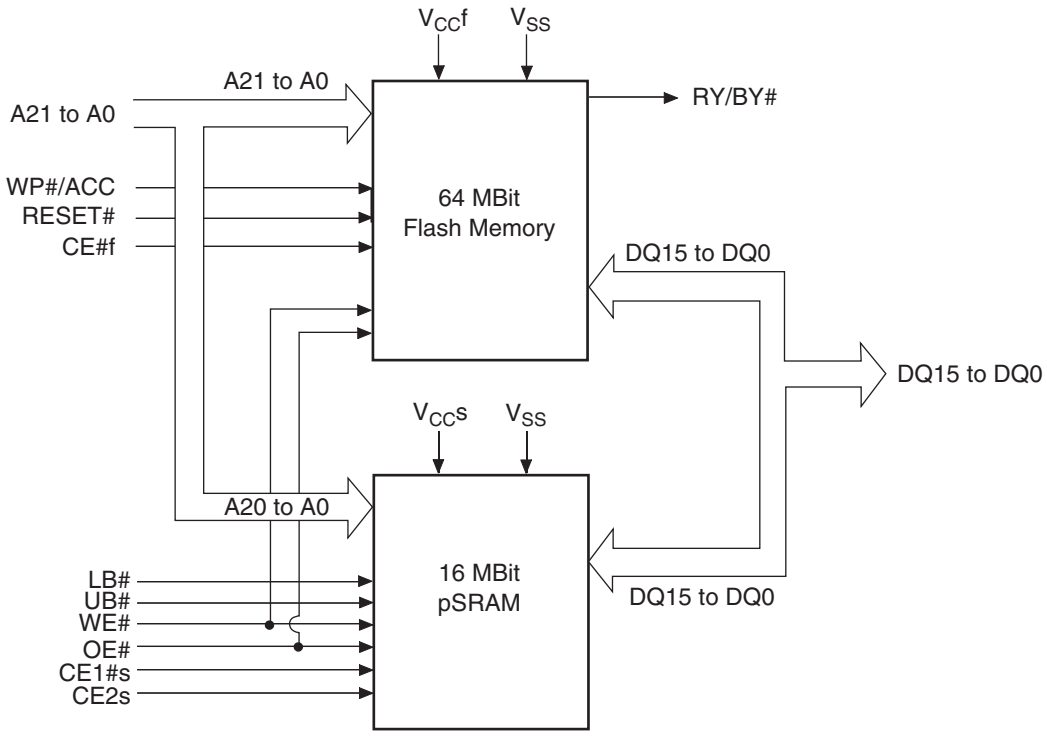
MCP Block Diagram of S71JL064HA0, Model Numbers 01/02



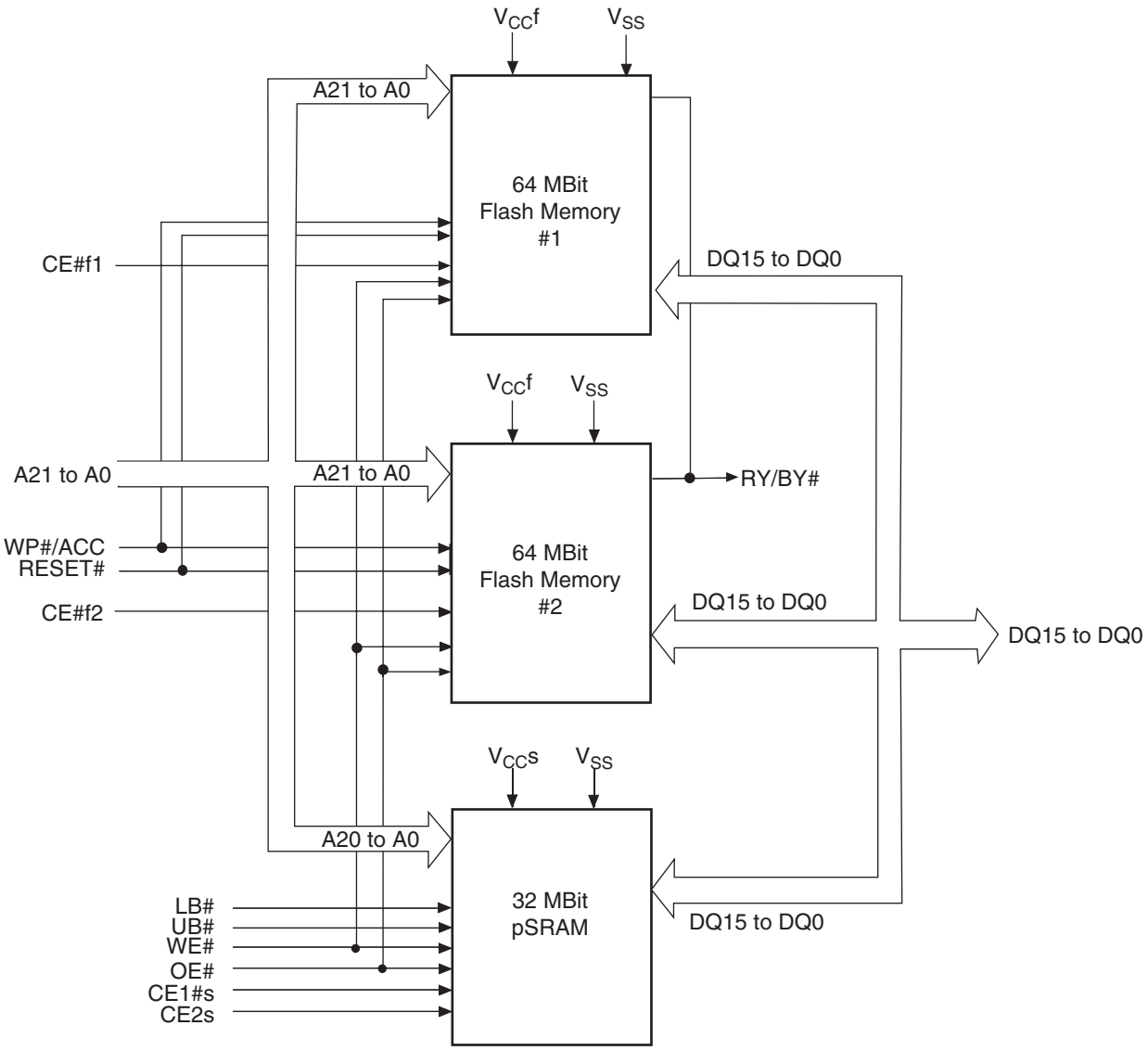
MCP Block Diagram of S71JL064HA0, Model Numbers 10/11/12/62



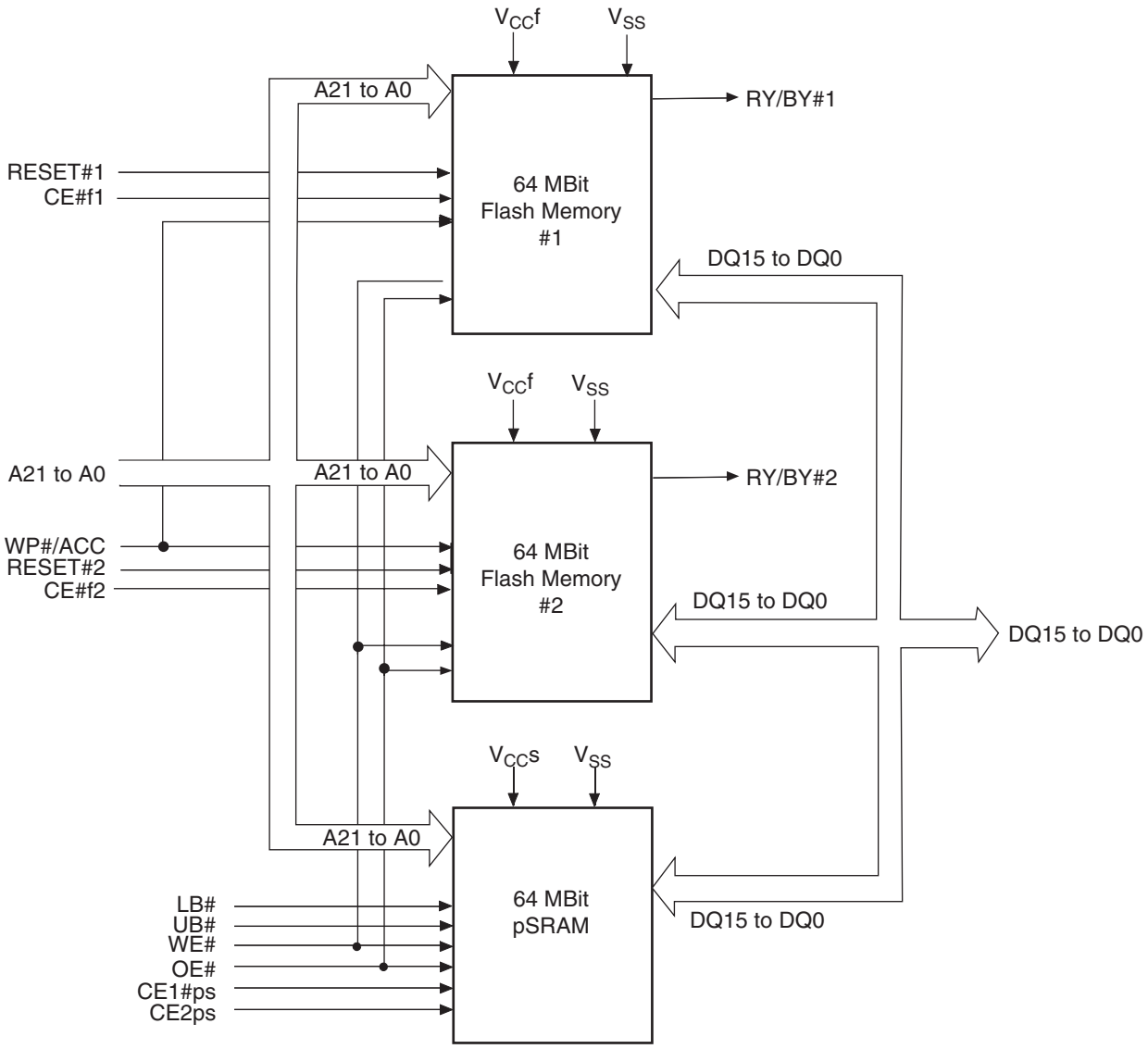
MCP Block Diagram of S71JL064HB0, Model Numbers 00/0I/02



MCP Block Diagram of S71JLI28HB0, Model Numbers 00/0I/02



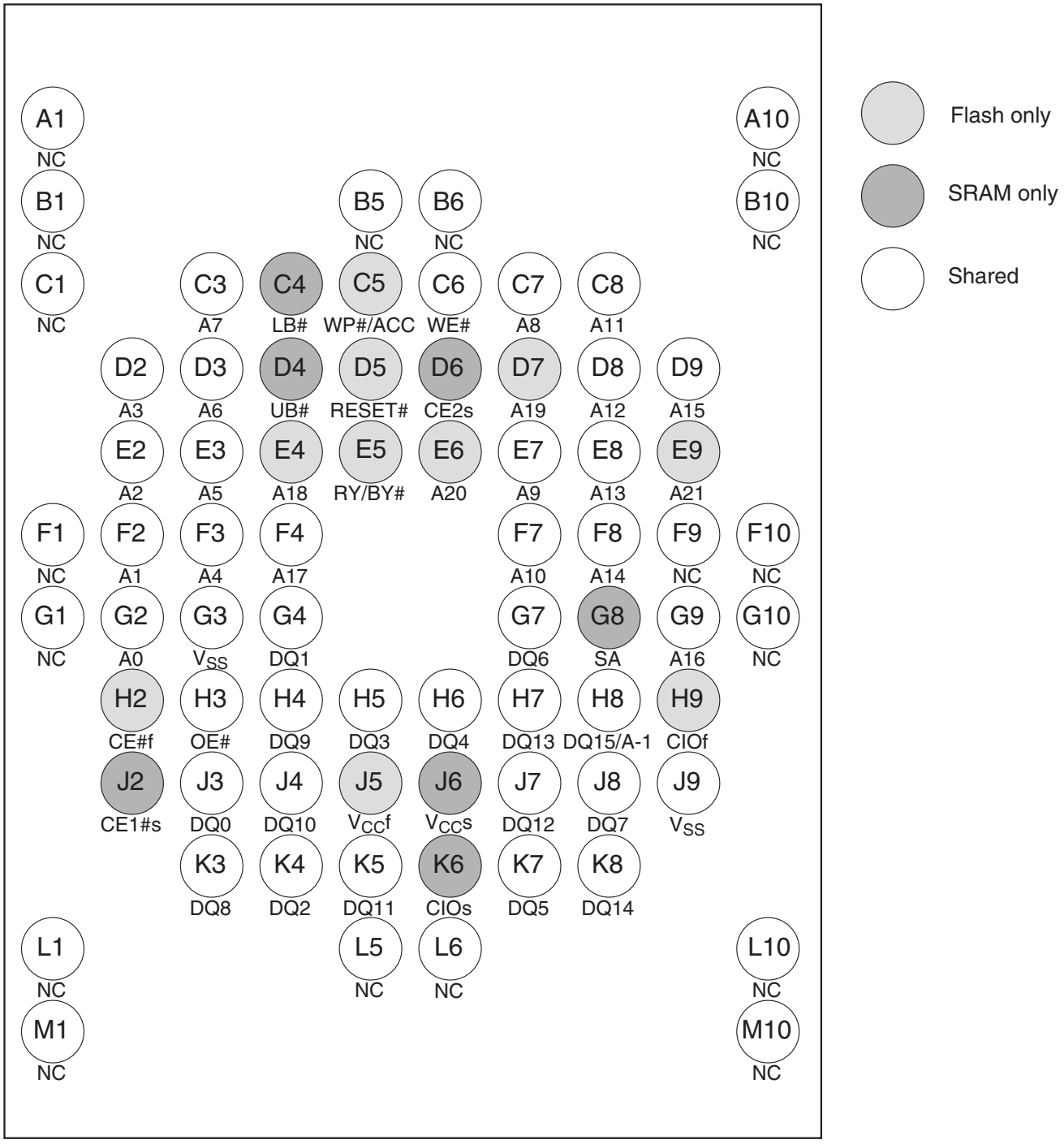
MCP Block Diagram of S71JLI28HC0, Model Numbers 00/0I/02



Connection Diagrams

Connection Diagram of S71JL064H80, Model Numbers 0I/02

73-Ball FBGA
Top View



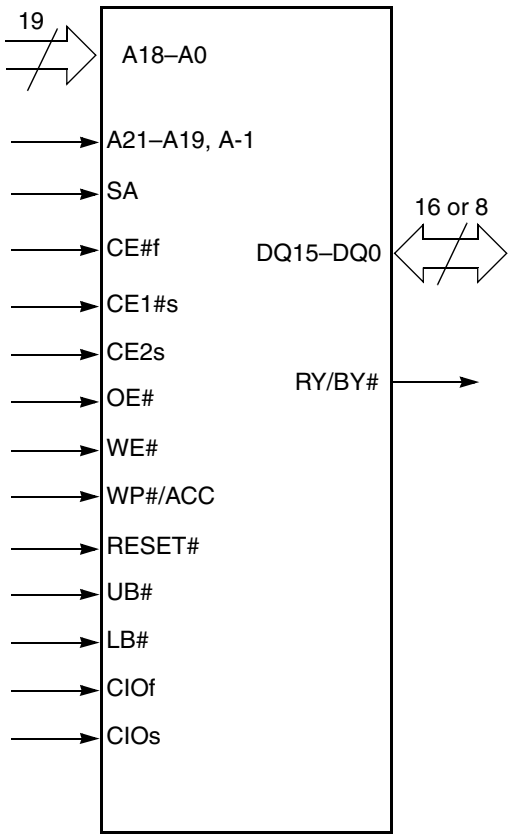
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (FBGA). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

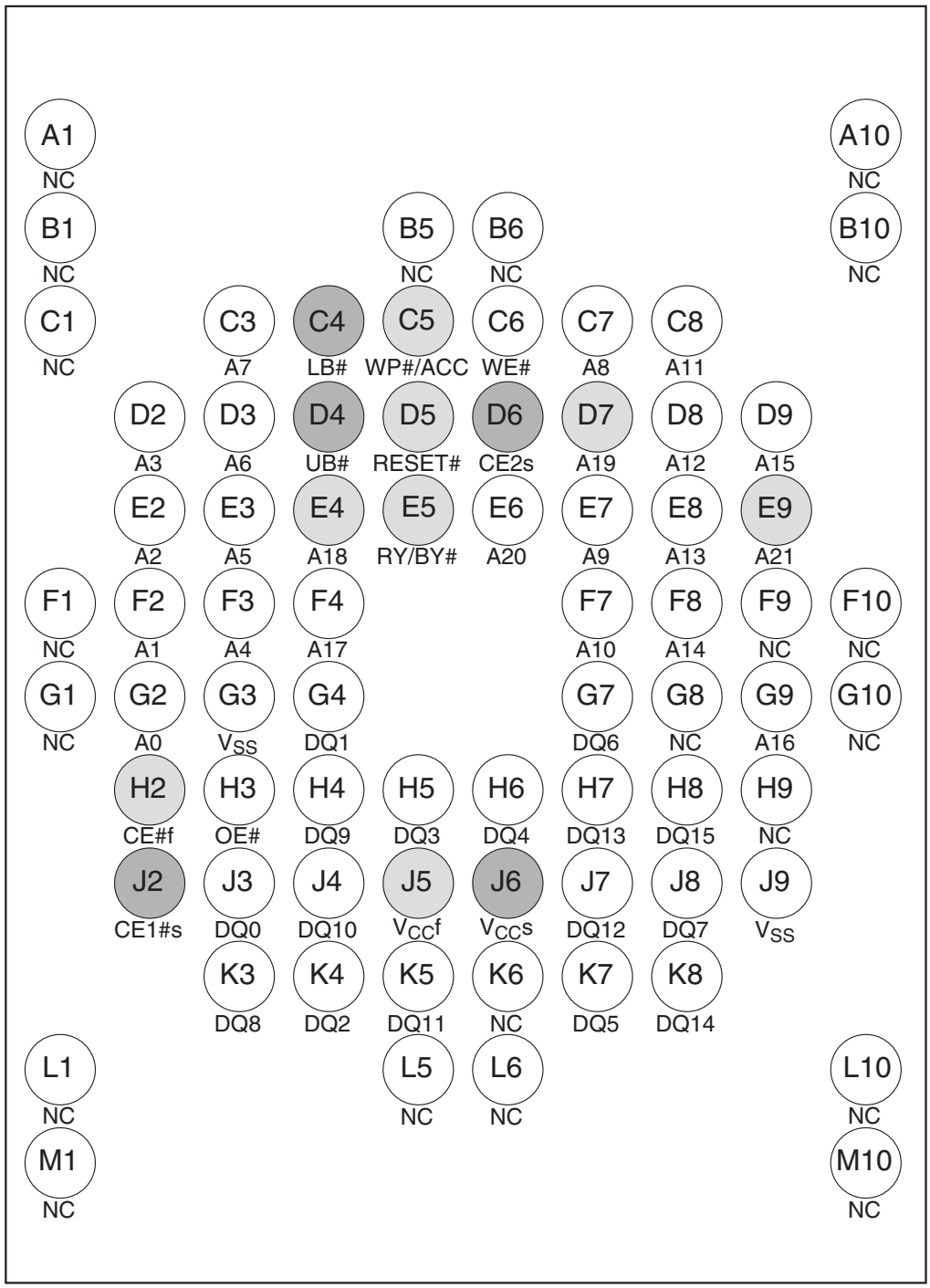
A18–A0	=	19 Address Inputs (Common)
A21–A19, A-1	=	4 Address Inputs (Flash)
SA	=	Highest Order Address Pin (SRAM) Byte mode
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f	=	Chip Enable (Flash)
CE#s	=	Chip Enable (SRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (SRAM)
LB#	=	Lower Byte Control (SRAM)
CIOf	=	I/O Configuration (Flash) CIOf = V_{IH} = Word mode (x16), CIOf = V_{IL} = Byte mode (x8)
CIOs	=	I/O Configuration (SRAM) CIOs = V_{IH} = Word mode (x16), CIOs = V_{IL} = Byte mode (x8)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
V_{CC}f	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{CC}s	=	SRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S71JL064H80, Model Numbers I0/II/I2

73-Ball FBGA
Top View



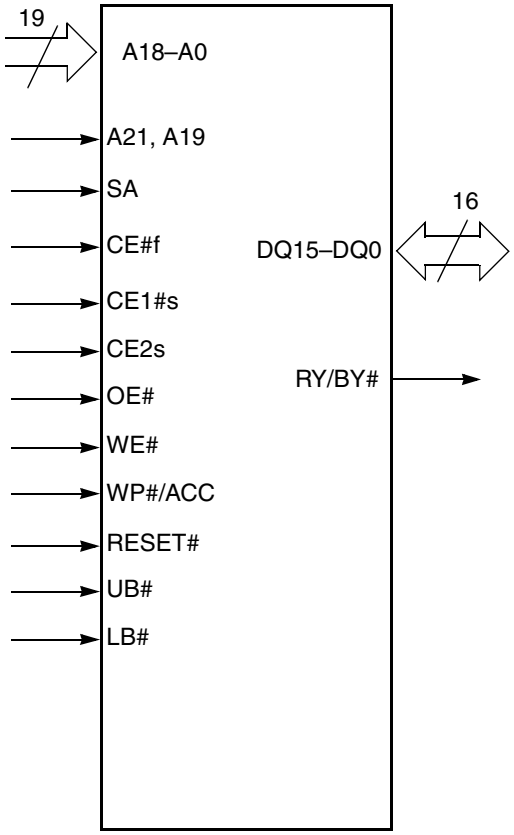
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (TSOP, BGA, PDIP, SSOP, PLCC). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

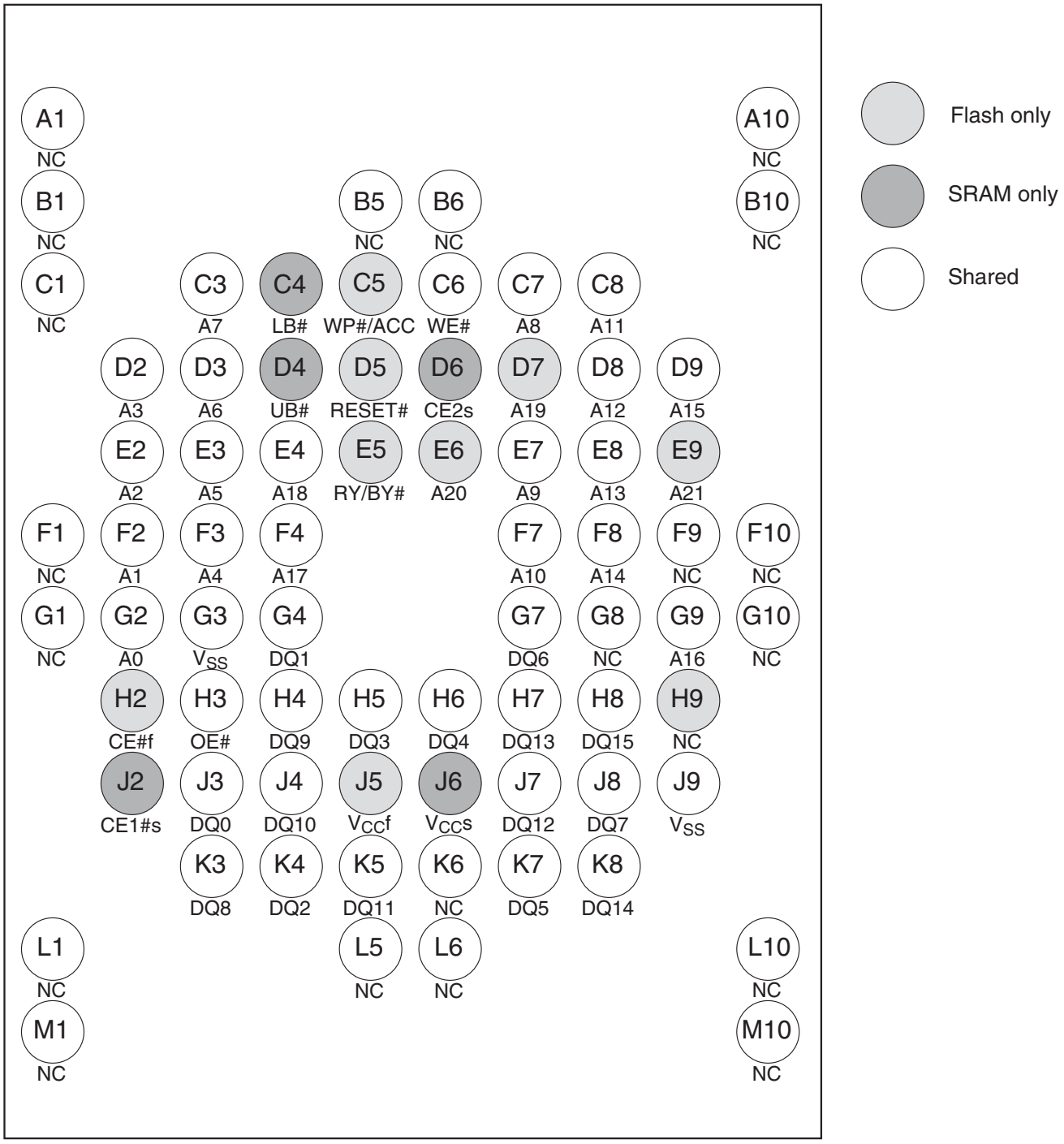
A18–A0	=	19 Address Inputs (Common)
A21–A19	=	2 Address Inputs (Flash)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f	=	Chip Enable (Flash)
CE1#s	=	Chip Enable 1 (pSRAM)
CE2s	=	Chip Enable 2 (pSRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (pSRAM)
LB#	=	Lower Byte Control (pSRAM)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
V_{CC}f	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{CC}s	=	pSRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S71JL064HA0, Model Numbers 0I/02

73-Ball FBGA
Top View



Special Package Handling Instructions for FBGA Package

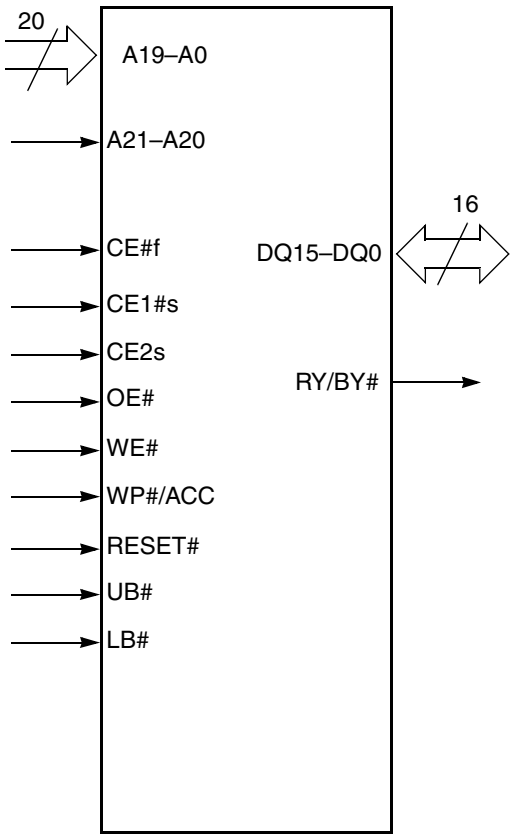
Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

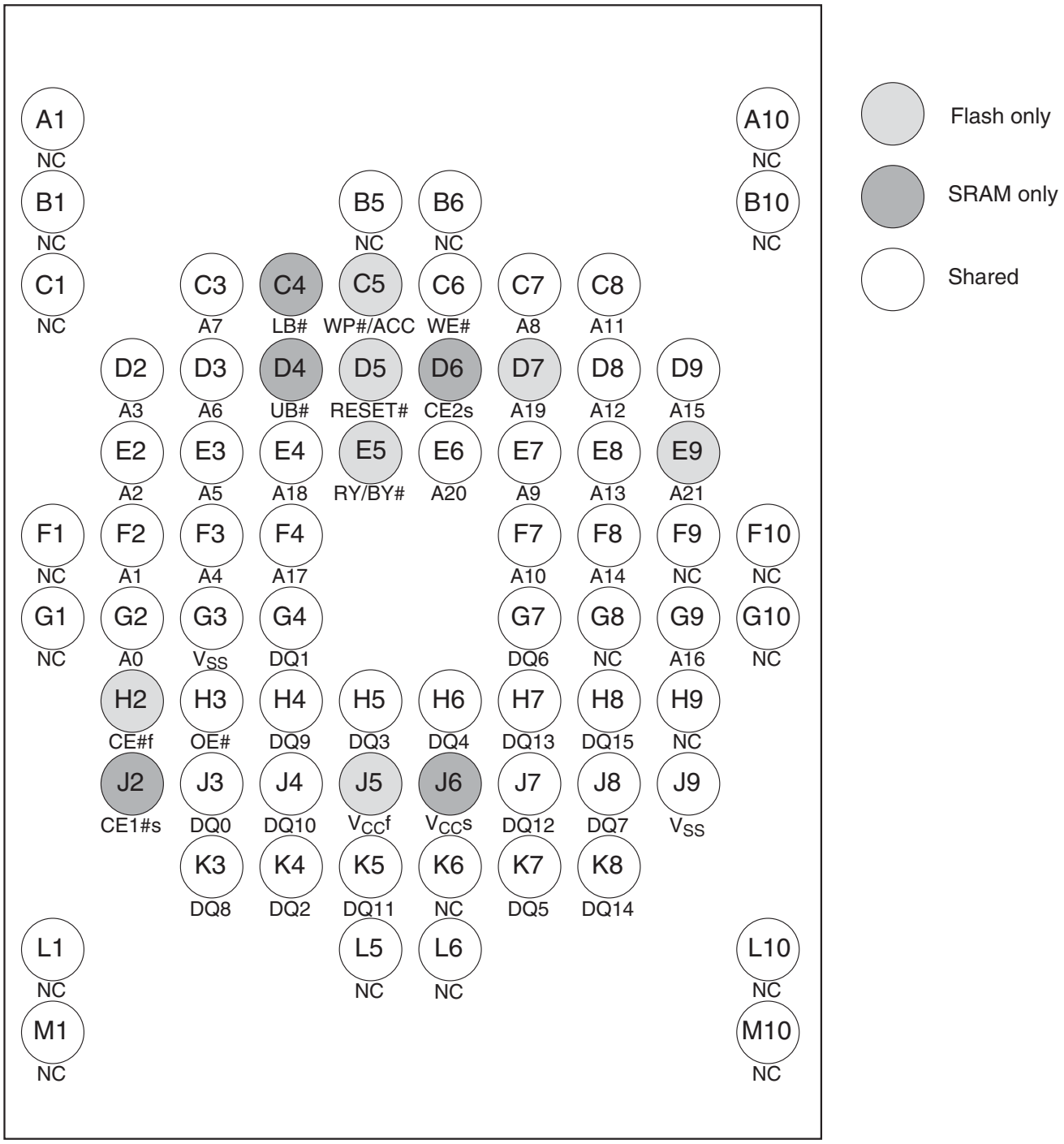
A19–A0	=	20 Address Inputs (Common)
A21–A20	=	2 Address Inputs (Flash)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f	=	Chip Enable (Flash)
CE#s	=	Chip Enable (SRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (SRAM)
LB#	=	Lower Byte Control (SRAM)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
V_{CC}f	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{CC}s	=	SRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S71JL064HA0, Model Numbers I0/I1/I2/62

73-Ball FBGA
Top View



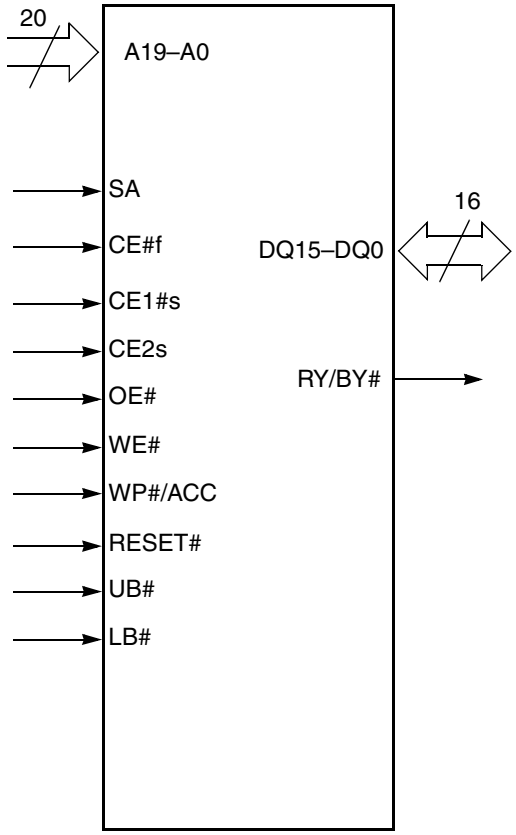
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (TSOP, BGA, PDIP, SSOP, PLCC). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

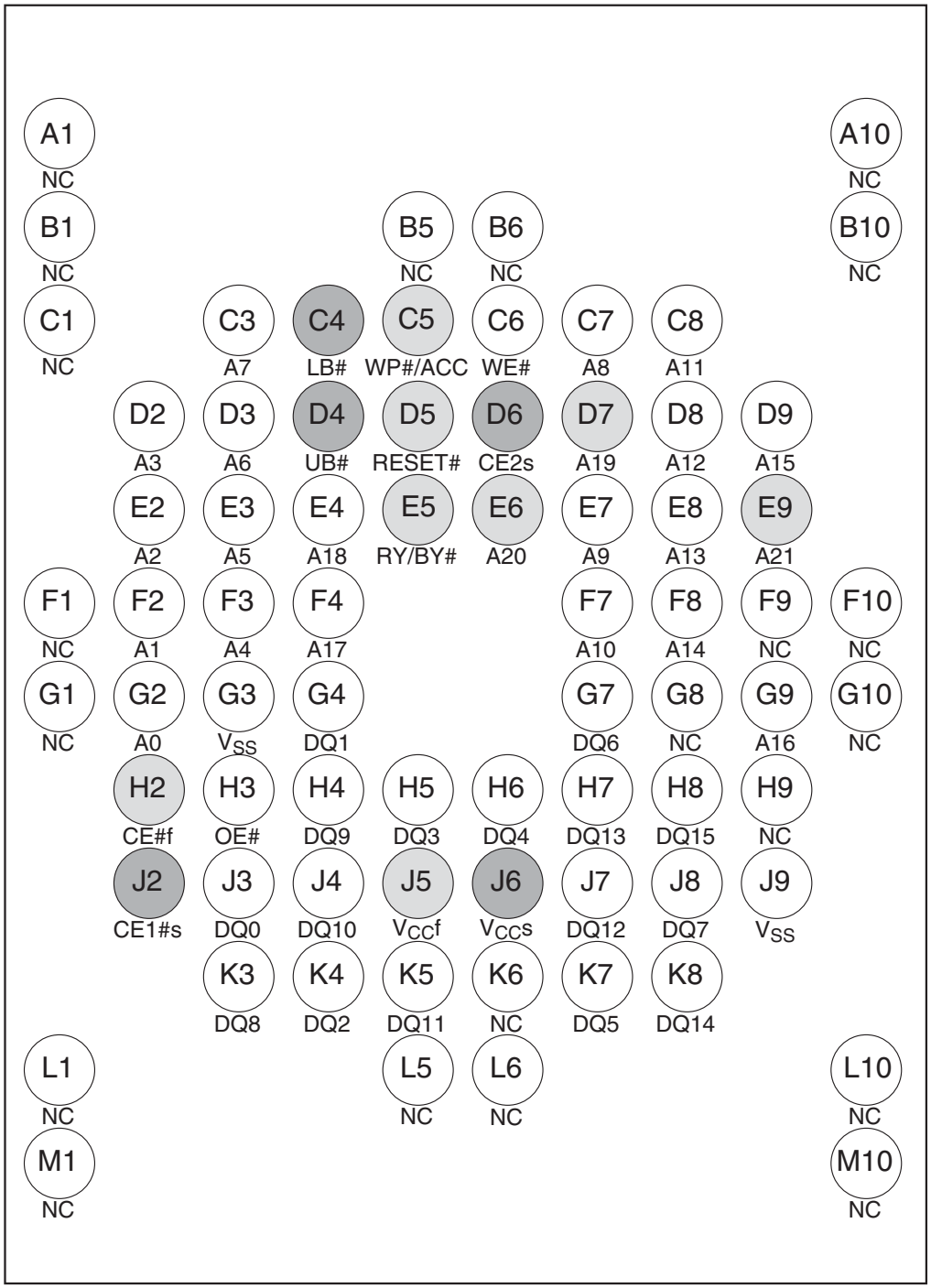
A19–A0	=	20 Address Inputs (Common)
A21–A20	=	2 Address Inputs (Flash)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f	=	Chip Enable (Flash)
CE1#s	=	Chip Enable 1 (pSRAM)
CE2s	=	Chip Enable 2 (pSRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (pSRAM)
LB#	=	Lower Byte Control (pSRAM)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
V_{CC}f	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{CC}s	=	pSRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S71JL064HB0, Model Numbers 00/0I/02

73-Ball FBGA
Top View



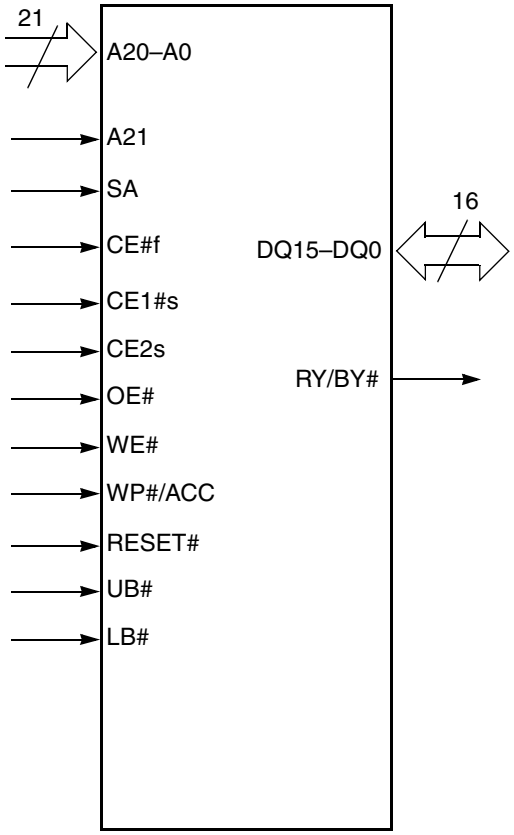
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (TSOP, BGA, PDIP, SSOP, PLCC). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

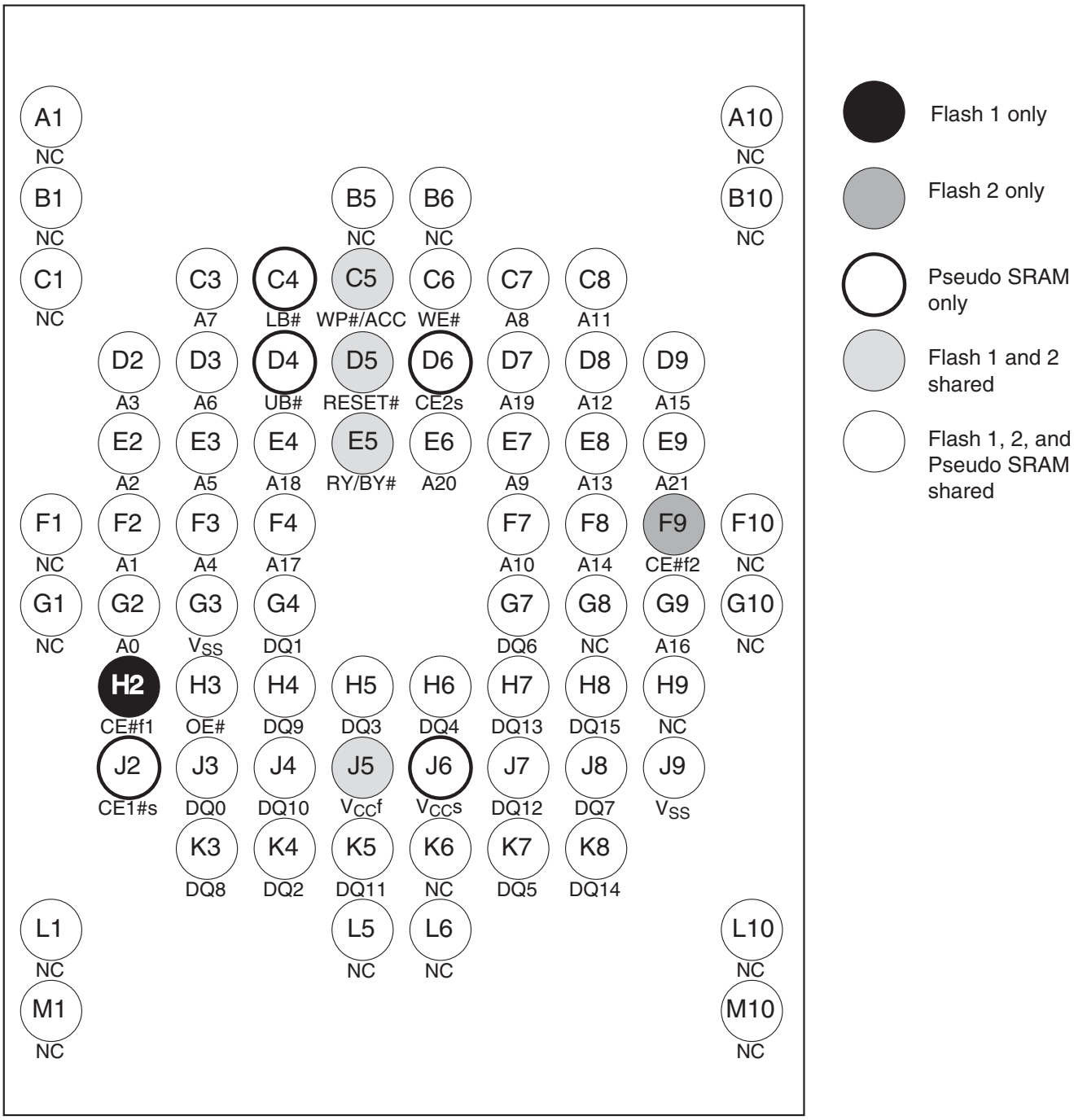
A20–A0	=	20 Address Inputs (Common)
A21	=	1 Address Input (Flash)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f	=	Chip Enable (Flash)
CE1#s	=	Chip Enable 1 (pSRAM)
CE2s	=	Chip Enable 2 (pSRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (pSRAM)
LB#	=	Lower Byte Control (pSRAM)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
V_{CC}f	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{CC}s	=	pSRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S71JLI28HB0, Model Numbers 00/0I/02

73-Ball FBGA
Top View



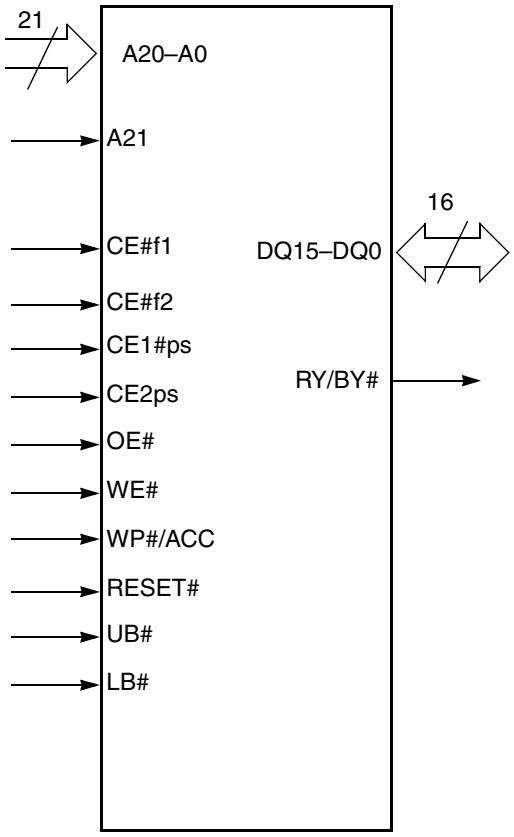
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (BGA). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

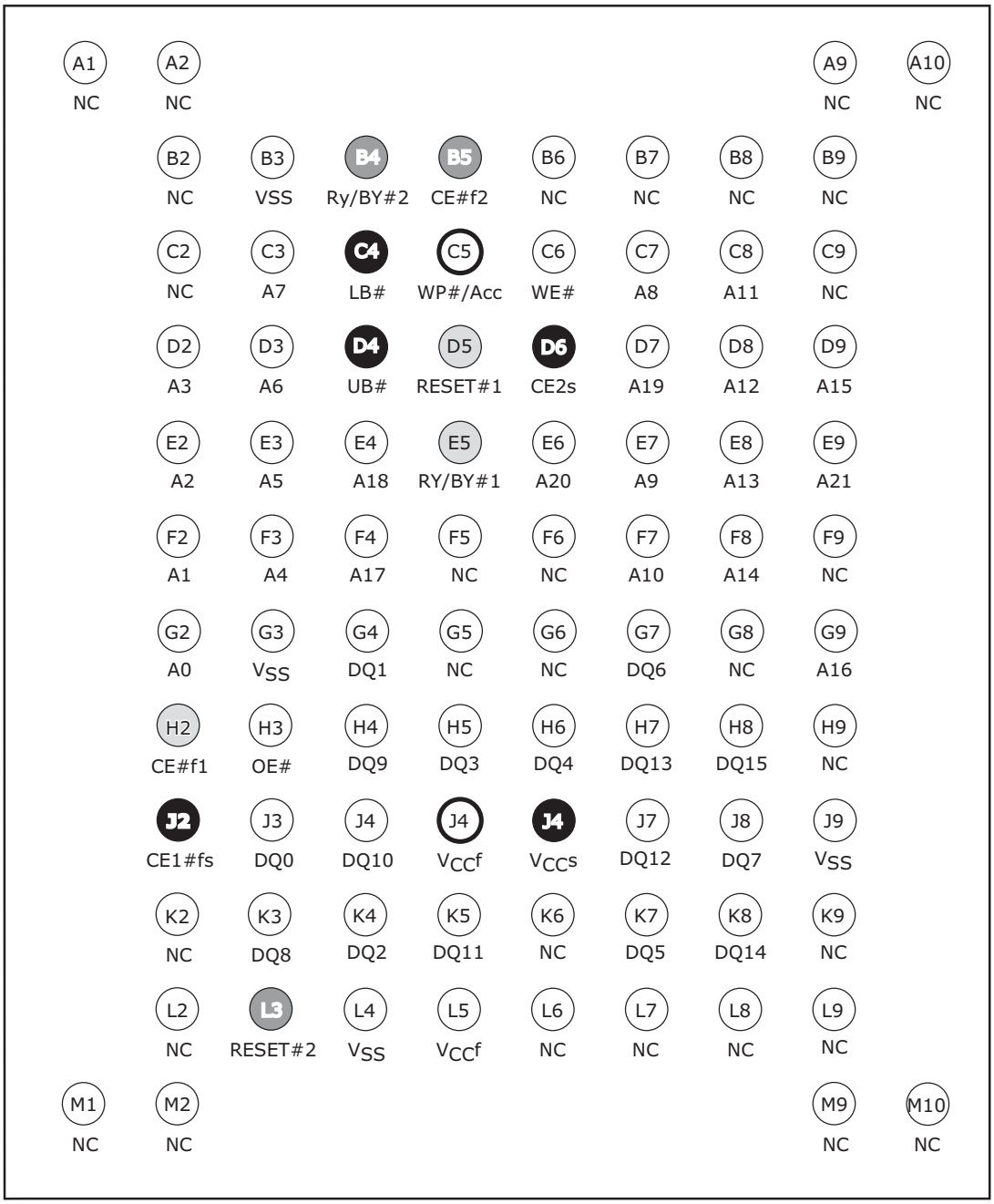
A20–A0	=	21 Address Inputs (Common)
A21	=	1 Address Input (Flash)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f1	=	Chip Enable 1 (Flash 1)
CE#f2	=	Chip Enable 2 (Flash 2)
CE1#ps	=	Chip Enable 1 (pSRAM)
CE2ps	=	Chip Enable 2 (pSRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#	=	Ready/Busy Output
UB#	=	Upper Byte Control (pSRAM)
LB#	=	Lower Byte Control (pSRAM)
RESET#	=	Hardware Reset Pin, Active Low
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
$V_{CC}f$	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
$V_{CC}ps$	=	pSRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Connection Diagram of S7IJLI28HC0, Model Numbers 00/0I/02

88-ball Fine-Pitch Ball Grid Array
(Top View, Balls Facing Down)



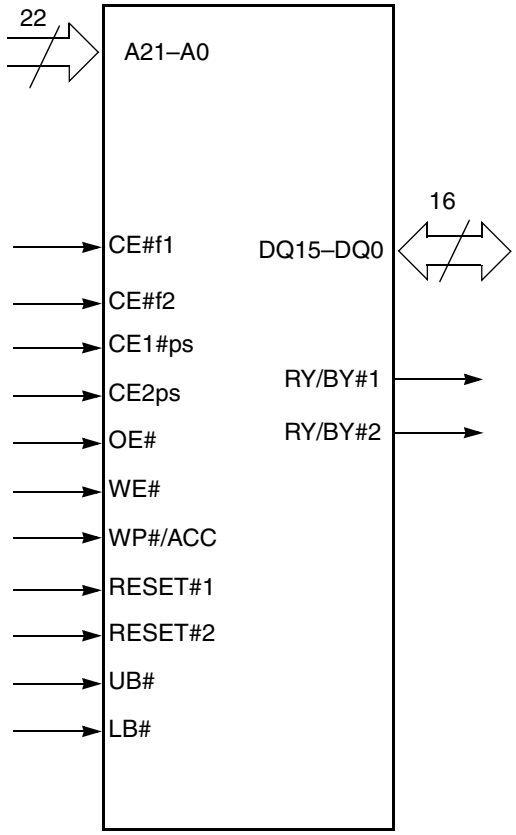
Special Package Handling Instructions

Special handling is required for Flash Memory products in molded packages (TSOP, BGA, PLCC, PDIP, SSOP). The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

Pin Description

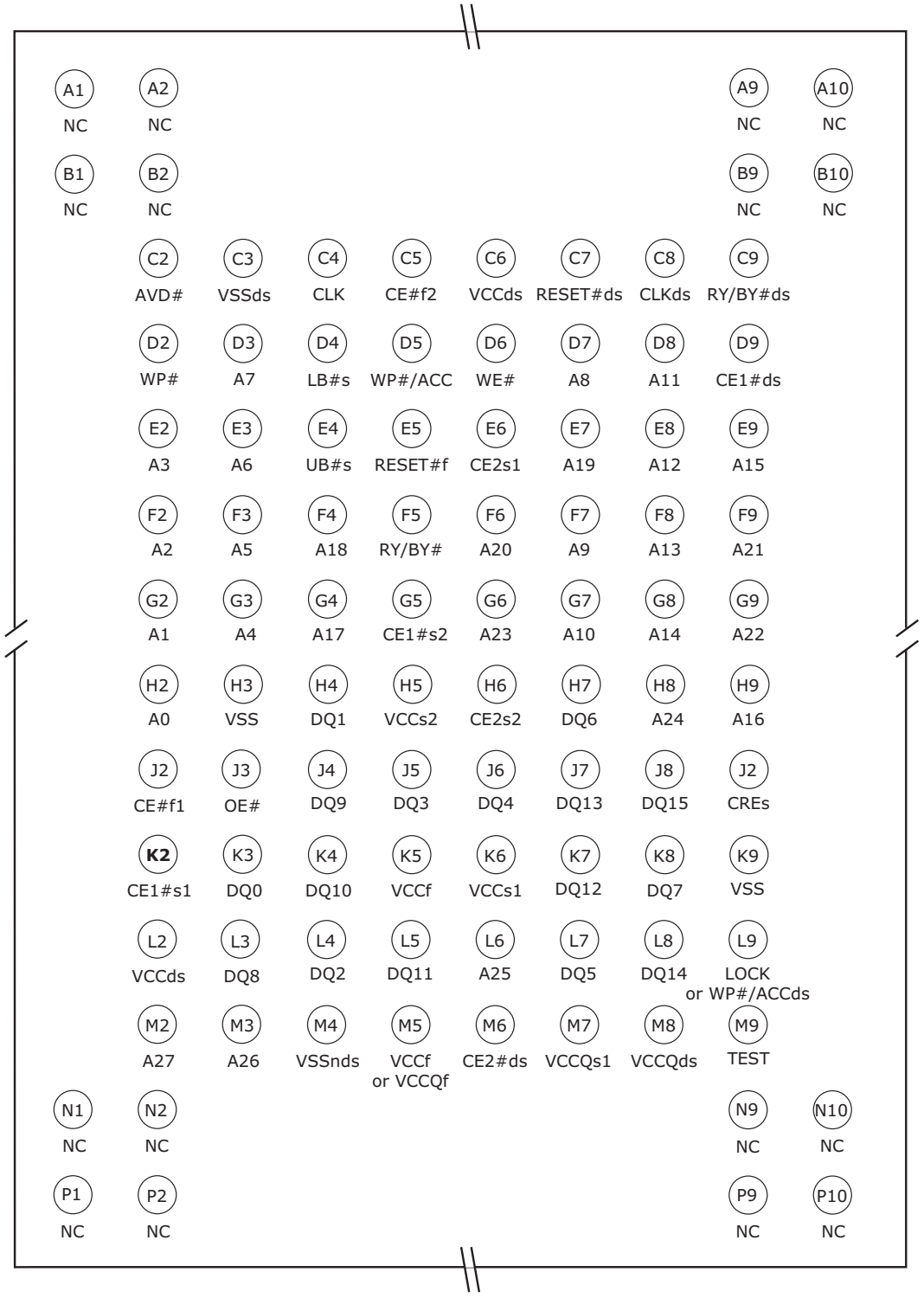
A21–A0	=	22 Address Inputs (Common)
DQ15–DQ0	=	16 Data Inputs/Outputs (Common)
CE#f1	=	Chip Enable 1 (Flash 1)
CE#f2	=	Chip Enable 2 (Flash 2)
CE1#ps	=	Chip Enable 1 (pSRAM)
CE2ps	=	Chip Enable 2 (pSRAM)
OE#	=	Output Enable (Common)
WE#	=	Write Enable (Common)
RY/BY#1	=	Ready/Busy Output (Flash 1)
RY/BY#2	=	Ready/Busy Output (Flash 2)
UB#	=	Upper Byte Control (pSRAM)
LB#	=	Lower Byte Control (pSRAM)
RESET#1	=	Hardware Reset Pin, Active Low (Flash 1)
RESET#2	=	Hardware Reset Pin, Active Low (Flash 2)
WP#/ACC	=	Hardware Write Protect/Acceleration Pin (Flash)
$V_{CC}f$	=	Flash 3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
$V_{CC}ps$	=	pSRAM Power Supply
V_{SS}	=	Device Ground (Common)
NC	=	Pin Not Connected Internally

Logic Symbol



Look-ahead Connection Diagram

96-ball Fine-Pitch Ball Grid Array
(Top View, Balls Facing Down)



Legend:

ds = Data storage only
f = Flash shared only
f1 = 1st Flash only
f2 = 2nd Flash only
NC = Outrigger balls
s = RAM shared
s1 = 1st RAM only
s2 = 2nd RAM only

Note: *To provide customers with a migration path to higher densities and an option to stack more die in a package, FASL has prepared a standard pinout that supports*

- *NOR Flash and SRAM densities up to 4 Gigabits*
- *NOR Flash and pSRAM densities up to 4 Gigabits*

- *NOR Flash and pSRAM and DATA STORAGE densities up to 4 Gigabits*

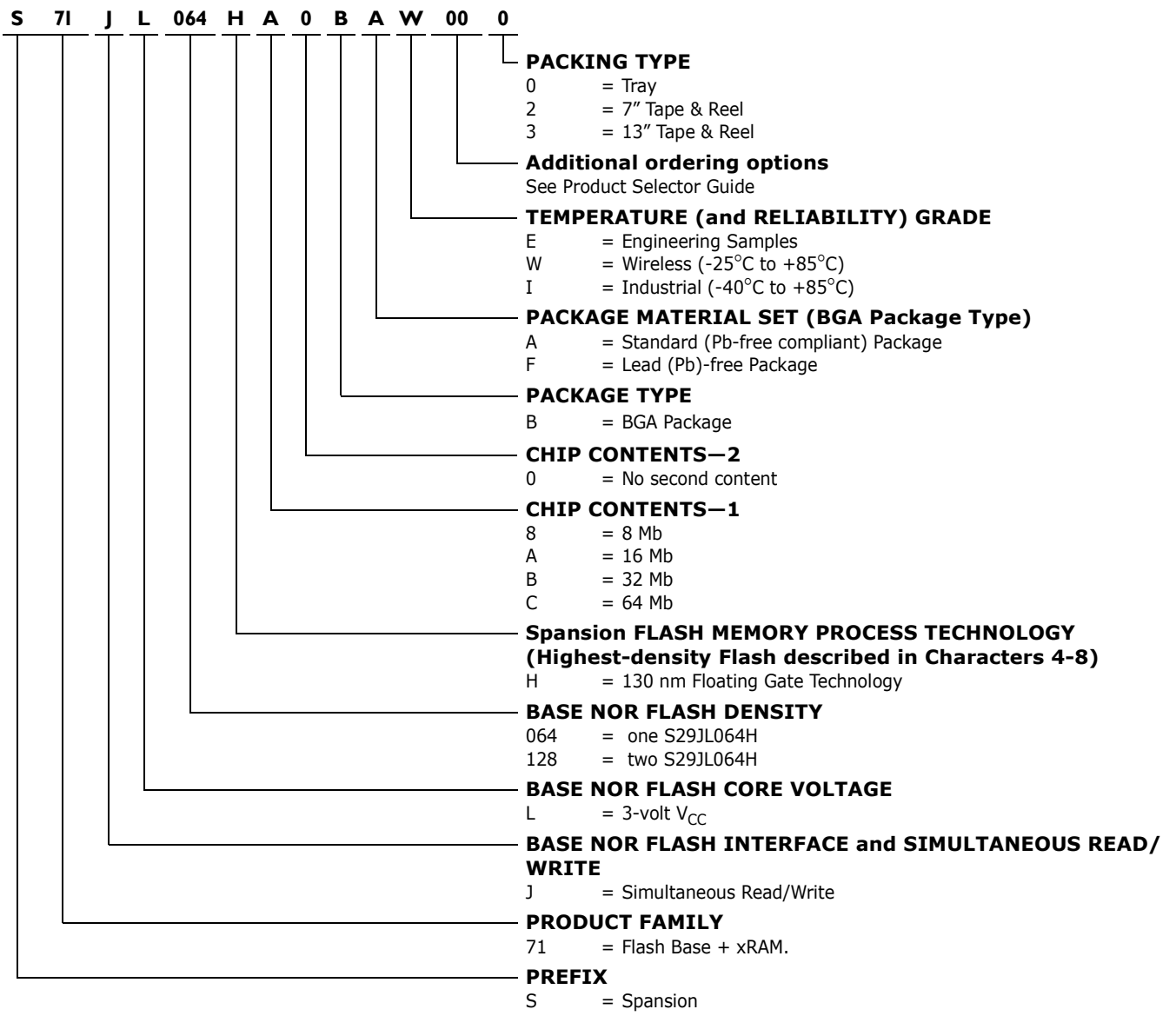
The signal locations of the resultant MCP device are shown above. Note that for different densities, the actual package outline may vary. Any pinout in any MCP, however, will be a subset of the pinout above.

In some cases, there may be outrigger balls in locations outside the grid shown above. In such cases, the user is recommended to treat them as reserved and not connect them to any other signal.

For any further inquiries about the above look-ahead pinout, please refer to the application note on this subject or contact your sales office.

Ordering Information

The order number (Valid Combination) is formed by the following:



Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Valid Combinations		Flash Access Time (ns)	(p)SRAM Access Time (ns)	Temperature Range	Supplier
Order Number	Package Marking				
S71JL064H80BAI01	71JL064H80BAI01	70	70	-40C to +85C	Supplier 1
S71JL064H80BAI02	71JL064H80BAI02	85	85	-40C to +85C	Supplier 1
S71JL064H80BAI10	71JL064H80BAI10	55	55	-40C to +85C	Supplier 2
S71JL064H80BAI11	71JL064H80BAI11	70	70	-40C to +85C	Supplier 2

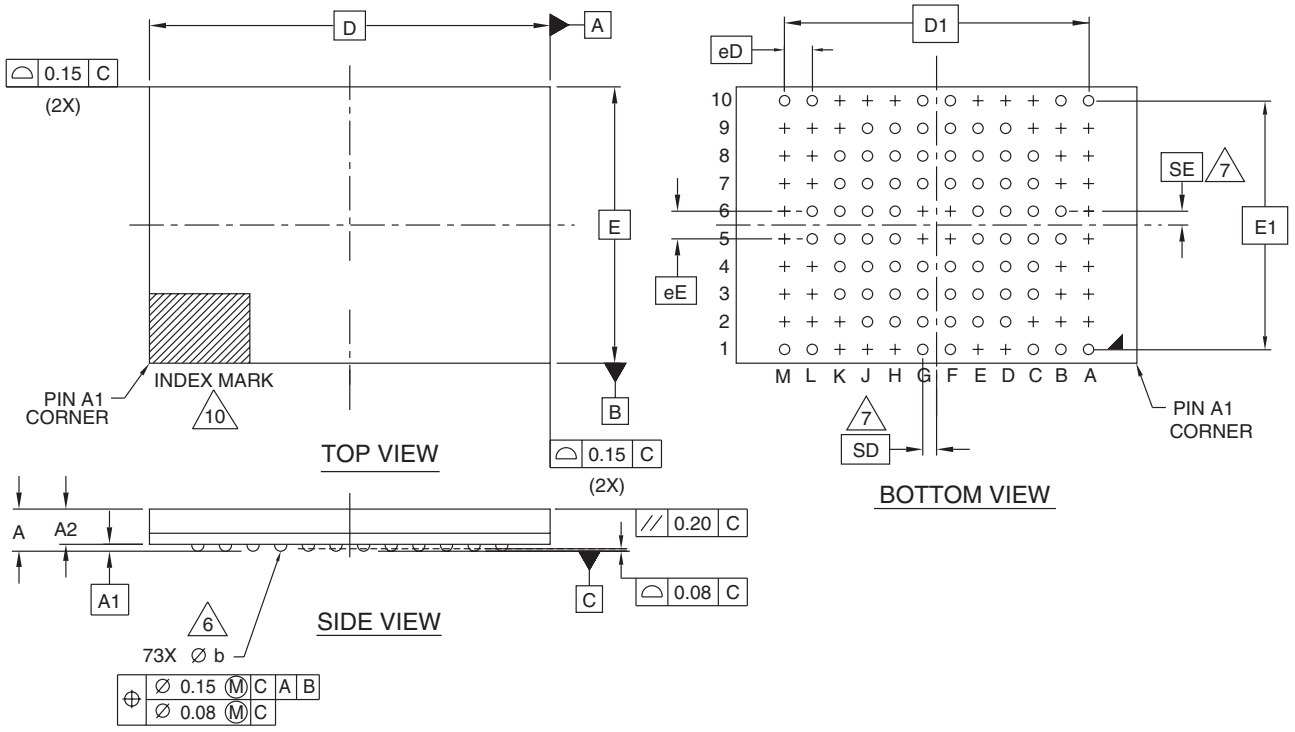
Valid Combinations		Flash Access Time (ns)	(p)SRAM Access Time (ns)	Temperature Range	Supplier
Order Number	Package Marking				
S71JL064H80BAI12	71JL064H80BAI12	85	85	-40C to +85C	Supplier 2
S71JL064H80BAW01	71JL064H80BAW01	70	70	-25C to +85C	Supplier 1
S71JL064H80BAW02	71JL064H80BAW02	85	85	-25C to +85C	Supplier 1
S71JL064H80BAW10	71JL064H80BAW10	55	55	-25C to +85C	Supplier 2
S71JL064H80BAW11	71JL064H80BAW11	70	70	-25C to +85C	Supplier 2
S71JL064H80BAW12	71JL064H80BAW12	85	85	-25C to +85C	Supplier 2
S71JL064H80BFI01	71JL064H80BFI01	70	70	-40C to +85C	Supplier 1
S71JL064H80BFI02	71JL064H80BFI02	85	85	-40C to +85C	Supplier 1
S71JL064H80BFI10	71JL064H80BFI10	55	55	-40C to +85C	Supplier 2
S71JL064H80BFI11	71JL064H80BFI11	70	70	-40C to +85C	Supplier 2
S71JL064H80BFI12	71JL064H80BFI12	85	85	-40C to +85C	Supplier 2
S71JL064H80BFW01	71JL064H80BFW01	70	70	-25C to +85C	Supplier 1
S71JL064H80BFW02	71JL064H80BFW02	85	85	-25C to +85C	Supplier 1
S71JL064H80BFW10	71JL064H80BFW10	55	55	-25C to +85C	Supplier 2
S71JL064H80BFW11	71JL064H80BFW11	70	70	-25C to +85C	Supplier 2
S71JL064H80BFW12	71JL064H80BFW12	85	85	-25C to +85C	Supplier 2
S71JL064HA0BAI01	71JL064HA0BAI01	70	70	-40C to +85C	Supplier 1
S71JL064HA0BAI02	71JL064HA0BAI02	85	85	-40C to +85C	Supplier 1
S71JL064HA0BAI10	71JL064HA0BAI10	55	55	-40C to +85C	Supplier 2
S71JL064HA0BAI11	71JL064HA0BAI11	70	70	-40C to +85C	Supplier 2
S71JL064HA0BAI12	71JL064HA0BAI12	85	85	-40C to +85C	Supplier 2
S71JL064HA0BAI61	71JL064HA0BAI61	70	70	-40C to +85C	Supplier 4
S71JL064HA0BAW01	71JL064HA0BAW01	70	70	-25C to +85C	Supplier 1
S71JL064HA0BAW02	71JL064HA0BAW02	85	85	-25C to +85C	Supplier 1
S71JL064HA0BAW10	71JL064HA0BAW10	55	55	-25C to +85C	Supplier 2
S71JL064HA0BAW11	71JL064HA0BAW11	70	70	-25C to +85C	Supplier 2
S71JL064HA0BAW12	71JL064HA0BAW12	85	85	-25C to +85C	Supplier 2
S71JL064HA0BAW61	71JL064HA0BAW61	70	70	-25C to +85C	Supplier 4
S71JL064HA0BFI01	71JL064HA0BFI01	70	70	-40C to +85C	Supplier 1
S71JL064HA0BFI02	71JL064HA0BFI02	85	85	-40C to +85C	Supplier 1
S71JL064HA0BFI10	71JL064HA0BFI10	55	55	-40C to +85C	Supplier 2
S71JL064HA0BFI11	71JL064HA0BFI11	70	70	-40C to +85C	Supplier 2
S71JL064HA0BFI12	71JL064HA0BFI12	85	85	-40C to +85C	Supplier 2
S71JL064HA0BFI62	71JL064HA0BFI62	70	70	-40C to +85C	Supplier 4

Valid Combinations		Flash Access Time (ns)	(p)SRAM Access Time (ns)	Temperature Range	Supplier
Order Number	Package Marking				
S71JL064HA0BFW01	71JL064HA0BFW01	70	70	-25C to +85C	Supplier 1
S71JL064HA0BFW02	71JL064HA0BFW02	85	85	-25C to +85C	Supplier 1
S71JL064HA0BFW10	71JL064HA0BFW10	55	55	-25C to +85C	Supplier 2
S71JL064HA0BFW11	71JL064HA0BFW11	70	70	-25C to +85C	Supplier 2
S71JL064HA0BFW12	71JL064HA0BFW12	85	85	-25C to +85C	Supplier 2
S71JL064HA0BFW62	71JL064HA0BFW62	70	70	-25C to +85C	Supplier 4
S71JL064HB0BAI00	71JL064HB0BAI00	55	55	-40C to +85C	Supplier 3
S71JL064HB0BAI01	71JL064HB0BAI01	70	70	-40C to +85C	Supplier 3
S71JL064HB0BAI02	71JL064HB0BAI02	85	85	-40C to +85C	Supplier 3
S71JL064HB0BAW00	71JL064HB0BAW00	55	55	-25C to +85C	Supplier 3
S71JL064HB0BAW01	71JL064HB0BAW01	70	70	-25C to +85C	Supplier 3
S71JL064HB0BAW02	71JL064HB0BAW02	85	85	-25C to +85C	Supplier 3
S71JL064HB0BFI00	71JL064HB0BFI00	55	55	-40C to +85C	Supplier 3
S71JL064HB0BFI01	71JL064HB0BFI01	70	70	-40C to +85C	Supplier 3
S71JL064HB0BFI02	71JL064HB0BFI02	85	85	-40C to +85C	Supplier 3
S71JL064HB0BFW00	71JL064HB0BFW00	55	55	-25C to +85C	Supplier 3
S71JL064HB0BFW01	71JL064HB0BFW01	70	70	-25C to +85C	Supplier 3
S71JL064HB0BFW02	71JL064HB0BFW02	85	85	-25C to +85C	Supplier 3
S71JL128HB0BAI00	71JL128HB0BAI00	55	55	-40C to +85C	Supplier 3
S71JL128HB0BAI01	71JL128HB0BAI01	70	70	-40C to +85C	Supplier 3
S71JL128HB0BAI02	71JL128HB0BAI02	85	85	-40C to +85C	Supplier 3
S71JL128HB0BAW00	71JL128HB0BAW00	55	55	-25C to +85C	Supplier 3
S71JL128HB0BAW01	71JL128HB0BAW01	70	70	-25C to +85C	Supplier 3
S71JL128HB0BAW02	71JL128HB0BAW02	85	85	-25C to +85C	Supplier 3
S71JL128HB0BFI00	71JL128HB0BFI00	55	55	-40C to +85C	Supplier 3
S71JL128HB0BFI01	71JL128HB0BFI01	70	70	-40C to +85C	Supplier 3
S71JL128HB0BFI02	71JL128HB0BFI02	85	85	-40C to +85C	Supplier 3
S71JL128HB0BFW00	71JL128HB0BFW00	55	55	-25C to +85C	Supplier 3
S71JL128HB0BFW01	71JL128HB0BFW01	70	70	-25C to +85C	Supplier 3
S71JL128HB0BFW02	71JL128HB0BFW02	85	85	-25C to +85C	Supplier 3
S71JL128HC0BAI00	71JL128HC0BAI00	55	55	-40C to +85C	Supplier 3
S71JL128HC0BAI01	71JL128HC0BAI01	70	70	-40C to +85C	Supplier 3

Valid Combinations		Flash Access Time (ns)	(p)SRAM Access Time (ns)	Temperature Range	Supplier
Order Number	Package Marking				
S71JL128HC0BAI02	71JL128HC0BAI02	85	85	-40C to +85C	Supplier 3
S71JL128HC0BAW00	71JL128HC0BAW00	55	55	-25C to +85C	Supplier 3
S71JL128HC0BAW01	71JL128HC0BAW01	70	70	-25C to +85C	Supplier 3
S71JL128HC0BAW02	71JL128HC0BAW02	85	85	-25C to +85C	Supplier 3
S71JL128HC0BFI00	71JL128HC0BFI00	55	55	-40C to +85C	Supplier 3
S71JL128HC0BFI01	71JL128HC0BFI01	70	70	-40C to +85C	Supplier 3
S71JL128HC0BFI02	71JL128HC0BFI02	85	85	-40C to +85C	Supplier 3
S71JL128HC0BFW00	71JL128HC0BFW00	55	55	-25C to +85C	Supplier 3
S71JL128HC0BFW01	71JL128HC0BFW01	70	70	-25C to +85C	Supplier 3
S71JL128HC0BFW02	71JL128HC0BFW02	85	85	-25C to +85C	Supplier 3

Physical Dimensions

FLB073



PACKAGE	FLB 073			NOTE
JEDEC	N/A			
	11.60 mm x 8.00 mm PACKAGE			
SYMBOL	MIN.	NOM.	MAX.	
A	---	---	1.40	PROFILE
A1	0.20	---	---	BALL HEIGHT
A2	0.95	---	1.13	BODY THICKNESS
D		11.60 BSC.		BODY SIZE
E		8.00 BSC.		BODY SIZE
D1		8.80 BSC.		MATRIX FOOTPRINT
E1		7.20 BSC.		MATRIX FOOTPRINT
MD		12		MATRIX SIZE D DIRECTION
ME		10		MATRIX SIZE E DIRECTION
n		73		BALL COUNT
Øb	0.25	0.30	0.35	BALL DIAMETER
eE		0.80 BSC		BALL PITCH
eD		0.80 BSC		BALL PITCH
SD/SE		0.40 BSC		SOLDER BALL PLACEMENT
	A2,A3,A4,A5,A6,A7,A8,A9 B2,B3,B4,B7,B8,B9 C2,C9,C10,D1,D10,E1,E10 F5,F6,G5,G6,H1,H10 J1,J10,K1,K2, K9,K10,L2,L3,L4,L7,L8,L9 M2,M3,M4,M5,M6,M7,M8,M9			DEPOPULATED SOLDER BALL

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
4. e REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

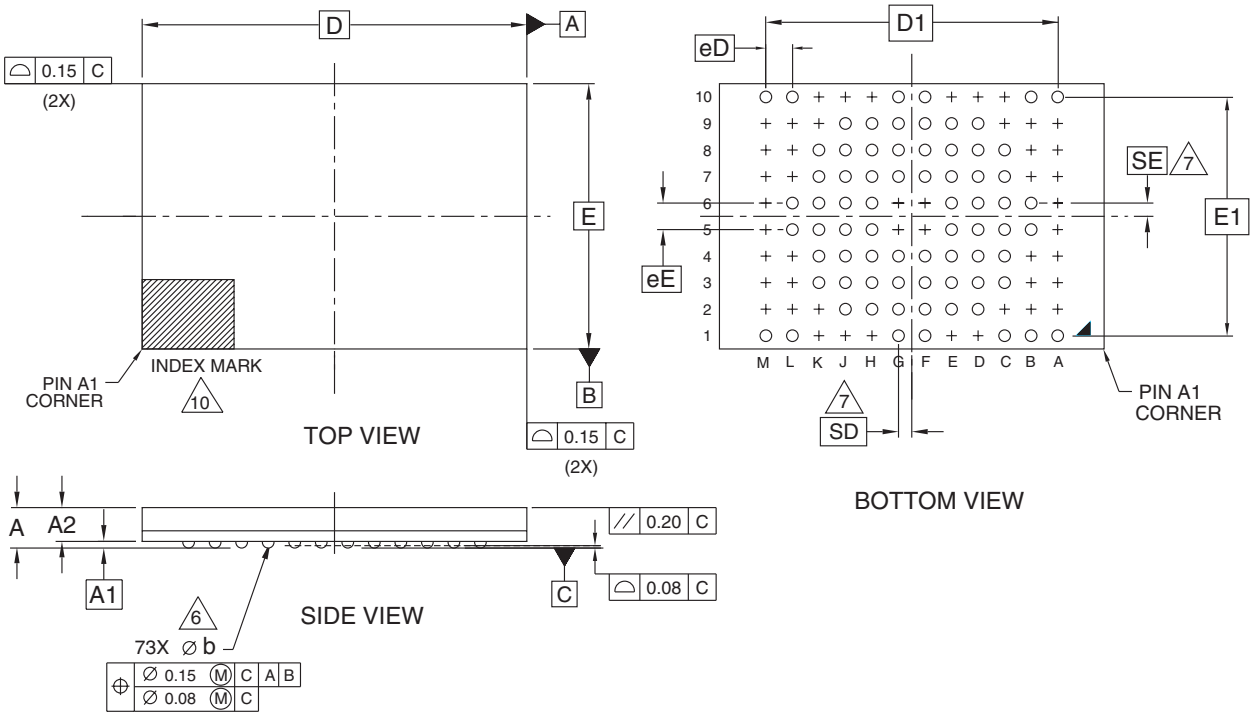
   n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
9. N/A
10. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTION OR OTHER MEANS.

3188\38.14b

FLJ073



PACKAGE	FLJ 073			
JEDEC	N/A			
	11.60 mm x 8.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
A	---	---	1.40	PROFILE
A1	0.25	---	---	BALL HEIGHT
A2	0.95	---	1.13	BODY THICKNESS
D		11.60 BSC.		BODY SIZE
E		8.00 BSC.		BODY SIZE
D1		8.80 BSC.		MATRIX FOOTPRINT
E1		7.20 BSC.		MATRIX FOOTPRINT
MD		12		MATRIX SIZE D DIRECTION
ME		10		MATRIX SIZE E DIRECTION
n		73		BALL COUNT
ϕb	0.30	0.35	0.40	BALL DIAMETER
eE		0.80 BSC.		BALL PITCH
eD		0.80 BSC.		BALL PITCH
SD / SE		0.40 BSC.		SOLDER BALL PLACEMENT
	A2,A3,A4,A5,A6,A7,A8,A9,B2,B3,B4,B7,B8,B9 C2,C9,C10,D1,D10,E1,E10,F5,F6,G5,G6,H1,H10 J1,J10,K1,K2,K9,K10,L2,L3,L4,L7,L8,L9 M2,M3,M4,M5,M6,M7,M8,M9			DEPOPULATED SOLDER BALLS

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
4. e REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

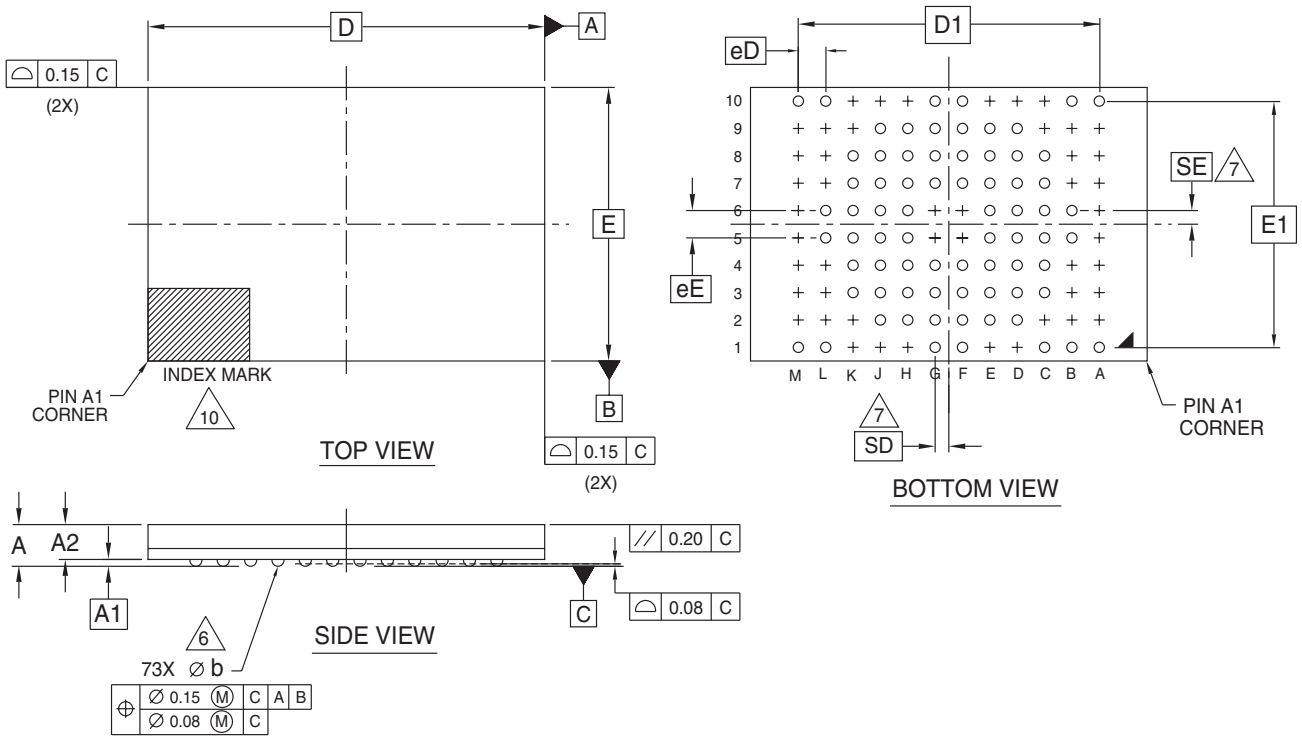
   n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = 0.000.

   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
9. NOT USED.
10. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

3232 \ 16-038.14b

FTA073



PACKAGE	FTA 073			NOTE
JEDEC	N/A			
	11.60 mm x 8.00 mm PACKAGE			
SYMBOL	MIN.	NOM.	MAX.	
A	---	---	1.40	PROFILE
A1	0.25	---	---	BALL HEIGHT
A2	1.00	---	1.11	BODY THICKNESS
D	11.60 BSC.			BODY SIZE
E	8.00 BSC.			BODY SIZE
D1	8.80 BSC.			MATRIX FOOTPRINT
E1	7.20 BSC.			MATRIX FOOTPRINT
MD	12			MATRIX SIZE D DIRECTION
ME	10			MATRIX SIZE E DIRECTION
n	73			BALL COUNT
øb	0.30	0.35	0.40	BALL DIAMETER
eE	0.80 BSC			BALL PITCH
eD	0.80 BSC			BALL PITCH
SD/SE	0.40 BSC			SOLDER BALL PLACEMENT
	A2,A3,A4,A5,A6,A7,A8,A9 B2,B3,B4,B7,B8,B9,C2,C9,C10 D1,D10,E1,E10,F5,F6,G5,G6 H1,H10,J1,J10,K1,K2,K9,K10 L2,L3,L4,L7,L8,L9 M2,M3,M4,M5,M6,M7,M8,M9			DEPOPULATED SOLDER BALL

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
4. e REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

   n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.

6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

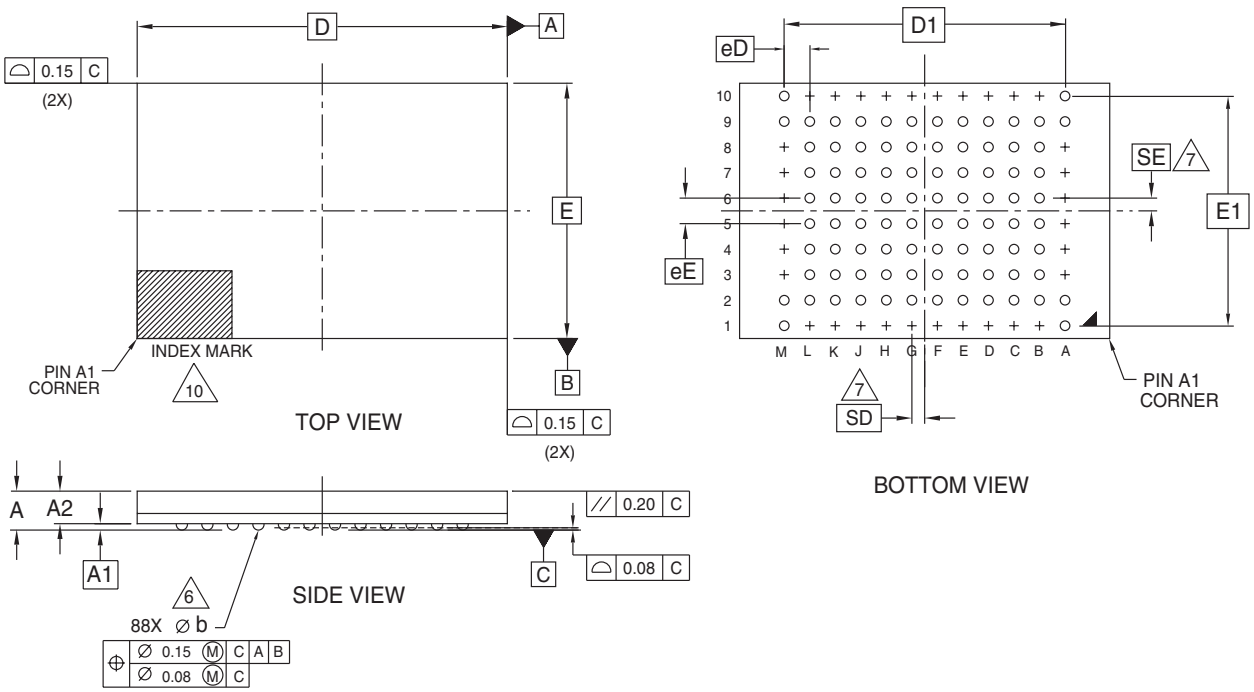
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2

8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
9. N/A
10. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTION OR OTHER MEANS.

3159\38.14b

FTA088



PACKAGE	FTA 088			
JEDEC	N/A			
	11.60 mm x 8.00 mm PACKAGE			
SYMBOL	MIN	NOM	MAX	NOTE
A	---	---	1.40	PROFILE
A1	0.25	---	---	BALL HEIGHT
A2	1.00	---	1.11	BODY THICKNESS
D		11.60 BSC.		BODY SIZE
E		8.00 BSC.		BODY SIZE
D1		8.80 BSC.		MATRIX FOOTPRINT
E1		7.20 BSC.		MATRIX FOOTPRINT
MD		12		MATRIX SIZE D DIRECTION
ME		10		MATRIX SIZE E DIRECTION
n		88		BALL COUNT
ϕb	0.30	0.35	0.40	BALL DIAMETER
eE		0.80 BSC.		BALL PITCH
eD		0.80 BSC		BALL PITCH
SD / SE		0.40 BSC.		SOLDER BALL PLACEMENT
	A3,A4,A5,A6,A7,A8,B1,B10,C1,C10,D1,D10 E1,E10,F1,F10,G1,G10,H1,H10 J1,J10,K1,K10,L1,L10,M3,M4,M5,M6,M7,M8			DEPOPULATED SOLDER BALLS

NOTES:

1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
4. e REPRESENTS THE SOLDER BALL GRID PITCH.
5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

   n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.

6. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
7. SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2

8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
9. N/A
10. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

3237 \ 16-038.14b

S29JL064H

For Multi-Chip Products (MCP)
64 Megabit (8 M x 8-Bit/4 M x 16-Bit)
CMOS 3.0 Volt-only, Simultaneous Read/Write
Flash Memory

Distinctive Characteristics

Architectural Advantages

- **Simultaneous Read/Write operations**
  - Data can be continuously read from one bank while executing erase/program functions in another bank.
  - Zero latency between read and write operations
- **Flexible Bank architecture**
  - Read may occur in any of the three banks not being written or erased.
  - Four banks may be grouped by customer to achieve desired bank divisions.
- **Boot Sectors**
  - Top and bottom boot sectors in the same device
  - Any combination of sectors can be erased
- **Manufactured on 130 nm process technology**
- **SecSi™ (Secured Silicon) Sector: Extra 256 Byte sector**
  - *Factory locked and identifiable:* 16 bytes available for secure, random factory Electronic Serial Number; verifiable as factory locked through autoselect function.
  - *Customer lockable:* One-time programmable only. Once locked, data cannot be changed
- **Zero Power Operation**
  - Sophisticated power management circuits reduce power consumed during inactive periods to nearly zero.
- **Compatible with JEDEC standards**
  - Pinout and software compatible with single-power-supply flash standard

Performance Characteristics

- **High performance**
  - Access time as fast as 55 ns
  - Program time: 4 µs/word typical using accelerated programming function
- **Ultra low power consumption (typical values)**
  - 2 mA active read current at 1 MHz
  - 10 mA active read current at 5 MHz
  - 200 nA in standby or automatic sleep mode
- **Cycling Endurance: 1 million cycles per sector typical**
- **Data Retention: 20 years typical**

Software Features

- **Supports Common Flash Memory Interface (CFI)**
- **Erase Suspend/Erase Resume**
  - Suspends erase operations to read data from, or program data to, a sector that is not being erased, then resumes the erase operation.
- **Data# Polling and Toggle Bits**
  - Provides a software method of detecting the status of program or erase cycles
- **Unlock Bypass Program command**
  - Reduces overall programming time when issuing multiple program command sequences

Hardware Features

- **Ready/Busy# output (RY/BY#)**
  - Hardware method for detecting program or erase cycle completion
- **Hardware reset pin (RESET#)**
  - Hardware method of resetting the internal state machine to the read mode
- **WP#/ACC input pin**
  - Write protect (WP#) function protects sectors 0, 1, 140, and 141, regardless of sector protect status
  - Acceleration (ACC) function accelerates program timing
- **Sector protection**
  - Hardware method to prevent any program or erase operation within a sector
  - Temporary Sector Unprotect allows changing data in protected sectors in-system

General Description

The S71JLxxxHxx_00 is a 64 megabit, 3.0 volt-only flash memory device, organized as 4,194,304 words of 16 bits each or 8,388,608 bytes of 8 bits each. Word mode Data appears on DQ15–DQ0; byte mode data appears on DQ7–DQ0. The device is designed to be programmed in-system with the standard 3.0 volt V_{CC} supply, and can also be programmed in standard EPROM programmers.

Standard control pins—chip enable (CE#), write enable (WE#), and output enable (OE#)—control normal read and write operations, and avoid bus contention issues.

The device requires only a **single 3.0 volt power supply** for both read and write functions. Internally generated and regulated voltages are provided for the program and erase operations.

Simultaneous Read/Write Operations with Zero Latency

The Simultaneous Read/Write architecture provides **simultaneous operation** by dividing the memory space into **four banks,** two 8 Mb banks with small and large sectors, and two 24 Mb banks of large sectors. Sector addresses are fixed, system software can be used to form user-defined bank groups.

During an Erase/Program operation, any of the three non-busy banks may be read from. Note that only two banks can operate simultaneously. The device can improve overall system performance by allowing a host system to program or erase in one bank, then immediately and simultaneously read from the other bank, with zero latency. This releases the system from waiting for the completion of program or erase operations.

The S71JLxxxHxx_00 can be organized as both a top and bottom boot sector configuration.

Bank	Megabits	Sector Sizes
Bank 1	8 Mb	Eight 8 Kbyte/4 Kword, Fifteen 64 Kbyte/32 Kword
Bank 2	24 Mb	Forty-eight 64 Kbyte/32 Kword
Bank 3	24 Mb	Forty-eight 64 Kbyte/32 Kword
Bank 4	8 Mb	Eight 8 Kbyte/4 Kword, Fifteen 64 Kbyte/32 Kword

S7IJLxxxHxx_00 Features

The **SecSi™ (Secured Silicon) Sector** is an extra 256 byte sector capable of being permanently locked by FASL or customers. The SecSi Customer Indicator Bit (DQ6) is permanently set to 1 if the part has been customer locked, permanently set to 0 if the part has been factory locked, and is 0 if customer lockable. This way, customer lockable parts can never be used to replace a factory locked part.

Factory locked parts provide several options. The SecSi Sector may store a secure, random 16 byte ESN (Electronic Serial Number), customer code (programmed through Spansion programming services), or both. Customer Lockable parts may utilize the SecSi Sector as bonus space, reading and writing like any other flash sector, or may permanently lock their own code there.

DMS (Data Management Software) allows systems to easily take advantage of the advanced architecture of the simultaneous read/write product line by allowing removal of EEPROM devices. DMS will also allow the system software to be simplified, as it will perform all functions necessary to modify data in file structures, as opposed to single-byte modifications. To write or update a particular piece of data (a phone number or configuration data, for example), the user only needs to state which piece of data is to be updated, and where the updated data is located in the system. This is an advantage compared to systems where user-written software must keep track of the old data location, status, logical to physical translation of the data onto the Flash memory device (or memory devices), and more. Using DMS, user-written software does not need to interface with the Flash memory directly. Instead, the user's software accesses the Flash memory by calling one of only six functions.

The device offers complete compatibility with the **JEDEC 42.4 single-power-supply Flash command set standard**. Commands are written to the command register using standard microprocessor write timings. Reading data out of the device is similar to reading from other Flash or EPROM devices.

The host system can detect whether a program or erase operation is complete by using the device **status bits:** RY/BY# pin, DQ7 (Data# Polling) and DQ6/DQ2 (toggle bits). After a program or erase cycle has been completed, the device automatically returns to the read mode.

The **sector erase architecture** allows memory sectors to be erased and reprogrammed without affecting the data contents of other sectors. The device is fully erased when shipped from the factory.

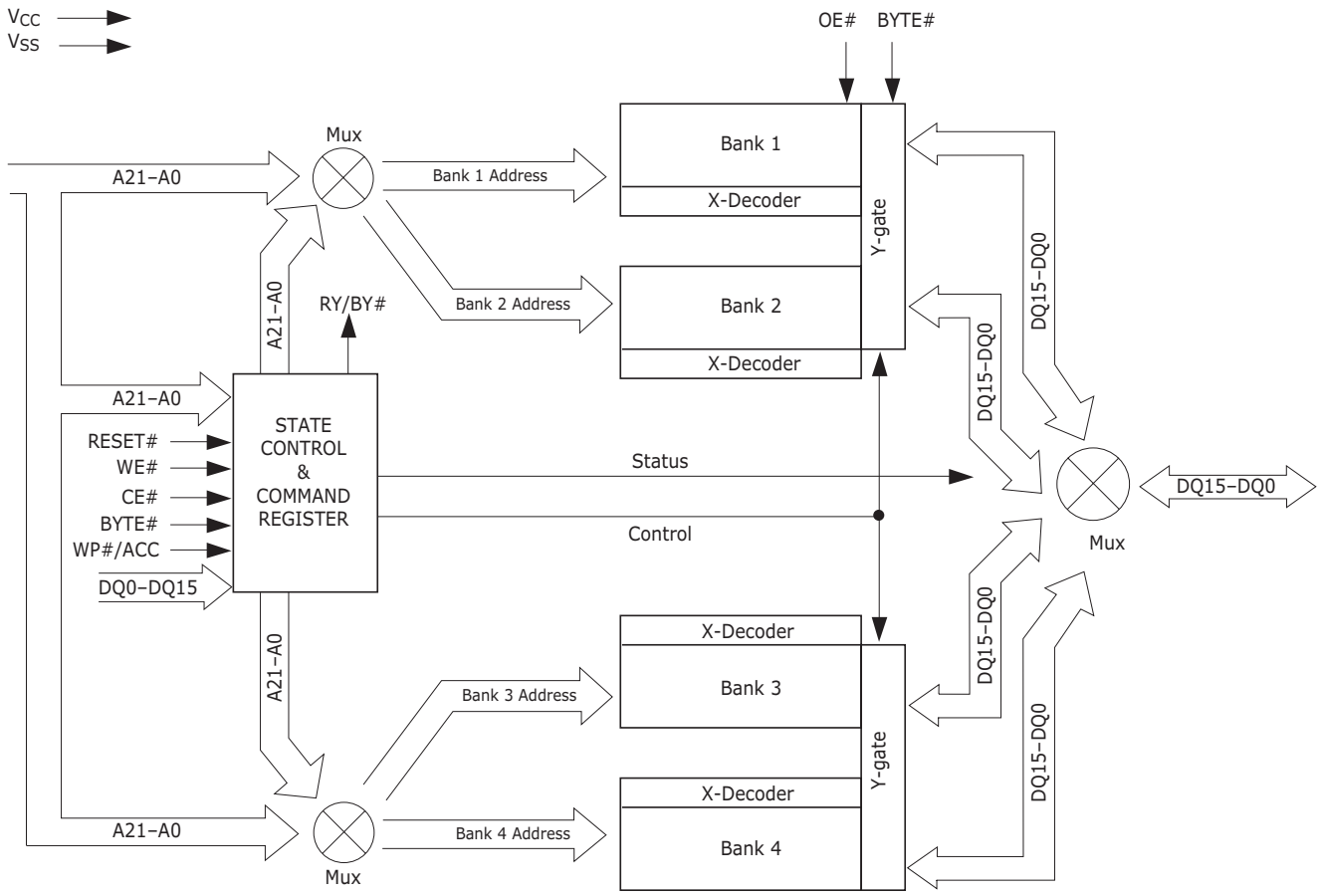
Hardware data protection measures include a low V_{CC} detector that automatically inhibits write operations during power transitions. The **hardware sector protection** feature disables both program and erase operations in any combination of the sectors of memory. This can be achieved in-system or via programming equipment.

The device offers two power-saving features. When addresses have been stable for a specified amount of time, the device enters the **automatic sleep mode**. The system can also place the device into the **standby mode**. Power consumption is greatly reduced in both modes.

Product Selector Guide

Part Number		S7IJLxxxHxx_00		
Speed Option	Standard Voltage Range: V_{CC} = 2.7–3.6 V	**55**	**70**	**85**
Max Access Time (ns), t_{ACC}		55	70	85
CE# Access (ns), t_{CE}		55	70	85
OE# Access (ns), t_{OE}		25	30	40

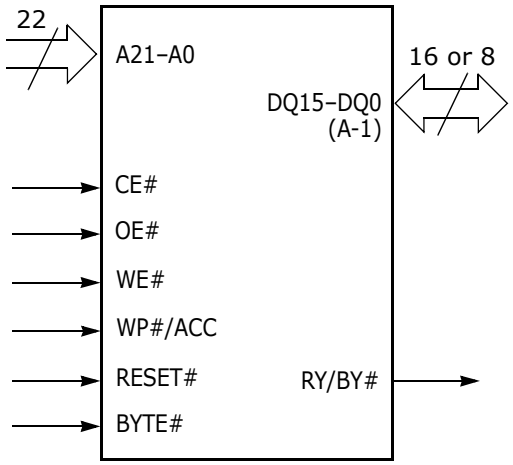
BLOCK DIAGRAM



Pin Description

A21–A0	=	22 Addresses
DQ14–DQ0	=	15 Data Inputs/Outputs (x16-only devices)
DQ15/A-1	=	DQ15 (Data Input/Output, word mode), A-1 (LSB Address Input, byte mode)
CE#	=	Chip Enable
OE#	=	Output Enable
WE#	=	Write Enable
WP#/ACC	=	Hardware Write Protect/ Acceleration Pin RESET#=Hardware Reset Pin, Active Low
BYTE#	=	Selects 8-bit or 16-bit mode
RY/BY#	=	Ready/Busy Output
V_{CC}	=	3.0 volt-only single power supply (see Product Selector Guide for speed options and voltage supply tolerances)
V_{SS}	=	Device Ground
NC	=	Pin Not Connected Internally

LOGIC SYMBOL



Device Bus Operations

This section describes the requirements and use of the device bus operations, which are initiated through the internal command register. The command register itself does not occupy any addressable memory location. The register is a latch used to store the commands, along with the address and data information needed to execute the command. The contents of the register serve as inputs to the internal state machine. The state machine outputs dictate the function of the device. Table 1 lists the device bus operations, the inputs and control levels they require, and the resulting output. The following subsections describe each of these operations in further detail.

Table I. S7IJLxxxHxx_00 Device Bus Operations

Operation	CE#	OE#	WE#	RESET#	WP#/ACC	Addresses (Note 2)	DQI5–DQ8		DQ7–DQ0
							BYTE# = V_{IH}	BYTE# = V_{IL}	
Read	L	L	H	H	L/H	A_{IN}	D_{OUT}	DQ14–DQ8 = High-Z, DQ15 = A-1	D_{OUT}
Write	L	H	L	H	(Note 3)	A_{IN}	D_{IN}		D_{IN}
Standby	V_{CC} ± 0.3 V	X	X	V_{CC} ± 0.3 V	L/H	X	High-Z	High-Z	High-Z
Output Disable	L	H	H	H	L/H	X	High-Z	High-Z	High-Z
Reset	X	X	X	L	L/H	X	High-Z	High-Z	High-Z
Sector Protect (Note 2)	L	H	L	V_{ID}	L/H	SA, A6 = L, A1 = H, A0 = L	X	X	D_{IN}
Sector Unprotect (Note 2)	L	H	L	V_{ID}	(Note 3)	SA, A6 = H, A1 = H, A0 = L	X	X	D_{IN}
Temporary Sector Unprotect	X	X	X	V_{ID}	(Note 3)	A_{IN}	D_{IN}	High-Z	D_{IN}

Legend: *L = Logic Low = V_{IL}, H = Logic High = V_{IH}, V_{ID} = 11.5–12.5 V, V_{HH} = 9.0 ± 0.5 V, X = Don't Care, SA = Sector Address, A_{IN} = Address In, D_{IN} = Data In, D_{OUT} = Data Out*

Notes:

1. *Addresses are A21:A0 in word mode (BYTE# = V_{IH}), A21:A-1 in byte mode (BYTE# = V_{IL}).*
2. *The sector protect and sector unprotect functions may also be implemented via programming equipment. See the "Sector/Sector Block Protection and Unprotection" section.*
3. *If WP#/ACC = V_{IL}, sectors 0, 1, 140, and 141 remain protected. If WP#/ACC = V_{IH}, protection on sectors 0, 1, 140, and 141 depends on whether they were last protected or unprotected using the method described in "Sector/Sector Block Protection and Unprotection". If WP#/ACC = V_{HH}, all sectors will be unprotected.*

Word/Byte Configuration

The BYTE# pin controls whether the device data I/O pins operate in the byte or word configuration. If the BYTE# pin is set at logic '1', the device is in word configuration, DQ15–DQ0 are active and controlled by CE# and OE#.

If the BYTE# pin is set at logic '0', the device is in byte configuration, and only data I/O pins DQ7–DQ0 are active and controlled by CE# and OE#. The data I/O pins DQ14–DQ8 are tri-stated, and the DQ15 pin is used as an input for the LSB (A-1) address function.

Requirements for Reading Array Data

To read array data from the outputs, the system must drive the CE# and OE# pins to V_{IL}. CE# is the power control and selects the device. OE# is the output control and gates array data to the output pins. WE# should remain at V_{IH}. The BYTE# pin determines whether the device outputs array data in words or bytes.

The internal state machine is set for reading array data upon device power-up, or after a hardware reset. This ensures that no spurious alteration of the memory content occurs during the power transition. No command is necessary in this mode to obtain array data. Standard microprocessor read cycles that assert valid addresses on the device address inputs produce valid data on the device data outputs. Each bank remains enabled for read access until the command register contents are altered.

Refer to the AC "Read-Only Operations" section table for timing specifications and to 14 for the timing diagram. I_{CC1} in the DC Characteristics table represents the active current specification for reading array data.

Writing Commands/Command Sequences

To write a command or command sequence (which includes programming data to the device and erasing sectors of memory), the system must drive WE# and CE# to V_{IL}, and OE# to V_{IH}.

For program operations, the BYTE# pin determines whether the device accepts program data in bytes or words. Refer to "Word/Byte Configuration" for more information.

The device features an **Unlock Bypass** mode to facilitate faster programming. Once a bank enters the Unlock Bypass mode, only two write cycles are required to program a word or byte, instead of four. The "Byte/Word Program Command Sequence" section has details on programming data to the device using both standard and Unlock Bypass command sequences.

An erase operation can erase one sector, multiple sectors, or the entire device. Table 3 indicates the address space that each sector occupies. Similarly, a "sector address" is the address bits required to uniquely select a sector. The "Command Definitions" section has details on erasing a sector or the entire chip, or suspending/resuming the erase operation.

The device address space is divided into four banks. A "bank address" is the address bits required to uniquely select a bank.

I_{CC2} in the DC Characteristics table represents the active current specification for the write mode. The "AC Characteristics" section contains timing specification tables and timing diagrams for write operations.

Accelerated Program Operation

The device offers accelerated program operations through the ACC function. This is one of two functions provided by the WP#/ACC pin. This function is primarily intended to allow faster manufacturing throughput at the factory.

If the system asserts V_{HH} on this pin, the device automatically enters the aforementioned Unlock Bypass mode, temporarily unprotects any protected sectors, and uses the higher voltage on the pin to reduce the time required for program operations. The system would use a two-cycle program command sequence as required by the Unlock Bypass mode. Removing V_{HH} from the WP#/ACC pin returns the device to normal operation. *Note that V_{HH} must not be asserted on WP#/ACC for operations other than accelerated programming, or device damage may result. In addition, the WP#/ACC pin must not be left floating or unconnected; inconsistent behavior of the device may result*. See "Write Protect (WP#)" on page 51. for related information.

Autoselect Functions

If the system writes the autoselect command sequence, the device enters the autoselect mode. The system can then read autoselect codes from the internal register (which is separate from the memory array) on DQ15–DQ0. Standard read cycle timings apply in this mode. Refer to the "Autoselect Mode" section and "Autoselect Command Sequence" section sections for more information.

Simultaneous Read/Write Operations with Zero Latency

This device is capable of reading data from one bank of memory while programming or erasing in the other bank of memory. An erase operation may also be suspended to read from or program to another location within the same bank (except the sector being erased). Figure 21 shows how read and write cycles may be initiated for simultaneous operation with zero latency. I_{CC6} and I_{CC7} in the "DC Characteristics" section table represent the current specifications for read-while-program and read-while-erase, respectively.

Standby Mode

When the system is not reading or writing to the device, it can place the device in the standby mode. In this mode, current consumption is greatly reduced, and the outputs are placed in the high impedance state, independent of the OE# input.

The device enters the CMOS standby mode when the CE# and RESET# pins are both held at V_{CC} ± 0.3 V. (Note that this is a more restricted voltage range than V_{IH}.) If CE# and RESET# are held at V_{IH}, but not within V_{CC} ± 0.3 V, the device will be in the standby mode, but the standby current will be greater. The device requires standard access time (t_{CE}) for read access when the device is in either of these standby modes, before it is ready to read data.

If the device is deselected during erasure or programming, the device draws active current until the operation is completed.

I_{CC3} in the "DC Characteristics" section table represents the standby current specification.

Automatic Sleep Mode

The automatic sleep mode minimizes Flash device energy consumption. The device automatically enables this mode when addresses remain stable for t_{ACC} + 30 ns. The automatic sleep mode is independent of the CE#, WE#, and OE# con-

trol signals. Standard address access timings provide new data when addresses are changed. While in sleep mode, output data is latched and always available to the system. I_{CC5} in the "DC Characteristics" section table represents the automatic sleep mode current specification.

RESET#: Hardware Reset Pin

The RESET# pin provides a hardware method of resetting the device to reading array data. When the RESET# pin is driven low for at least a period of t_{RP}, the device immediately terminates any operation in progress, tristates all output pins, and ignores all read/write commands for the duration of the RESET# pulse. The device also resets the internal state machine to reading array data. The operation that was interrupted should be reinitiated once the device is ready to accept another command sequence, to ensure data integrity.

Current is reduced for the duration of the RESET# pulse. When RESET# is held at V_{SS}±0.3 V, the device draws CMOS standby current (I_{CC4}). If RESET# is held at V_{IL} but not within V_{SS}±0.3 V, the standby current will be greater.

The RESET# pin may be tied to the system reset circuitry. A system reset would thus also reset the Flash memory, enabling the system to read the boot-up firmware from the Flash memory.

If RESET# is asserted during a program or erase operation, the RY/BY# pin remains a "0" (busy) until the internal reset operation is complete, which requires a time of t_{READY} (during Embedded Algorithms). The system can thus monitor RY/BY# to determine whether the reset operation is complete. If RESET# is asserted when a program or erase operation is not executing (RY/BY# pin is "1"), the reset operation is completed within a time of t_{READY} (not during Embedded Algorithms). The system can read data t_{RH} after the RESET# pin returns to V_{IH}.

Refer to the "AC Characteristics" section tables for RESET# parameters and to 15 for the timing diagram.

Output Disable Mode

When the OE# input is at V_{IH}, output from the device is disabled. The output pins are placed in the high impedance state.

Table 2. S29JL064H Sector Architecture

Bank	Sector	Sector Address A21–A12	Sector Size (Kbytes/ Kwords)	(x8) Address Range	(x16) Address Range
Bank 1	SA0	0000000000	8/4	000000h–001FFFh	00000h–00FFFh
	SA1	0000000001	8/4	002000h–003FFFh	01000h–01FFFh
	SA2	0000000010	8/4	004000h–005FFFh	02000h–02FFFh
	SA3	0000000011	8/4	006000h–007FFFh	03000h–03FFFh
	SA4	0000000100	8/4	008000h–009FFFh	04000h–04FFFh
	SA5	0000000101	8/4	00A000h–00BFFFh	05000h–05FFFh
	SA6	0000000110	8/4	00C000h–00DFFFh	06000h–06FFFh
	SA7	0000000111	8/4	00E000h–00FFFFh	07000h–07FFFh
	SA8	0000001xxx	64/32	010000h–01FFFFh	08000h–0FFFFh
	SA9	0000010xxx	64/32	020000h–02FFFFh	10000h–17FFFh
	SA10	0000011xxx	64/32	030000h–03FFFFh	18000h–1FFFFh
	SA11	0000100xxx	64/32	040000h–04FFFFh	20000h–27FFFh
	SA12	0000101xxx	64/32	050000h–05FFFFh	28000h–2FFFFh
	SA13	0000110xxx	64/32	060000h–06FFFFh	30000h–37FFFh
	SA14	0000111xxx	64/32	070000h–07FFFFh	38000h–3FFFFh
	SA15	0001000xxx	64/32	080000h–08FFFFh	40000h–47FFFh
	SA16	0001001xxx	64/32	090000h–09FFFFh	48000h–4FFFFh
	SA17	0001010xxx	64/32	0A0000h–0AFFFFh	50000h–57FFFh
	SA18	0001011xxx	64/32	0B0000h–0BFFFFh	58000h–5FFFFh
	SA19	0001100xxx	64/32	0C0000h–0CFFFFh	60000h–67FFFh
	SA20	0001101xxx	64/32	0D0000h–0DFFFFh	68000h–6FFFFh
	SA21	0001110xxx	64/32	0E0000h–0EFFFFh	70000h–77FFFh
	SA22	0001111xxx	64/32	0F0000h–0FFFFFh	78000h–7FFFFh

Table 2. S29JL064H Sector Architecture (Continued)

Bank	Sector	Sector Address A21–A12	Sector Size (Kbytes/ Kwords)	(x8) Address Range	(x16) Address Range
Bank 2	SA23	0010000xxx	64/32	100000h–10FFFFh	80000h–87FFFh
	SA24	0010001xxx	64/32	110000h–11FFFFh	88000h–8FFFFh
	SA25	0010010xxx	64/32	120000h–12FFFFh	90000h–97FFFh
	SA26	0010011xxx	64/32	130000h–13FFFFh	98000h–9FFFFh
	SA27	0010100xxx	64/32	140000h–14FFFFh	A0000h–A7FFFh
	SA28	0010101xxx	64/32	150000h–15FFFFh	A8000h–AFFFFh
	SA29	0010110xxx	64/32	160000h–16FFFFh	B0000h–B7FFFh
	SA30	0010111xxx	64/32	170000h–17FFFFh	B8000h–BFFFFh
	SA31	0011000xxx	64/32	180000h–18FFFFh	C0000h–C7FFFh
	SA32	0011001xxx	64/32	190000h–19FFFFh	C8000h–CFFFFh
	SA33	0011010xxx	64/32	1A0000h–1AFFFFh	D0000h–D7FFFh
	SA34	0011011xxx	64/32	1B0000h–1BFFFFh	D8000h–DFFFFh
	SA35	0011000xxx	64/32	1C0000h–1CFFFFh	E0000h–E7FFFh
	SA36	0011101xxx	64/32	1D0000h–1DFFFFh	E8000h–EFFFFh
	SA37	0011110xxx	64/32	1E0000h–1EFFFFh	F0000h–F7FFFh
	SA38	0011111xxx	64/32	1F0000h–1FFFFFh	F8000h–FFFFFh
	SA39	0100000xxx	64/32	200000h–20FFFFh	100000h–107FFFh
	SA40	0100001xxx	64/32	210000h–21FFFFh	108000h–10FFFFh
	SA41	0100010xxx	64/32	220000h–22FFFFh	110000h–117FFFh
	SA42	0101011xxx	64/32	230000h–23FFFFh	118000h–11FFFFh
	SA43	0100100xxx	64/32	240000h–24FFFFh	120000h–127FFFh
	SA44	0100101xxx	64/32	250000h–25FFFFh	128000h–12FFFFh
	SA45	0100110xxx	64/32	260000h–26FFFFh	130000h–137FFFh
	SA46	0100111xxx	64/32	270000h–27FFFFh	138000h–13FFFFh
	SA47	0101000xxx	64/32	280000h–28FFFFh	140000h–147FFFh
	SA48	0101001xxx	64/32	290000h–29FFFFh	148000h–14FFFFh
	SA49	0101010xxx	64/32	2A0000h–2AFFFFh	150000h–157FFFh
	SA50	0101011xxx	64/32	2B0000h–2BFFFFh	158000h–15FFFFh
	SA51	0101100xxx	64/32	2C0000h–2CFFFFh	160000h–167FFFh
	SA52	0101101xxx	64/32	2D0000h–2DFFFFh	168000h–16FFFFh
	SA53	0101110xxx	64/32	2E0000h–2EFFFFh	170000h–177FFFh
	SA54	0101111xxx	64/32	2F0000h–2FFFFFh	178000h–17FFFFh
	SA55	0110000xxx	64/32	300000h–30FFFFh	180000h–187FFFh
	SA56	0110001xxx	64/32	310000h–31FFFFh	188000h–18FFFFh
	SA57	0110010xxx	64/32	320000h–32FFFFh	190000h–197FFFh
	SA58	0110011xxx	64/32	330000h–33FFFFh	198000h–19FFFFh
	SA59	0110100xxx	64/32	340000h–34FFFFh	1A0000h–1A7FFFh
	SA60	0110101xxx	64/32	350000h–35FFFFh	1A8000h–1AFFFFh
	SA61	0110110xxx	64/32	360000h–36FFFFh	1B0000h–1B7FFFh
	SA62	0110111xxx	64/32	370000h–37FFFFh	1B8000h–1BFFFFh
	SA63	0111000xxx	64/32	380000h–38FFFFh	1C0000h–1C7FFFh
	SA64	0111001xxx	64/32	390000h–39FFFFh	1C8000h–1CFFFFh
	SA65	0111010xxx	64/32	3A0000h–3AFFFFh	1D0000h–1D7FFFh
	SA66	0111011xxx	64/32	3B0000h–3BFFFFh	1D8000h–1DFFFFh
	SA67	0111100xxx	64/32	3C0000h–3CFFFFh	1E0000h–1E7FFFh
	SA68	0111101xxx	64/32	3D0000h–3DFFFFh	1E8000h–1EFFFFh
	SA69	0111110xxx	64/32	3E0000h–3EFFFFh	1F0000h–1F7FFFh
	SA70	0111111xxx	64/32	3F0000h–3FFFFFh	1F8000h–1FFFFFh

Table 2. S29JL064H Sector Architecture (Continued)

Bank	Sector	Sector Address A21–A12	Sector Size (Kbytes/ Kwords)	(x8) Address Range	(x16) Address Range
Bank 3	SA71	1000000xxx	64/32	400000h–40FFFFh	200000h–207FFFh
	SA72	1000001xxx	64/32	410000h–41FFFFh	208000h–20FFFFh
	SA73	1000010xxx	64/32	420000h–42FFFFh	210000h–217FFFh
	SA74	1000011xxx	64/32	430000h–43FFFFh	218000h–21FFFFh
	SA75	1000100xxx	64/32	440000h–44FFFFh	220000h–227FFFh
	SA76	1000101xxx	64/32	450000h–45FFFFh	228000h–22FFFFh
	SA77	1000110xxx	64/32	460000h–46FFFFh	230000h–237FFFh
	SA78	1000111xxx	64/32	470000h–47FFFFh	238000h–23FFFFh
	SA79	1001000xxx	64/32	480000h–48FFFFh	240000h–247FFFh
	SA80	1001001xxx	64/32	490000h–49FFFFh	248000h–24FFFFh
	SA81	1001010xxx	64/32	4A0000h–4AFFFFh	250000h–257FFFh
	SA82	1001011xxx	64/32	4B0000h–4BFFFFh	258000h–25FFFFh
	SA83	1001100xxx	64/32	4C0000h–4CFFFFh	260000h–267FFFh
	SA84	1001101xxx	64/32	4D0000h–4DFFFFh	268000h–26FFFFh
	SA85	1001110xxx	64/32	4E0000h–4EFFFFh	270000h–277FFFh
	SA86	1001111xxx	64/32	4F0000h–4FFFFFh	278000h–27FFFFh
	SA87	1010000xxx	64/32	500000h–50FFFFh	280000h–28FFFFh
	SA88	1010001xxx	64/32	510000h–51FFFFh	288000h–28FFFFh
	SA89	1010010xxx	64/32	520000h–52FFFFh	290000h–297FFFh
	SA90	1010011xxx	64/32	530000h–53FFFFh	298000h–29FFFFh
	SA91	1010100xxx	64/32	540000h–54FFFFh	2A0000h–2A7FFFh
	SA92	1010101xxx	64/32	550000h–55FFFFh	2A8000h–2AFFFFh
	SA93	1010110xxx	64/32	560000h–56FFFFh	2B0000h–2B7FFFh
	SA94	1010111xxx	64/32	570000h–57FFFFh	2B8000h–2BFFFFh
	SA95	1011000xxx	64/32	580000h–58FFFFh	2C0000h–2C7FFFh
	SA96	1011001xxx	64/32	590000h–59FFFFh	2C8000h–2CFFFFh
	SA97	1011010xxx	64/32	5A0000h–5AFFFFh	2D0000h–2D7FFFh
	SA98	1011011xxx	64/32	5B0000h–5BFFFFh	2D8000h–2DFFFFh
	SA99	1011100xxx	64/32	5C0000h–5CFFFFh	2E0000h–2E7FFFh
	SA100	1011101xxx	64/32	5D0000h–5DFFFFh	2E8000h–2EFFFFh
	SA101	1011110xxx	64/32	5E0000h–5EFFFFh	2F0000h–2FFFFFh
	SA102	1011111xxx	64/32	5F0000h–5FFFFFh	2F8000h–2FFFFFh
	SA103	1100000xxx	64/32	600000h–60FFFFh	300000h–307FFFh
	SA104	1100001xxx	64/32	610000h–61FFFFh	308000h–30FFFFh
	SA105	1100010xxx	64/32	620000h–62FFFFh	310000h–317FFFh
	SA106	1100011xxx	64/32	630000h–63FFFFh	318000h–31FFFFh
	SA107	1100100xxx	64/32	640000h–64FFFFh	320000h–327FFFh
	SA108	1100101xxx	64/32	650000h–65FFFFh	328000h–32FFFFh
	SA109	1100110xxx	64/32	660000h–66FFFFh	330000h–337FFFh
	SA110	1100111xxx	64/32	670000h–67FFFFh	338000h–33FFFFh
	SA111	1101000xxx	64/32	680000h–68FFFFh	340000h–347FFFh
	SA112	1101001xxx	64/32	690000h–69FFFFh	348000h–34FFFFh
	SA113	1101010xxx	64/32	6A0000h–6AFFFFh	350000h–357FFFh
	SA114	1101011xxx	64/32	6B0000h–6BFFFFh	358000h–35FFFFh
	SA115	1101100xxx	64/32	6C0000h–6CFFFFh	360000h–367FFFh
	SA116	1101101xxx	64/32	6D0000h–6DFFFFh	368000h–36FFFFh
	SA117	1101110xxx	64/32	6E0000h–6EFFFFh	370000h–377FFFh
	SA118	1101111xxx	64/32	6F0000h–6FFFFFh	378000h–37FFFFh

Table 2. S29JL064H Sector Architecture (Continued)

Bank	Sector	Sector Address A21–A12	Sector Size (Kbytes/ Kwords)	(x8) Address Range	(x16) Address Range
Bank 4	SA119	1110000xxx	64/32	700000h–70FFFFh	380000h–387FFFh
	SA120	1110001xxx	64/32	710000h–71FFFFh	388000h–38FFFFh
	SA121	1110010xxx	64/32	720000h–72FFFFh	390000h–397FFFh
	SA122	1110011xxx	64/32	730000h–73FFFFh	398000h–39FFFFh
	SA123	1110100xxx	64/32	740000h–74FFFFh	3A0000h–3A7FFFh
	SA124	1110101xxx	64/32	750000h–75FFFFh	3A8000h–3AFFFFh
	SA125	1110110xxx	64/32	760000h–76FFFFh	3B0000h–3B7FFFh
	SA126	1110111xxx	64/32	770000h–77FFFFh	3B8000h–3BFFFFh
	SA127	1111000xxx	64/32	780000h–78FFFFh	3C0000h–3C7FFFh
	SA128	1111001xxx	64/32	790000h–79FFFFh	3C8000h–3CFFFFh
	SA129	1111010xxx	64/32	7A0000h–7AFFFFh	3D0000h–3D7FFFh
	SA130	1111011xxx	64/32	7B0000h–7BFFFFh	3D8000h–3DFFFFh
	SA131	1111100xxx	64/32	7C0000h–7CFFFFh	3E0000h–3E7FFFh
	SA132	1111101xxx	64/32	7D0000h–7DFFFFh	3E8000h–3EFFFFh
	SA133	1111110xxx	64/32	7E0000h–7EFFFFh	3F0000h–3F7FFFh
	SA134	1111111000	8/4	7F0000h–7F1FFFh	3F8000h–3F8FFFh
	SA135	1111111001	8/4	7F2000h–7F3FFFh	3F9000h–3F9FFFh
	SA136	1111111010	8/4	7F4000h–7F5FFFh	3FA000h–3FAFFFh
	SA137	1111111011	8/4	7F6000h–7F7FFFh	3FB000h–3FBFFFh
	SA138	1111111100	8/4	7F8000h–7F9FFFh	3FC000h–3FCFFFh
	SA139	1111111101	8/4	7FA000h–7FBFFFh	3FD000h–3FDFFFh
	SA140	1111111110	8/4	7FC000h–7FDFFFh	3FE000h–3FEFFFh
	SA141	1111111111	8/4	7FE000h–7FFFFFh	3FF000h–3FFFFFh

Note: *The address range is A21:A-1 in byte mode (BYTE#=V_{IL}) or A21:A0 in word mode (BYTE#=V_{IH}).*

Table 3. Bank Address

Bank	A2I–AI9
1	000
2	001, 010, 011
3	100, 101, 110
4	111

Table 4. SecSi™ Sector Addresses

Device	Sector Size	(x8) Address Range	(x16) Address Range
S29JL064H	256 bytes	000000h–0000FFh	000000h–00007Fh

Autoselect Mode

The autoselect mode provides manufacturer and device identification, and sector protection verification, through identifier codes output on DQ7–DQ0. This mode is primarily intended for programming equipment to automatically match a device to be programmed with its corresponding programming algorithm. However, the autoselect codes can also be accessed in-system through the command register.

Sector/Sector Block Protection and Unprotection

(Note: For the following discussion, the term "sector" applies to both sectors and sector blocks. A sector block consists of two or more adjacent sectors that are protected or unprotected at the same time (see Table 5).

The hardware sector protection feature disables both program and erase operations in any sector. The hardware sector unprotection feature re-enables both program and erase operations in previously protected sectors. Sector protection/unprotection can be implemented via two methods.

Table 5. S7IJLxxxHxx_00 Boot Sector/Sector Block Addresses for Protection/Unprotection

Sector	A21–A12	Sector/ Sector Block Size
SA0	0000000000	8 Kbytes
SA1	0000000001	8 Kbytes
SA2	0000000010	8 Kbytes
SA3	0000000011	8 Kbytes
SA4	0000000100	8 Kbytes
SA5	0000000101	8 Kbytes
SA6	0000000110	8 Kbytes
SA7	0000000111	8 Kbytes
SA8–SA10	0000001XXX, 0000010XXX, 0000011XXX,	192 (3x64) Kbytes
SA11–SA14	00001XXXXX	256 (4x64) Kbytes
SA15–SA18	00010XXXXX	256 (4x64) Kbytes
SA19–SA22	00011XXXXX	256 (4x64) Kbytes
SA23–SA26	00100XXXXX	256 (4x64) Kbytes
SA27-SA30	00101XXXXX	256 (4x64) Kbytes
SA31-SA34	00110XXXXX	256 (4x64) Kbytes
SA35-SA38	00111XXXXX	256 (4x64) Kbytes
SA39-SA42	01000XXXXX	256 (4x64) Kbytes
SA43-SA46	01001XXXXX	256 (4x64) Kbytes
SA47-SA50	01010XXXXX	256 (4x64) Kbytes
SA51-SA54	01011XXXXX	256 (4x64) Kbytes
SA55–SA58	01100XXXXX	256 (4x64) Kbytes
SA59–SA62	01101XXXXX	256 (4x64) Kbytes
SA63–SA66	01110XXXXX	256 (4x64) Kbytes
SA67–SA70	01111XXXXX	256 (4x64) Kbytes
SA71–SA74	10000XXXXX	256 (4x64) Kbytes
SA75–SA78	10001XXXXX	256 (4x64) Kbytes
SA79–SA82	10010XXXXX	256 (4x64) Kbytes
SA83–SA86	10011XXXXX	256 (4x64) Kbytes
SA87–SA90	10100XXXXX	256 (4x64) Kbytes
SA91–SA94	10101XXXXX	256 (4x64) Kbytes
SA95–SA98	10110XXXXX	256 (4x64) Kbytes
SA99–SA102	10111XXXXX	256 (4x64) Kbytes
SA103–SA106	11000XXXXX	256 (4x64) Kbytes

Table 5. S7IJLxxxHxx_00 Boot Sector/Sector Block Addresses for Protection/Unprotection (Continued)

Sector	A21–A12	Sector/ Sector Block Size
SA107–SA110	11001XXXXX	256 (4x64) Kbytes
SA111–SA114	11010XXXXX	256 (4x64) Kbytes
SA115–SA118	11011XXXXX	256 (4x64) Kbytes
SA119–SA122	11100XXXXX	256 (4x64) Kbytes
SA123–SA126	11101XXXXX	256 (4x64) Kbytes
SA127–SA130	11110XXXXX	256 (4x64) Kbytes
SA131–SA133	1111100XXX, 1111101XXX, 1111110XXX	192 (3x64) Kbytes
SA134	1111111000	8 Kbytes
SA135	1111111001	8 Kbytes
SA136	1111111010	8 Kbytes
SA137	1111111011	8 Kbytes
SA138	1111111100	8 Kbytes
SA139	1111111101	8 Kbytes
SA140	1111111110	8 Kbytes
SA141	1111111111	8 Kbytes

Sector protect/Sector Unprotect requires V_{ID} on the RESET# pin only, and can be implemented either in-system or via programming equipment. Figure 2 shows the algorithms and Figure 26 shows the timing diagram. For sector unprotect, all unprotected sectors must first be protected prior to the first sector unprotect write cycle. *Note that the sector unprotect algorithm unprotects all sectors in parallel. All previously protected sectors must be individually re-protected.* To change data in protected sectors efficiently, the temporary sector unprotect function is available. See "Temporary Sector Unprotect" .

The device is shipped with all sectors unprotected. Optional Spansion programming service enable programming and protecting sectors at the factory prior to shipping the device. Contact your local sales office for details.

It is possible to determine whether a sector is protected or unprotected. See the "Autoselect Mode" section section for details.

Write Protect (WP#)

The Write Protect function provides a hardware method of protecting without using V_{ID}. This function is one of two provided by the WP#/ACC pin.

If the system asserts V_{IL} on the WP#/ACC pin, the device disables program and erase functions in sectors 0, 1, 140, and 141, independently of whether those sectors were protected or unprotected using the method described in "Sector/ Sector Block Protection and Unprotection".

If the system asserts V_{IH} on the WP#/ACC pin, the device reverts to whether sectors 0, 1, 140, and 141 were last set to be protected or unprotected. That is, sector protection or unprotection for these sectors depends on whether they were last protected or unprotected using the method described in "Sector/Sector Block Protection and Unprotection".

Note that the WP#/ACC pin must not be left floating or unconnected; inconsistent behavior of the device may result.

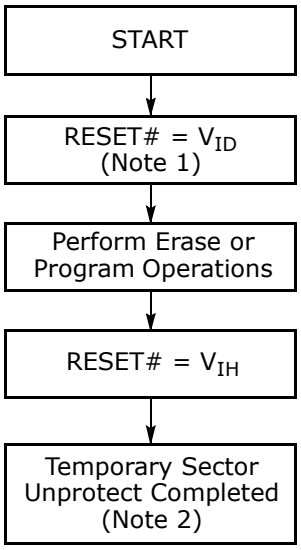
Table 6. WP#/ACC Modes

WP# Input Voltage	Device Mode
V_{IL}	Disables programming and erasing in SA0, SA1, SA140, and SA141
V_{IH}	Enables programming and erasing in SA0, SA1, SA140, and SA141, dependent on whether they were last protected or unprotected.
V_{HH}	Enables accelerated progamming (ACC). See "Accelerated Program Operation" on page 44..

Temporary Sector Unprotect

(Note: For the following discussion, the term "sector" applies to both sectors and sector blocks. A sector block consists of two or more adjacent sectors that are protected or unprotected at the same time (see Table 5).

This feature allows temporary unprotection of previously protected sectors to change data in-system. The Temporary Sector Unprotect mode is activated by setting the RESET# pin to "V_{ID}" section. During this mode, formerly protected sectors can be programmed or erased by selecting the sector addresses. Once V_{ID} is removed from the RESET# pin, all the previously protected sectors are protected again. Figure 2 shows the algorithm, and Figure 25 shows the timing diagrams, for this feature. If the WP#/ACC pin is at V_{IL}, sectors 0, 1, 140, and 141 will remain protected during the Temporary sector Unprotect mode.



Notes:

1. *All protected sectors unprotected (If WP#/ACC = V_{IL}, sectors 0, 1, 140, and 141 will remain protected).*
2. *All previously protected sectors are protected once again.*

Figure I. Temporary Sector Unprotect Operation

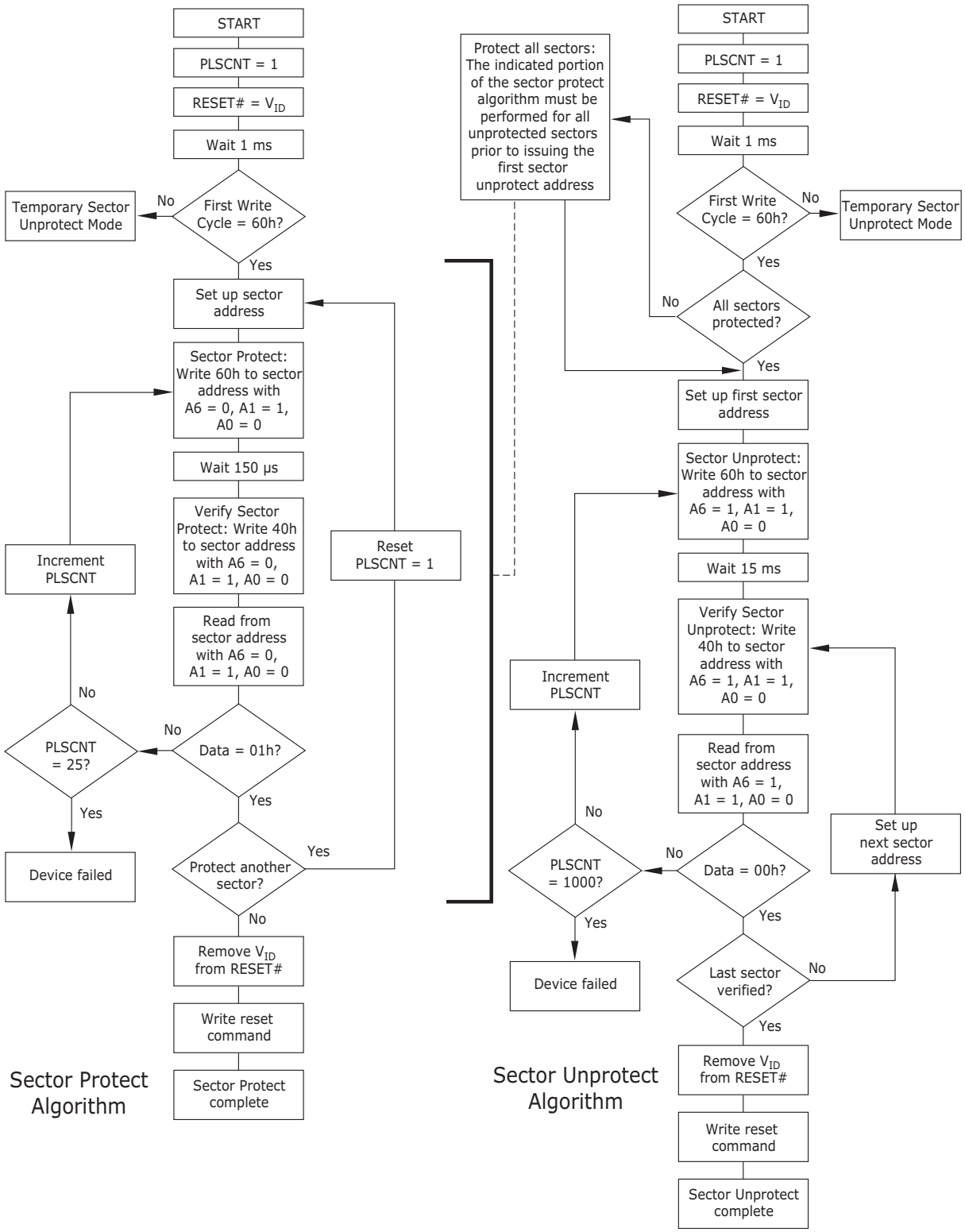


Figure 2. In-System Sector Protect/Unprotect Algorithms

SecSi™ (Secured Silicon) Sector Flash Memory Region

The SecSi (Secured Silicon) Sector feature provides a Flash memory region that enables permanent part identification through an Electronic Serial Number (ESN). The SecSi Sector is 256 bytes in length, and uses a SecSi Sector Indicator

Bit (DQ7) to indicate whether or not the SecSi Sector is locked when shipped from the factory. This bit is permanently set at the factory and cannot be changed, which prevents cloning of a factory locked part. This ensures the security of the ESN once the product is shipped to the field.

The product is available with the SecSi Sector either factory locked or customer lockable. The factory-locked version is always protected when shipped from the factory, and has the SecSi (Secured Silicon) Sector Indicator Bit permanently set to a "1." The customer-lockable version is shipped with the SecSi Sector unprotected, allowing customers to utilize the that sector in any manner they choose. The customer-lockable version has the SecSi (Secured Silicon) Sector Indicator Bit permanently set to a "0." Thus, the SecSi Sector Indicator Bit prevents customer-lockable devices from being used to replace devices that are factory locked. The SecSi Customer Indicator Bit (DQ6) is permanently set to 1 if the part has been customer locked, permanently set to 0 if the part has been factory locked, and is 0 if customer lockable.

The system accesses the SecSi Sector Secure through a command sequence (see "Enter SecSi™ Sector/Exit SecSi Sector Command Sequence"). After the system has written the Enter SecSi Sector command sequence, it may read the SecSi Sector by using the addresses normally occupied by the boot sectors. This mode of operation continues until the system issues the Exit SecSi Sector command sequence, or until power is removed from the device. On power-up, or following a hardware reset, the device reverts to sending commands to the first 256 bytes of Sector 0. *Note that the ACC function and unlock bypass modes are not available when the SecSi Sector is enabled.*

Factory Locked: SecSi Sector Programmed and Protected At the Factory

In a factory locked device, the SecSi Sector is protected when the device is shipped from the factory. The SecSi Sector cannot be modified in any way. The device is preprogrammed with both a random number and a secure ESN. The 8-word random number is at addresses 000000h–000007h in word mode (or 000000h–00000Fh in byte mode). The secure ESN is programmed in the next 8 words at addresses 000008h–00000Fh (or 000010h–00001Fh in byte mode). The device is available preprogrammed with one of the following:

- A random, secure ESN only
- Customer code through Spansion programming services
- Both a random, secure ESN and customer code through Spansion programming services

Contact an your local sales office for details on using Spansion programming services.

Customer Lockable: SecSi Sector NOT Programmed or Protected At the Factory

If the security feature is not required, the SecSi Sector can be treated as an additional Flash memory space. The SecSi Sector can be read any number of times, but can be programmed and locked only once. Note that the accelerated programming (ACC) and unlock bypass functions are not available when programming the SecSi Sector.

The SecSi Sector area can be protected using one of the following procedures:

- Write the three-cycle Enter SecSi Sector Region command sequence, and then follow the in-system sector protect algorithm as shown in Figure 2, except that *RESET# may be at either V_{IH} or V_{ID}*. This allows in-system protec-

tion of the SecSi Sector Region without raising any device pin to a high voltage. Note that this method is only applicable to the SecSi Sector.

- To verify the protect/unprotect status of the SecSi Sector, follow the algorithm shown in Figure 3.

Once the SecSi Sector is locked and verified, the system must write the Exit SecSi Sector Region command sequence to return to reading and writing the remainder of the array.

The SecSi Sector lock must be used with caution since, once locked, there is no procedure available for unlocking the SecSi Sector area and none of the bits in the SecSi Sector memory space can be modified in any way.

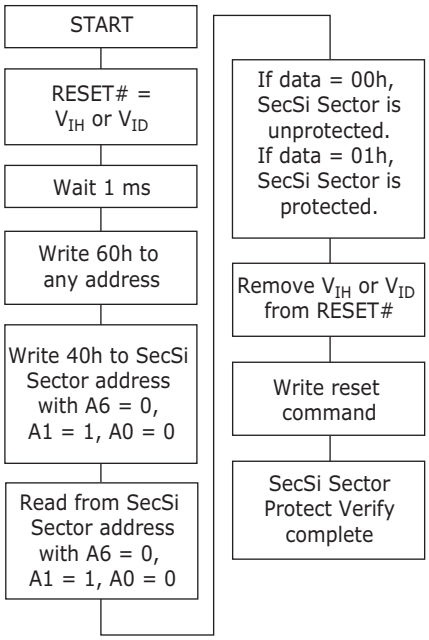


Figure 3. SecSi Sector Protect Verify

Hardware Data Protection

The command sequence requirement of unlock cycles for programming or erasing provides data protection against inadvertent writes (refer to Table 11 for command definitions). In addition, the following hardware data protection measures prevent accidental erasure or programming, which might otherwise be caused by spurious system level signals during V_{CC} power-up and power-down transitions, or from system noise.

Low V_{CC} Write Inhibit

When V_{CC} is less than V_{LKO}, the device does not accept any write cycles. This protects data during V_{CC} power-up and power-down. The command register and all internal program/erase circuits are disabled, and the device resets to the read mode. Subsequent writes are ignored until V_{CC} is greater than V_{LKO}. The system must provide the proper signals to the control pins to prevent unintentional writes when V_{CC} is greater than V_{LKO}.

Write Pulse "Glitch" Protection

Noise pulses of less than 5 ns (typical) on OE#, CE# or WE# do not initiate a write cycle.

Logical Inhibit

Write cycles are inhibited by holding any one of OE# = V_{IL}, CE# = V_{IH} or WE# = V_{IH}. To initiate a write cycle, CE# and WE# must be a logical zero while OE# is a logical one.

Power-Up Write Inhibit

If WE# = CE# = V_{IL} and OE# = V_{IH} during power up, the device does not accept commands on the rising edge of WE#. The internal state machine is automatically reset to the read mode on power-up.

Common Flash Memory Interface (CFI)

The Common Flash Interface (CFI) specification outlines device and host system software interrogation handshake, which allows specific vendor-specified software algorithms to be used for entire families of devices. Software support can then be device-independent, JEDEC ID-independent, and forward- and backward-compatible for the specified flash device families. Flash vendors can standardize their existing interfaces for long-term compatibility.

This device enters the CFI Query mode when the system writes the CFI Query command, 98h, to address 55h in word mode (or address AAh in byte mode), any time the device is ready to read array data. The system can read CFI information at the addresses given in Tables 7–10. To terminate reading CFI data, the system must write the reset command.The CFI Query mode is not accessible when the device is executing an Embedded Program or embedded Erase algorithm.

The system can also write the CFI query command when the device is in the autoselect mode. The device enters the CFI query mode, and the system can read CFI data at the addresses given in Tables 7–10. The system must write the reset command to reading array data.

For further information, please refer to the CFI Specification and CFI Publication 100. Contact your local sales office for copies of these documents.

Table 7. CFI Query Identification String

Addresses (Word Mode)	Addresses (Byte Mode)	Data	Description
10h 11h 12h	20h 22h 24h	0051h 0052h 0059h	Query Unique ASCII string “QRY”
13h 14h	26h 28h	0002h 0000h	Primary OEM Command Set
15h 16h	2Ah 2Ch	0040h 0000h	Address for Primary Extended Table
17h 18h	2Eh 30h	0000h 0000h	Alternate OEM Command Set (00h = none exists)
19h 1Ah	32h 34h	0000h 0000h	Address for Alternate OEM Extended Table (00h = none exists)

Table 8. System Interface String

Addresses (Word Mode)	Addresses (Byte Mode)	Data	Description
1Bh	36h	0027h	V_{CC} Min. (write/erase) D7–D4: volt, D3–D0: 100 millivolt
1Ch	38h	0036h	V_{CC} Max. (write/erase) D7–D4: volt, D3–D0: 100 millivolt
1Dh	3Ah	0000h	V_{PP} Min. voltage (00h = no V_{PP} pin present)
1Eh	3Ch	0000h	V_{PP} Max. voltage (00h = no V_{PP} pin present)
1Fh	3Eh	0003h	Typical timeout per single byte/word write 2^N µs
20h	40h	0000h	Typical timeout for Min. size buffer write 2^N µs (00h = not supported)
21h	42h	0009h	Typical timeout per individual block erase 2^N ms
22h	44h	0000h	Typical timeout for full chip erase 2^N ms (00h = not supported)
23h	46h	0005h	Max. timeout for byte/word write 2^N times typical
24h	48h	0000h	Max. timeout for buffer write 2^N times typical
25h	4Ah	0004h	Max. timeout per individual block erase 2^N times typical
26h	4Ch	0000h	Max. timeout for full chip erase 2^N times typical (00h = not supported)

Table 9. Device Geometry Definition

Addresses (Word Mode)	Addresses (Byte Mode)	Data	Description
27h	4Eh	0017h	Device Size = 2^N byte
28h 29h	50h 52h	0002h 0000h	Flash Device Interface description (refer to CFI publication 100)
2Ah 2Bh	54h 56h	0000h 0000h	Max. number of byte in multi-byte write = 2^N (00h = not supported)
2Ch	58h	0003h	Number of Erase Block Regions within device
2Dh 2Eh 2Fh 30h	5Ah 5Ch 5Eh 60h	0007h 0000h 0020h 0000h	Erase Block Region 1 Information (refer to the CFI specification or CFI publication 100)
31h 32h 33h 34h	62h 64h 66h 68h	007Dh 0000h 0000h 0001h	Erase Block Region 2 Information (refer to the CFI specification or CFI publication 100)
35h 36h 37h 38h	6Ah 6Ch 6Eh 70h	0007h 0000h 0020h 0000h	Erase Block Region 3 Information (refer to the CFI specification or CFI publication 100)
39h 3Ah 3Bh 3Ch	72h 74h 76h 78h	0000h 0000h 0000h 0000h	Erase Block Region 4 Information (refer to the CFI specification or CFI publication 100)

Table 10. Primary Vendor-Specific Extended Query

Addresses (Word Mode)	Addresses (Byte Mode)	Data	Description
40h 41h 42h	80h 82h 84h	0050h 0052h 0049h	Query-unique ASCII string "PRI"
43h	86h	0031h	Major version number, ASCII (reflects modifications to the silicon)
44h	88h	0033h	Minor version number, ASCII (reflects modifications to the CFI table)
45h	8Ah	000Ch	Address Sensitive Unlock (Bits 1-0) 0 = Required, 1 = Not Required Silicon Revision Number (Bits 7-2)
46h	8Ch	0002h	Erase Suspend 0 = Not Supported, 1 = To Read Only, 2 = To Read & Write
47h	8Eh	0001h	Sector Protect 0 = Not Supported, X = Number of sectors in per group
48h	90h	0001h	Sector Temporary Unprotect 00 = Not Supported, 01 = Supported
49h	92h	0004h	Sector Protect/Unprotect scheme 01 =29F040 mode, 02 = 29F016 mode, 03 = 29F400, 04 = 29LV800 mode
4Ah	94h	0077h	Simultaneous Operation 00 = Not Supported, X = Number of Sectors (excluding Bank 1)
4Bh	96h	0000h	Burst Mode Type 00 = Not Supported, 01 = Supported
4Ch	98h	0000h	Page Mode Type 00 = Not Supported, 01 = 4 Word Page, 02 = 8 Word Page
4Dh	9Ah	0085h	ACC (Acceleration) Supply Minimum 00h = Not Supported, D7-D4: Volt, D3-D0: 100 mV
4Eh	9Ch	0095h	ACC (Acceleration) Supply Maximum 00h = Not Supported, D7-D4: Volt, D3-D0: 100 mV
4Fh	9Eh	0001h	Top/Bottom Boot Sector Flag 00h = Uniform device, 01h = 8 x 8 Kbyte Sectors, Top And Bottom Boot with Write Protect, 02h = Bottom Boot Device, 03h = Top Boot Device, 04h= Both Top and Bottom
50h	A0h	0001h	Program Suspend 0 = Not supported, 1 = Supported
57h	AEh	0004h	Bank Organization 00 = Data at 4Ah is zero, X = Number of Banks
58h	B0h	0017h	Bank 1 Region Information X = Number of Sectors in Bank 1
59h	B2h	0030h	Bank 2 Region Information X = Number of Sectors in Bank 2
5Ah	B4h	0030h	Bank 3 Region Information X = Number of Sectors in Bank 3
5Bh	B6h	0017h	Bank 4 Region Information X = Number of Sectors in Bank 4

Command Definitions

Writing specific address and data commands or sequences into the command register initiates device operations. Table 11 defines the valid register command sequences. *Writing incorrect address and data values or writing them in the improper sequence may place the device in an unknown state. A reset command is then required to return the device to reading array data.*

All addresses are latched on the falling edge of WE# or CE#, whichever happens later. All data is latched on the rising edge of WE# or CE#, whichever happens first. Refer to the "AC Characteristics" section for timing diagrams.

Reading Array Data

The device is automatically set to reading array data after device power-up. No commands are required to retrieve data. Each bank is ready to read array data after completing an Embedded Program or Embedded Erase algorithm.

After the device accepts an Erase Suspend command, the corresponding bank enters the erase-suspend-read mode, after which the system can read data from any non-erase-suspended sector within the same bank. The system can read array data using the standard read timing, except that if it reads at an address within erase-suspended sectors, the device outputs status data. After completing a programming operation in the Erase Suspend mode, the system may once again read array data with the same exception. See the "Erase Suspend/Erase Resume Commands" section section for more information.

The system *must* issue the reset command to return a bank to the read (or erase-suspend-read) mode if DQ5 goes high during an active program or erase operation, or if the bank is in the autoselect mode. See the next section, "Reset Command" section, for more information.

See also "Requirements for Reading Array Data" section in the "Device Bus Operations" section section for more information. The "Read-Only Operations" section table provides the read parameters, and 14 shows the timing diagram.

Reset Command

Writing the reset command resets the banks to the read or erase-suspend-read mode. Address bits are don't cares for this command.

The reset command may be written between the sequence cycles in an erase command sequence before erasing begins. This resets the bank to which the system was writing to the read mode. Once erasure begins, however, the device ignores reset commands until the operation is complete.

The reset command may be written between the sequence cycles in a program command sequence before programming begins. This resets the bank to which the system was writing to the read mode. If the program command sequence is written to a bank that is in the Erase Suspend mode, writing the reset command returns that bank to the erase-suspend-read mode. Once programming begins, however, the device ignores reset commands until the operation is complete.

The reset command may be written between the sequence cycles in an autoselect command sequence. Once in the autoselect mode, the reset command must be written to return to the read mode. If a bank entered the autoselect mode while in the Erase Suspend mode, writing the reset command returns that bank to the erase-suspend-read mode.

If DQ5 goes high during a program or erase operation, writing the reset command returns the banks to the read mode (or erase-suspend-read mode if that bank was in Erase Suspend).

Autoselect Command Sequence

The autoselect command sequence allows the host system to access the manufacturer and device codes, and determine whether or not a sector is protected. The autoselect command sequence may be written to an address within a bank that is either in the read or erase-suspend-read mode. The autoselect command may not be written while the device is actively programming or erasing in another bank.

The autoselect command sequence is initiated by first writing two unlock cycles. This is followed by a third write cycle that contains the bank address and the autoselect command. The bank then enters the autoselect mode. The system may read any number of autoselect codes without reinitiating the command sequence.

Table 11 shows the address and data requirements. To determine sector protection information, the system must write to the appropriate bank address (BA) and sector address (SA). Table 3 shows the address range and bank number associated with each sector.

The system must write the reset command to return to the read mode (or erase-suspend-read mode if the bank was previously in Erase Suspend).

Enter SecSi™ Sector/Exit SecSi Sector Command Sequence

The SecSi Sector region provides a secured data area containing a random, sixteen-byte electronic serial number (ESN). The system can access the SecSi Sector region by issuing the three-cycle Enter SecSi Sector command sequence. The device continues to access the SecSi Sector region until the system issues the four-cycle Exit SecSi Sector command sequence. The Exit SecSi Sector command sequence returns the device to normal operation. The SecSi Sector is not accessible when the device is executing an Embedded Program or embedded Erase algorithm. Table 11 shows the address and data requirements for both command sequences. See also "SecSi™ (Secured Silicon) Sector Flash Memory Region" for further information. *Note that the ACC function and unlock bypass modes are not available when the SecSi Sector is enabled.*

Byte/Word Program Command Sequence

The system may program the device by word or byte, depending on the state of the BYTE# pin. Programming is a four-bus-cycle operation. The program command sequence is initiated by writing two unlock write cycles, followed by the program set-up command. The program address and data are written next, which in turn initiate the Embedded Program algorithm. The system is *not* required to provide further controls or timings. The device automatically provides internally generated program pulses and verifies the programmed cell margin. Table 11 shows the address and data requirements for the byte program command sequence.

When the Embedded Program algorithm is complete, that bank then returns to the read mode and addresses are no longer latched. The system can determine the status of the program operation by using DQ7, DQ6, or RY/BY#. Refer to the "Write Operation Status" section section for information on these status bits.

Any commands written to the device during the Embedded Program Algorithm are ignored. Note that a **hardware reset** immediately terminates the program

operation. The program command sequence should be reinitiated once that bank has returned to the read mode, to ensure data integrity. *Note that the SecSi Sector, autoselect, and CFI functions are unavailable when a program operation is in progress.*

Programming is allowed in any sequence and across sector boundaries. **A bit cannot be programmed from "0" back to a "1."** Attempting to do so may cause that bank to set DQ5 = 1, or cause the DQ7 and DQ6 status bits to indicate the operation was successful. However, a succeeding read will show that the data is still "0." Only erase operations can convert a "0" to a "1."

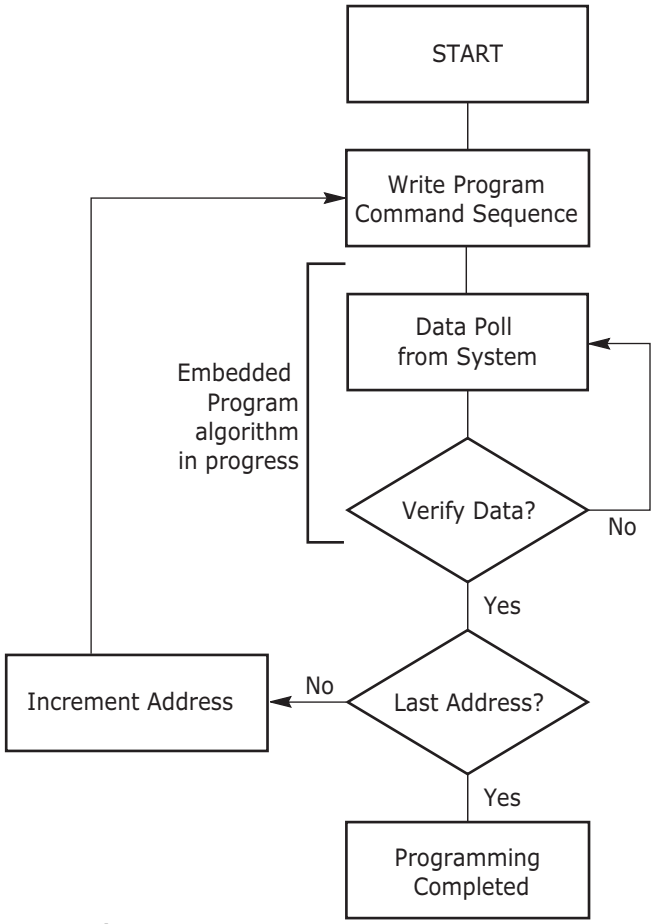
Unlock Bypass Command Sequence

The unlock bypass feature allows the system to program bytes or words to a bank faster than using the standard program command sequence. The unlock bypass command sequence is initiated by first writing two unlock cycles. This is followed by a third write cycle containing the unlock bypass command, 20h. That bank then enters the unlock bypass mode. A two-cycle unlock bypass program command sequence is all that is required to program in this mode. The first cycle in this sequence contains the unlock bypass program command, A0h; the second cycle contains the program address and data. Additional data is programmed in the same manner. This mode dispenses with the initial two unlock cycles required in the standard program command sequence, resulting in faster total programming time. Table 11 shows the requirements for the command sequence.

During the unlock bypass mode, only the Unlock Bypass Program and Unlock Bypass Reset commands are valid. To exit the unlock bypass mode, the system must issue the two-cycle unlock bypass reset command sequence. (See Table 12).

The device offers accelerated program operations through the WP#/ACC pin. When the system asserts V_{HH} on the WP#/ACC pin, the device automatically enters the Unlock Bypass mode. The system may then write the two-cycle Unlock Bypass program command sequence. The device uses the higher voltage on the WP#/ACC pin to accelerate the operation. *Note that the WP#/ACC pin must not be at V_{HH} for any operation other than accelerated programming, or device damage may result. In addition, the WP#/ACC pin must not be left floating or unconnected; inconsistent behavior of the device may result*.

4 illustrates the algorithm for the program operation. Refer to the "Erase and Program Operations" section table in the AC Characteristics section for parameters, and Figure 18 for timing diagrams.



Note: See Table 11 for program command sequence.

Figure 4. Program Operation

Chip Erase Command Sequence

Chip erase is a six bus cycle operation. The chip erase command sequence is initiated by writing two unlock cycles, followed by a set-up command. Two additional unlock write cycles are then followed by the chip erase command, which in turn invokes the Embedded Erase algorithm. The device does *not* require the system to preprogram prior to erase. The Embedded Erase algorithm automatically preprograms and verifies the entire memory for an all zero data pattern prior to electrical erase. The system is not required to provide any controls or timings during these operations. Table 11 shows the address and data requirements for the chip erase command sequence.

When the Embedded Erase algorithm is complete, that bank returns to the read mode and addresses are no longer latched. The system can determine the status of the erase operation by using DQ7, DQ6, DQ2, or RY/BY#. Refer to the "Write Operation Status" section section for information on these status bits.

Any commands written during the chip erase operation are ignored. However, note that a **hardware reset** immediately terminates the erase operation. If that occurs, the chip erase command sequence should be reinitiated once that bank has returned to reading array data, to ensure data integrity. *Note that the SecSi Sector, autoselect, and CFI functions are unavailable when an erase operation is in progress.*

5 illustrates the algorithm for the erase operation. Refer to the "Erase and Program Operations" section tables in the AC Characteristics section for parameters, and Figure 20 section for timing diagrams.

Sector Erase Command Sequence

Sector erase is a six bus cycle operation. The sector erase command sequence is initiated by writing two unlock cycles, followed by a set-up command. Two additional unlock cycles are written, and are then followed by the address of the sector to be erased, and the sector erase command. Table 11 shows the address and data requirements for the sector erase command sequence.

The device does *not* require the system to preprogram prior to erase. The Embedded Erase algorithm automatically programs and verifies the entire sector for an all zero data pattern prior to electrical erase. The system is not required to provide any controls or timings during these operations.

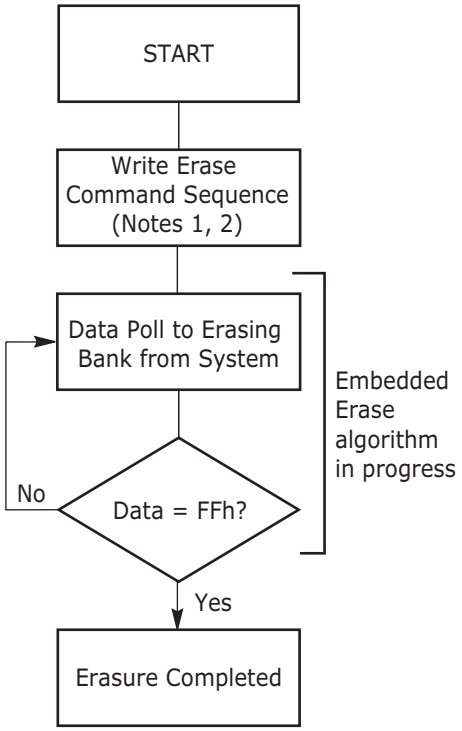
After the command sequence is written, a sector erase time-out of 80 µs occurs. During the time-out period, additional sector addresses and sector erase commands may be written. Loading the sector erase buffer may be done in any sequence, and the number of sectors may be from one sector to all sectors. The time between these additional cycles must be less than 80 µs, otherwise erasure may begin. Any sector erase address and command following the exceeded time-out may or may not be accepted. It is recommended that processor interrupts be disabled during this time to ensure all commands are accepted. The interrupts can be re-enabled after the last Sector Erase command is written. **Any command other than Sector Erase or Erase Suspend during the time-out period resets that bank to the read mode.** The system must rewrite the command sequence and any additional addresses and commands.

The system can monitor DQ3 to determine if the sector erase timer has timed out (See the section on DQ3: Sector Erase Timer.). The time-out begins from the rising edge of the final WE# or CE# pulse (first rising edge) in the command sequence.

When the Embedded Erase algorithm is complete, the bank returns to reading array data and addresses are no longer latched. Note that while the Embedded Erase operation is in progress, the system can read data from the non-erasing bank. The system can determine the status of the erase operation by reading DQ7, DQ6, DQ2, or RY/BY# in the erasing bank. Refer to the "Write Operation Status" section section for information on these status bits.

Once the sector erase operation has begun, only the Erase Suspend command is valid. All other commands are ignored. However, note that a **hardware reset** immediately terminates the erase operation. If that occurs, the sector erase command sequence should be reinitiated once that bank has returned to reading array data, to ensure data integrity. *Note that the SecSi Sector, autoselect, and CFI functions are unavailable when an erase operation is in progress.*

5 illustrates the algorithm for the erase operation. Refer to the "Erase and Program Operations" section tables in the AC Characteristics section for parameters, and Figure 20 section for timing diagrams.



Notes:

1. *See Table 11 for erase command sequence.*
2. *See the section on DQ3 for information on the sector erase timer.*

Figure 5. Erase Operation

Erase Suspend/Erase Resume Commands

The Erase Suspend command, B0h, allows the system to interrupt a sector erase operation and then read data from, or program data to, any sector not selected for erasure. The bank address is required when writing this command. This command is valid only during the sector erase operation, including the 80 µs time-out period during the sector erase command sequence. The Erase Suspend command is ignored if written during the chip erase operation or Embedded Program algorithm. The bank address must contain one of the sectors currently selected for erase.

When the Erase Suspend command is written during the sector erase operation, the device requires a maximum of 20 µs to suspend the erase operation. However, when the Erase Suspend command is written during the sector erase time-out, the device immediately terminates the time-out period and suspends the erase operation.

After the erase operation has been suspended, the bank enters the erase-suspend-read mode. The system can read data from or program data to any sector not selected for erasure. (The device “erase suspends” all sectors selected for erasure.) Reading at any address within erase-suspended sectors produces status information on DQ7–DQ0. The system can use DQ7, or DQ6 and DQ2 together, to determine if a sector is actively erasing or is erase-suspended. Refer to the "Write Operation Status" section section for information on these status bits.

After an erase-suspended program operation is complete, the bank returns to the erase-suspend-read mode. The system can determine the status of the program

operation using the DQ7 or DQ6 status bits, just as in the standard Byte Program operation. Refer to the "Write Operation Status" section section for more information.

In the erase-suspend-read mode, the system can also issue the autoselect command sequence. The device allows reading autoselect codes even at addresses within erasing sectors, since the codes are not stored in the memory array. When the device exits the autoselect mode, the device reverts to the Erase Suspend mode, and is ready for another valid operation. Refer to the "Autoselect Mode" section and "Autoselect Command Sequence" section sections for details.

To resume the sector erase operation, the system must write the Erase Resume command. The bank address of the erase-suspended bank is required when writing this command. Further writes of the Resume command are ignored. Another Erase Suspend command can be written after the chip has resumed erasing.

Table II. S29JL064H Command Definitions

Command Sequence (Note 1)			Cycles	Bus Cycles (Notes 2–5)											
				First		Second		Third		Fourth		Fifth		Sixth	
				Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data	Addr	Data
Read (Note 6)			1	RA	RD										
Reset (Note 7)			1	XXX	F0										
Autoselect (Note 8)	Manufacturer ID	Word	4	555	AA	2AA	55	(BA)555	90	(BA)X00	01				
		Byte		AAA		555		(BA)AAA							
	Device ID (Note 9)	Word	6	555	AA	2AA	55	(BA)555	90	(BA)X01	7E	(BA)X0E	02	(BA)X0F	01
		Byte		AAA		555		(BA)AAA		(BA)X02		(BA)X1C		(BA)X1E	
	SecSi Sector Factory Protect (Note 10)	Word	4	555	AA	2AA	55	(BA)555	90	(BA)X03	80/00				
		Byte		AAA		555		(BA)AAA		(BA)X06					
	Sector/Sector Block Protect Verify (Note 11)	Word	4	555	AA	2AA	55	(BA)555	90	(SA)X02	00/01				
		Byte		AAA		555		(BA)AAA		(SA)X04					
Enter SecSi Sector Region		Word	3	555	AA	2AA	55	555	88						
		Byte		AAA		555		AAA							
Exit SecSi Sector Region		Word	4	555	AA	2AA	55	555	90	XXX	00				
		Byte		AAA		555		AAA							
Program		Word	4	555	AA	2AA	55	555	A0	PA	PD				
		Byte		AAA		555		AAA							
Unlock Bypass		Word	3	555	AA	2AA	55	555	20						
		Byte		AAA		555		AAA							
Unlock Bypass Program (Note 12)			2	XXX	A0	PA	PD								
Unlock Bypass Reset (Note 13)			2	XXX	90	XXX	00								
Chip Erase		Word	6	555	AA	2AA	55	555	80	555	AA	2AA	55	555	10
		Byte		AAA		555		AAA		AAA		555		AAA	
Sector Erase		Word	6	555	AA	2AA	55	555	80	555	AA	2AA	55	SA	30
		Byte		AAA		555		AAA		AAA		555			
Erase Suspend (Note 14)			1	BA	B0										
Erase Resume (Note 15)			1	BA	30										
CFI Query (Note 16)		Word	1	55	98										
		Byte		AA											

Legend:

X = Don't care

RA = Address of the memory location to be read.

RD = Data read from location RA during read operation.

PA = Address of the memory location to be programmed. Addresses latch on the falling edge of the WE# or CE# pulse, whichever happens later.

PD = Data to be programmed at location PA. Data latches on the rising edge of WE# or CE# pulse, whichever happens first.

SA = Address of the sector to be verified (in autoselect mode) or erased. Address bits A21–A12 uniquely select any sector. Refer to Table 3 for information on sector addresses.

BA = Address of the bank that is being switched to autoselect mode, is in bypass mode, or is being erased. A21–A19 uniquely select a bank.

Notes:

1. *See Table 1 for description of bus operations.*
2. *All values are in hexadecimal.*
3. *Except for the read cycle and the fourth, fifth, and sixth cycle of the autoselect command sequence, all bus cycles are write cycles.*
4. *Data bits DQ15–DQ8 are don't care in command sequences, except for RD and PD.*
5. *Unless otherwise noted, address bits A21–A11 are don't cares for unlock and command cycles, unless SA or PA is required.*
6. *No unlock or command cycles required when bank is reading array data.*
7. *The Reset command is required to return to the read mode (or to the erase-suspend-read mode if previously in Erase Suspend) when a bank is in the autoselect mode, or if DQ5 goes high (while the bank is providing status information).*
8. *The fourth cycle of the autoselect command sequence is a read cycle. The system must provide the bank address to obtain the manufacturer ID, device ID, or SecSi Sector factory protect information. Data bits DQ15–DQ8 are don't care. While reading the autoselect addresses, the bank address must be the same until a reset command is given. See the "Autoselect Command Sequence" section section for more information.*
9. *The device ID must be read across the fourth, fifth, and sixth cycles.*
10. *The data is 80h for factory locked, 40h for customer locked, and 00h for not factory/customer locked.*
11. *The data is 00h for an unprotected sector/sector block and 01h for a protected sector/sector block.*
12. *The Unlock Bypass command is required prior to the Unlock Bypass Program command.*
13. *The Unlock Bypass Reset command is required to return to the read mode when the bank is in the unlock bypass mode.*
14. *The system may read and program in non-erasing sectors, or enter the autoselect mode, when in the Erase Suspend mode. The Erase Suspend command is valid only during a sector erase operation, and requires the bank address.*
15. *The Erase Resume command is valid only during the Erase Suspend mode, and requires the bank address.*
16. *Command is valid when device is ready to read array data or when device is in autoselect mode.*

Write Operation Status

The device provides several bits to determine the status of a program or erase operation: DQ2, DQ3, DQ5, DQ6, and DQ7. Table 12 and the following subsections describe the function of these bits. DQ7 and DQ6 each offer a method for determining whether a program or erase operation is complete or in progress. The device also provides a hardware-based output signal, RY/BY#, to determine whether an Embedded Program or Erase operation is in progress or has been completed.

DQ7: Data# Polling

The Data# Polling bit, DQ7, indicates to the host system whether an Embedded Program or Erase algorithm is in progress or completed, or whether a bank is in Erase Suspend. Data# Polling is valid after the rising edge of the final WE# pulse in the command sequence.

During the Embedded Program algorithm, the device outputs on DQ7 the complement of the datum programmed to DQ7. This DQ7 status also applies to programming during Erase Suspend. When the Embedded Program algorithm is complete, the device outputs the datum programmed to DQ7. The system must provide the program address to read valid status information on DQ7. If a program address falls within a protected sector, Data# Polling on DQ7 is active for approximately 1 µs, then that bank returns to the read mode.

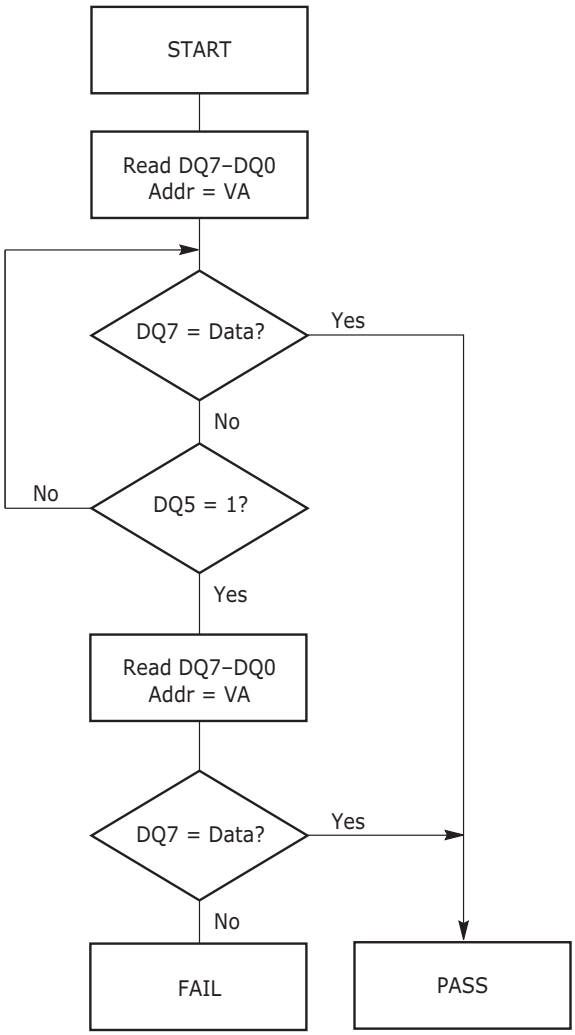
During the Embedded Erase algorithm, Data# Polling produces a "0" on DQ7. When the Embedded Erase algorithm is complete, or if the bank enters the Erase Suspend mode, Data# Polling produces a "1" on DQ7. The system must provide

an address within any of the sectors selected for erasure to read valid status information on DQ7.

After an erase command sequence is written, if all sectors selected for erasing are protected, Data# Polling on DQ7 is active for approximately 100 µs, then the bank returns to the read mode. If not all selected sectors are protected, the Embedded Erase algorithm erases the unprotected sectors, and ignores the selected sectors that are protected. However, if the system reads DQ7 at an address within a protected sector, the status may not be valid.

When the system detects DQ7 has changed from the complement to true data, it can read valid data at DQ15–DQ0 (or DQ7–DQ0 for x8-only device) on the *following* read cycles. Just prior to the completion of an Embedded Program or Erase operation, DQ7 may change asynchronously with DQ15–DQ8 (DQ7–DQ0 for x8-only device) while Output Enable (OE#) is asserted low. That is, the device may change from providing status information to valid data on DQ7. Depending on when the system samples the DQ7 output, it may read the status or valid data. Even if the device has completed the program or erase operation and DQ7 has valid data, the data outputs on DQ15–DQ0 may be still invalid. Valid data on DQ15–DQ0 (or DQ7–DQ0 for x8-only device) will appear on successive read cycles.

Table 12 shows the outputs for Data# Polling on DQ7. 6 shows the Data# Polling algorithm. 22 in the "AC Characteristics" section shows the Data# Polling timing diagram.



Notes:

1. *VA = Valid address for programming. During a sector erase operation, a valid address is any sector address within the sector being erased. During chip erase, a valid address is any non-protected sector address.*
2. *DQ7 should be rechecked even if DQ5 = "1" because DQ7 may change simultaneously with DQ5.*

Figure 6. Data# Polling Algorithm

RY/BY#: Ready/Busy#

The RY/BY# is a dedicated, open-drain output pin which indicates whether an Embedded Algorithm is in progress or complete. The RY/BY# status is valid after the rising edge of the final WE# pulse in the command sequence. Since RY/BY# is an open-drain output, several RY/BY# pins can be tied together in parallel with a pull-up resistor to V_{CC}.

If the output is low (Busy), the device is actively erasing or programming. (This includes programming in the Erase Suspend mode.) If the output is high (Ready), the device is in the read mode, the standby mode, or one of the banks is in the erase-suspend-read mode.

Table 12 shows the outputs for RY/BY#.

DQ6: Toggle Bit I

Toggle Bit I on DQ6 indicates whether an Embedded Program or Erase algorithm is in progress or complete, or whether the device has entered the Erase Suspend mode. Toggle Bit I may be read at any address, and is valid after the rising edge of the final WE# pulse in the command sequence (prior to the program or erase operation), and during the sector erase time-out.

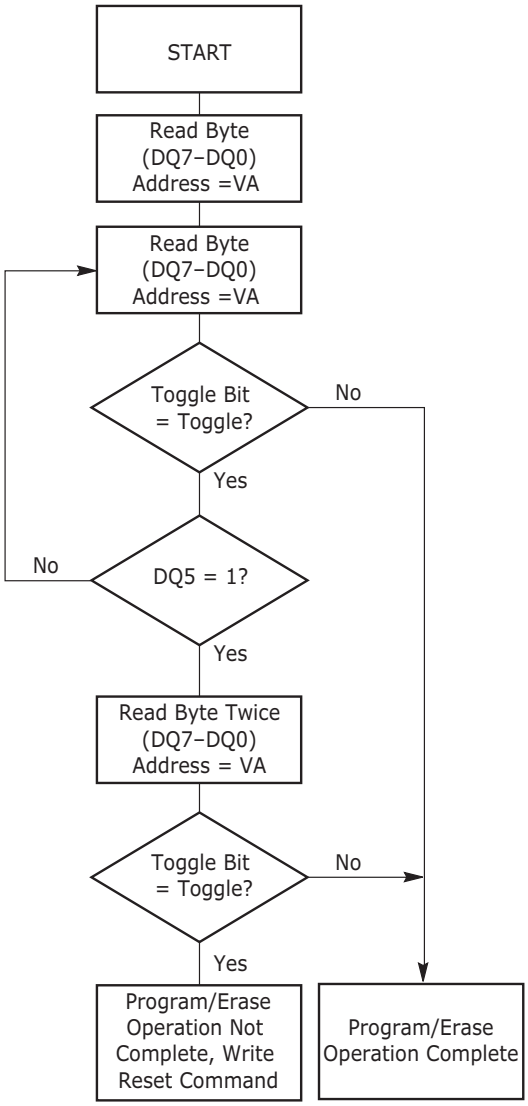
During an Embedded Program or Erase algorithm operation, successive read cycles to any address cause DQ6 to toggle. The system may use either OE# or CE# to control the read cycles. When the operation is complete, DQ6 stops toggling.

After an erase command sequence is written, if all sectors selected for erasing are protected, DQ6 toggles for approximately 100 µs, then returns to reading array data. If not all selected sectors are protected, the Embedded Erase algorithm erases the unprotected sectors, and ignores the selected sectors that are protected.

The system can use DQ6 and DQ2 together to determine whether a sector is actively erasing or is erase-suspended. When the device is actively erasing (that is, the Embedded Erase algorithm is in progress), DQ6 toggles. When the device enters the Erase Suspend mode, DQ6 stops toggling. However, the system must also use DQ2 to determine which sectors are erasing or erase-suspended. Alternatively, the system can use DQ7 (see the subsection on "DQ7: Data# Polling" section).

If a program address falls within a protected sector, DQ6 toggles for approximately 1 µs after the program command sequence is written, then returns to reading array data.

DQ6 also toggles during the erase-suspend-program mode, and stops toggling once the Embedded Program algorithm is complete.



Note: *The system should recheck the toggle bit even if DQ5 = "1" because the toggle bit may stop toggling as DQ5 changes to "1." See the subsections on DQ6 and DQ2 for more information.*

Figure 7. Toggle Bit Algorithm

DQ2: Toggle Bit II

The "Toggle Bit II" on DQ2, when used with DQ6, indicates whether a particular sector is actively erasing (that is, the Embedded Erase algorithm is in progress), or whether that sector is erase-suspended. Toggle Bit II is valid after the rising edge of the final WE# pulse in the command sequence.

DQ2 toggles when the system reads at addresses within those sectors that have been selected for erasure. (The system may use either OE# or CE# to control the read cycles.) But DQ2 cannot distinguish whether the sector is actively erasing or is erase-suspended. DQ6, by comparison, indicates whether the device is actively erasing, or is in Erase Suspend, but cannot distinguish which sectors are selected for erasure. Thus, both status bits are required for sector and mode information. Refer to Table 12 to compare outputs for DQ2 and DQ6.

7 shows the toggle bit algorithm in flowchart form, and the section "DQ2: Toggle Bit II" explains the algorithm. See also the "DQ6: Toggle Bit I" section subsection.

23 shows the toggle bit timing diagram. 24 shows the differences between DQ2 and DQ6 in graphical form.

Reading Toggle Bits DQ6/DQ2

Refer to 7 for the following discussion. Whenever the system initially begins reading toggle bit status, it must read DQ15–DQ0 (or DQ7–DQ0 for x8-only device) at least twice in a row to determine whether a toggle bit is toggling. Typically, the system would note and store the value of the toggle bit after the first read. After the second read, the system would compare the new value of the toggle bit with the first. If the toggle bit is not toggling, the device has completed the program or erase operation. The system can read array data on DQ15–DQ0 (or DQ7–DQ0 for x8-only device) on the following read cycle.

However, if after the initial two read cycles, the system determines that the toggle bit is still toggling, the system also should note whether the value of DQ5 is high (see the section on DQ5). If it is, the system should then determine again whether the toggle bit is toggling, since the toggle bit may have stopped toggling just as DQ5 went high. If the toggle bit is no longer toggling, the device has successfully completed the program or erase operation. If it is still toggling, the device did not completed the operation successfully, and the system must write the reset command to return to reading array data.

The remaining scenario is that the system initially determines that the toggle bit is toggling and DQ5 has not gone high. The system may continue to monitor the toggle bit and DQ5 through successive read cycles, determining the status as described in the previous paragraph. Alternatively, it may choose to perform other system tasks. In this case, the system must start at the beginning of the algorithm when it returns to determine the status of the operation (top of 7).

DQ5: Exceeded Timing Limits

DQ5 indicates whether the program or erase time has exceeded a specified internal pulse count limit. Under these conditions DQ5 produces a "1," indicating that the program or erase cycle was not successfully completed.

The device may output a "1" on DQ5 if the system tries to program a "1" to a location that was previously programmed to "0." **Only an erase operation can change a "0" back to a "1."** Under this condition, the device halts the operation, and when the timing limit has been exceeded, DQ5 produces a "1."

Under both these conditions, the system must write the reset command to return to the read mode (or to the erase-suspend-read mode if a bank was previously in the erase-suspend-program mode).

DQ3: Sector Erase Timer

After writing a sector erase command sequence, the system may read DQ3 to determine whether or not erasure has begun. (The sector erase timer does not apply to the chip erase command.) If additional sectors are selected for erasure, the entire time-out also applies after each additional sector erase command. When the time-out period is complete, DQ3 switches from a "0" to a "1." If the time between additional sector erase commands from the system can be assumed to be less than 50 µs, the system need not monitor DQ3. See also the "Sector Erase Command Sequence" section section.

After the sector erase command is written, the system should read the status of DQ7 (Data# Polling) or DQ6 (Toggle Bit I) to ensure that the device has accepted the command sequence, and then read DQ3. If DQ3 is "1," the Embedded Erase

algorithm has begun; all further commands (except Erase Suspend) are ignored until the erase operation is complete. If DQ3 is "0," the device will accept additional sector erase commands. To ensure the command has been accepted, the system software should check the status of DQ3 prior to and following each subsequent sector erase command. If DQ3 is high on the second status check, the last command might not have been accepted.

Table 12 shows the status of DQ3 relative to the other status bits.

Table 12. Write Operation Status

Status			DQ7 (Note 2)	DQ6	DQ5 (Note 1)	DQ3	DQ2 (Note 2)	RY/BY#
Standard Mode	Embedded Program Algorithm		DQ7#	Toggle	0	N/A	No toggle	0
	Embedded Erase Algorithm		0	Toggle	0	1	Toggle	0
Erase Suspend Mode	Erase-Suspend-Read	Erase Suspended Sector	1	No toggle	0	N/A	Toggle	1
		Non-Erase Suspended Sector	Data	Data	Data	Data	Data	1
	Erase-Suspend-Program		DQ7#	Toggle	0	N/A	N/A	0

Notes:

1. *DQ5 switches to '1' when an Embedded Program or Embedded Erase operation has exceeded the maximum timing limits. Refer to the section on DQ5 for more information.*
2. *DQ7 and DQ2 require a valid address when reading status information. Refer to the appropriate subsection for further details.*
3. *When reading write operation status bits, the system must always provide the bank address where the Embedded Algorithm is in progress. The device outputs array data if the system addresses a non-busy bank.*

Absolute Maximum Ratings

Storage Temperature
Plastic Packages . . . . . –65°C to +150°C
Ambient Temperature
with Power Applied . . . . . –65°C to +125°C
Voltage with Respect to Ground
V_{CC} (Note 1). . . . . –0.5 V to +4.0 V
OE# and RESET#
(Note 2). . . . . –0.5 V to +12.5 V
WP#/ACC. . . . . –0.5 V to +10.5 V
All other pins (Note 1) . . . . . –0.5 V to V_{CC} +0.5 V
Output Short Circuit Current (Note 3) . . . . . 200 mA

Notes:

1. *Minimum DC voltage on input or I/O pins is –0.5 V. During voltage transitions, input or I/O pins may overshoot V_{SS} to –2.0 V for periods of up to 20 ns. Maximum DC voltage on input or I/O pins is V_{CC} +0.5 V. See Figure 8. During voltage transitions, input or I/O pins may overshoot to V_{CC} +2.0 V for periods up to 20 ns. See Figure 9.*
2. *Minimum DC input voltage on pins OE#, RESET#, and WP#/ACC is –0.5 V. During voltage transitions, OE#, WP#/ACC, and RESET# may overshoot V_{SS} to –2.0 V for periods of up to 20 ns. See Figure 8. Maximum DC input voltage on WP#/ACC is +9.5 V which may overshoot to +12.0 V for periods up to 20 ns.*
3. *No more than one output may be shorted to ground at a time. Duration of the short circuit should not be greater than one second.*

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this data sheet is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

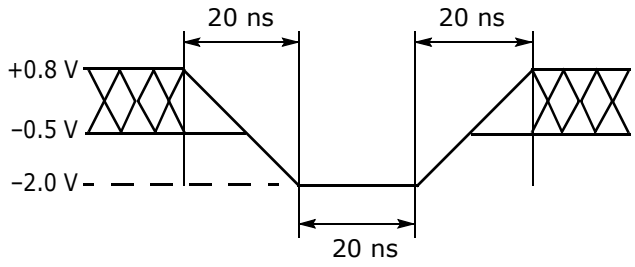


Figure 8. Maximum Negative Overshoot Waveform

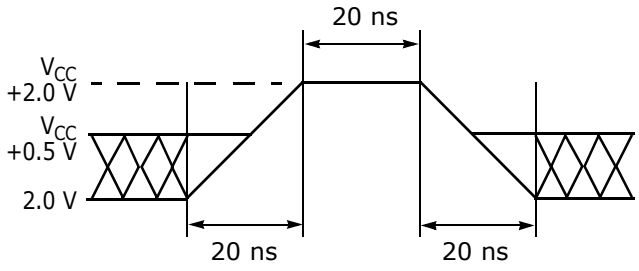


Figure 9. Maximum Positive Overshoot Waveform

OPERATING RANGES

Wireless (W) Devices

Ambient Temperature (T_A) . . . . . –25°C to +85°C

Industrial (I) Devices

Ambient Temperature (T_A) . . . . . –40°C to +85°C

V_{CC} Supply Voltages

V_{CC} for standard voltage range . . . . . 2.7 V to 3.6 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC Characteristics

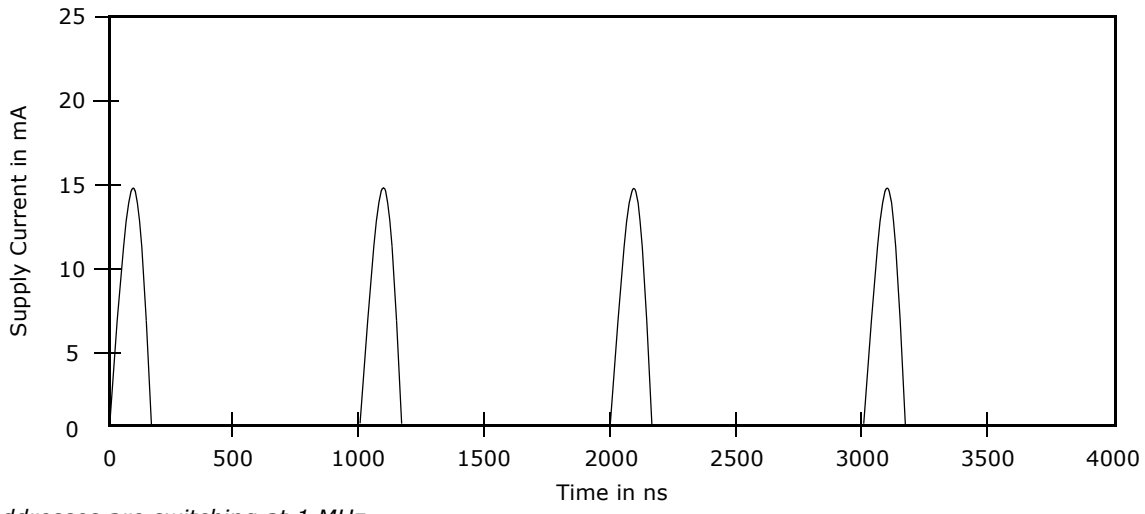
Table 13. CMOS Compatible

Parameter Symbol	Parameter Description	Test Conditions		Min	Typ	Max	Unit
I_{LI}	Input Load Current	$V_{IN} = V_{SS}$ to V_{CC}, $V_{CC} = V_{CC\ max}$				±1.0	µA
I_{LIT}	OE# and RESET# Input Load Current	$V_{CC} = V_{CC\ max}$, OE# = V_{IH}; OE# or RESET# = 12.5 V				35	µA
I_{LO}	Output Leakage Current	$V_{OUT} = V_{SS}$ to V_{CC}, $V_{CC} = V_{CC\ max}$, OE# = V_{IH}				±1.0	µA
I_{LR}	Reset Leakage Current	$V_{CC} = V_{CC\ max}$; RESET# = 12.5 V				35	µA
I_{CC1}	V_{CC} Active Read Current (Notes 1, 2)	CE# = V_{IL}, OE# = V_{IH}, Byte Mode	5 MHz		10	16	mA
			1 MHz		2	4	
		CE# = V_{IL}, OE# = V_{IH}, Word Mode	5 MHz		10	16	
			1 MHz		2	4	
I_{CC2}	V_{CC} Active Write Current (Notes 2, 3)	CE# = V_{IL}, OE# = V_{IH}, WE# = V_{IL}			15	30	mA
I_{CC3}	V_{CC} Standby Current (Note 2)	CE#, RESET# = V_{CC} ± 0.3 V			0.2	5	µA
I_{CC4}	V_{CC} Reset Current (Note 2)	RESET# = V_{SS} ± 0.3 V			0.2	5	µA
I_{CC5}	Automatic Sleep Mode (Notes 2, 4)	$V_{IH} = V_{CC}$ ± 0.3 V; $V_{IL} = V_{SS}$ ± 0.3 V			0.2	5	µA
I_{CC6}	V_{CC} Active Read-While-Program Current (Notes 1, 2)	CE# = V_{IL}, OE# = V_{IH}	Byte		21	45	mA
			Word		21	45	
I_{CC7}	V_{CC} Active Read-While-Erase Current (Notes 1, 2)	CE# = V_{IL}, OE# = V_{IH}	Byte		21	45	mA
			Word		21	45	
I_{CC8}	V_{CC} Active Program-While-Erase-Suspended Current (Notes 2, 5)	CE# = V_{IL}, OE# = V_{IH}			17	35	mA
V_{IL}	Input Low Voltage			–0.5		0.8	V
V_{IH}	Input High Voltage			0.7 x V_{CC}		V_{CC} + 0.3	V
V_{HH}	Voltage for WP#/ACC Sector Protect/Unprotect and Program Acceleration	V_{CC} = 3.0 V ± 10%		8.5		9.5	V
V_{ID}	Voltage for Autoselect and Temporary Sector Unprotect	V_{CC} = 3.0 V ± 10%		11.5		12.5	V
V_{OL}	Output Low Voltage	I_{OL} = 2.0 mA, $V_{CC} = V_{CC\ min}$				0.45	V
V_{OH1}	Output High Voltage	I_{OH} = –2.0 mA, $V_{CC} = V_{CC\ min}$		0.85 V_{CC}			V
V_{OH2}		I_{OH} = –100 µA, $V_{CC} = V_{CC\ min}$		V_{CC}–0.4			
V_{LKO}	Low V_{CC} Lock-Out Voltage (Note 5)			2.3		2.5	V

Notes:

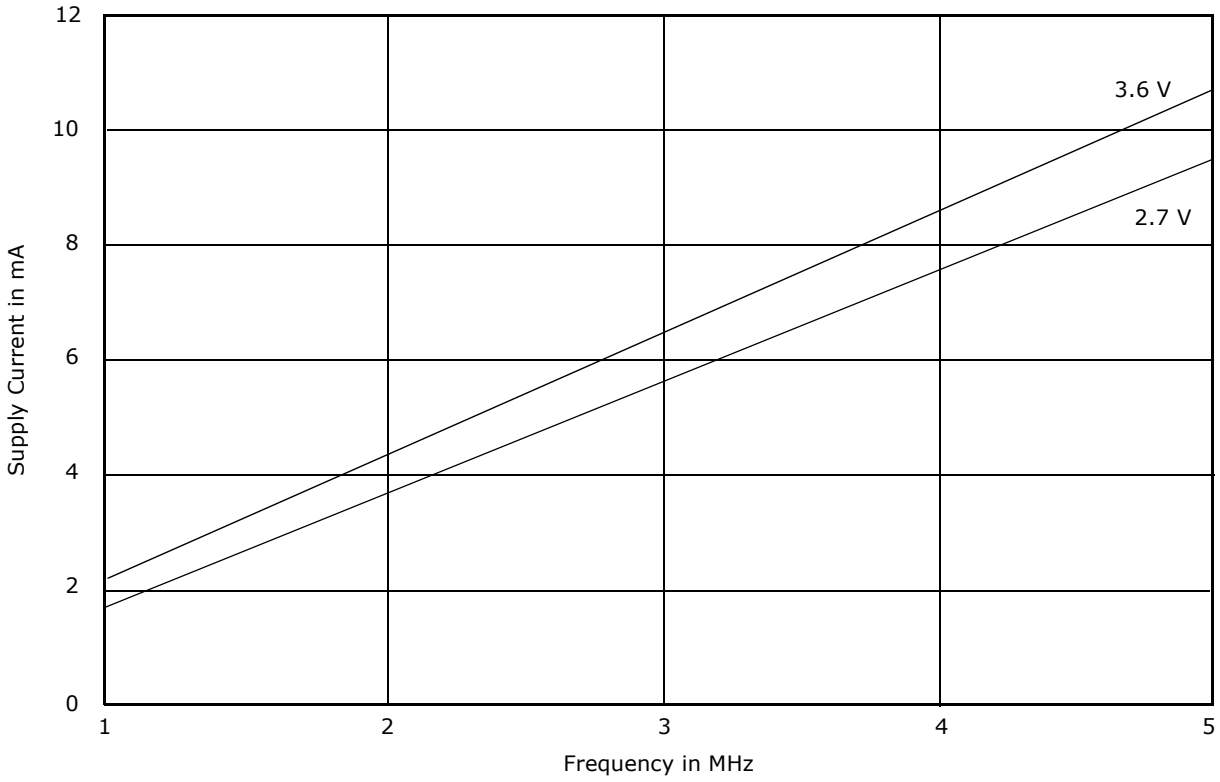
1. *The I_{CC} current listed is typically less than 2 mA/MHz, with OE# at V_{IH}.*
2. *Maximum I_{CC} specifications are tested with $V_{CC} = V_{CC}max$.*
3. *I_{CC} active while Embedded Erase or Embedded Program is in progress.*
4. *Automatic sleep mode enables the low power mode when addresses remain stable for t_{ACC} + 30 ns. Typical sleep mode current is 200 nA.*
5. *Not 100% tested.*

Zero-Power Flash



Note: *Addresses are switching at 1 MHz*

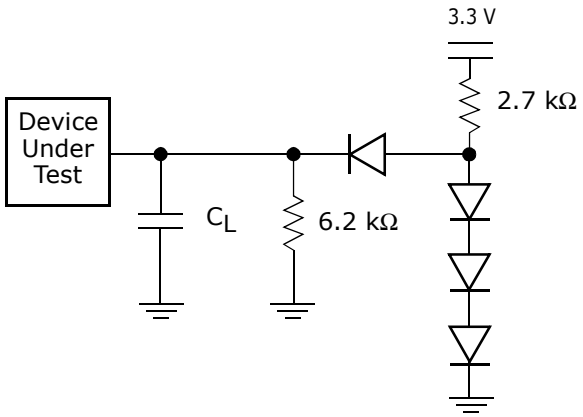
Figure 10. I_{CCI} Current vs. Time (Showing Active and Automatic Sleep Currents)



Note: *T = 25 ×C*

Figure 11. Typical ICCI vs. Frequency

Test Conditions



Note: *Diodes are IN3064 or equivalent*

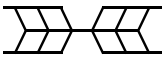
Figure I2. Test Setup

Table I4. Test Specifications

Test Condition	All Speeds	Unit
Output Load	1 TTL gate	
Output Load Capacitance, C_L (including jig capacitance)	30	pF
Input Rise and Fall Times	5	ns
Input Pulse Levels	0.0–3.0	V
Input timing measurement reference levels	1.5	V
Output timing measurement reference levels	1.5	V

Switching Waveforms

Table I5. Key To Switching Waveforms

WAVEFORM	INPUTS	OUTPUTS
	Steady	
	Changing from H to L	
	Changing from L to H	
	Don't Care, Any Change Permitted	Changing, State Unknown
	Does Not Apply	Center Line is High Impedance State (High Z)

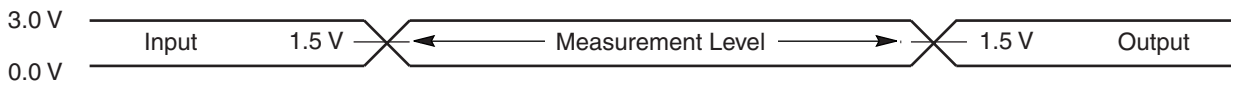


Figure I3. Input Waveforms and Measurement Levels

AC Characteristics

Read-Only Operations

Parameter		Description		Test Setup		Speed Options			Unit
JEDEC	Std.					55	70	85	
t_{AVAV}	t_{RC}	Read Cycle Time (Note 1)			Min	55	70	85	ns
t_{AVQV}	t_{ACC}	Address to Output Delay		CE#, OE# = V_{IL}	Max	55	70	85	ns
t_{ELQV}	t_{CE}	Chip Enable to Output Delay		OE# = V_{IL}	Max	55	70	85	ns
t_{GLQV}	t_{OE}	Output Enable to Output Delay			Max	25	30	40	ns
t_{EHQZ}	t_{DF}	Chip Enable to Output High Z (Notes 1, 3)			Max	16			ns
t_{GHQZ}	t_{DF}	Output Enable to Output High Z (Notes 1, 3)			Max	16			ns
t_{AXQX}	t_{OH}	Output Hold Time From Addresses, CE# or OE#, Whichever Occurs First			Min	0			ns
	t_{OEH}	Output Enable Hold Time (Note 1)	Read		Min	0			ns
			Toggle and Data# Polling		Min	5	10		ns

Notes:

1. *Not 100% tested.*
2. *See 12 and Table 14 for test specifications*
3. *Measurements performed by placing a 50 ohm termination on the data pin with a bias of $V_{CC}/2$. The time from OE# high to the data bus driven to $V_{CC}/2$ is taken as t_{DF}*

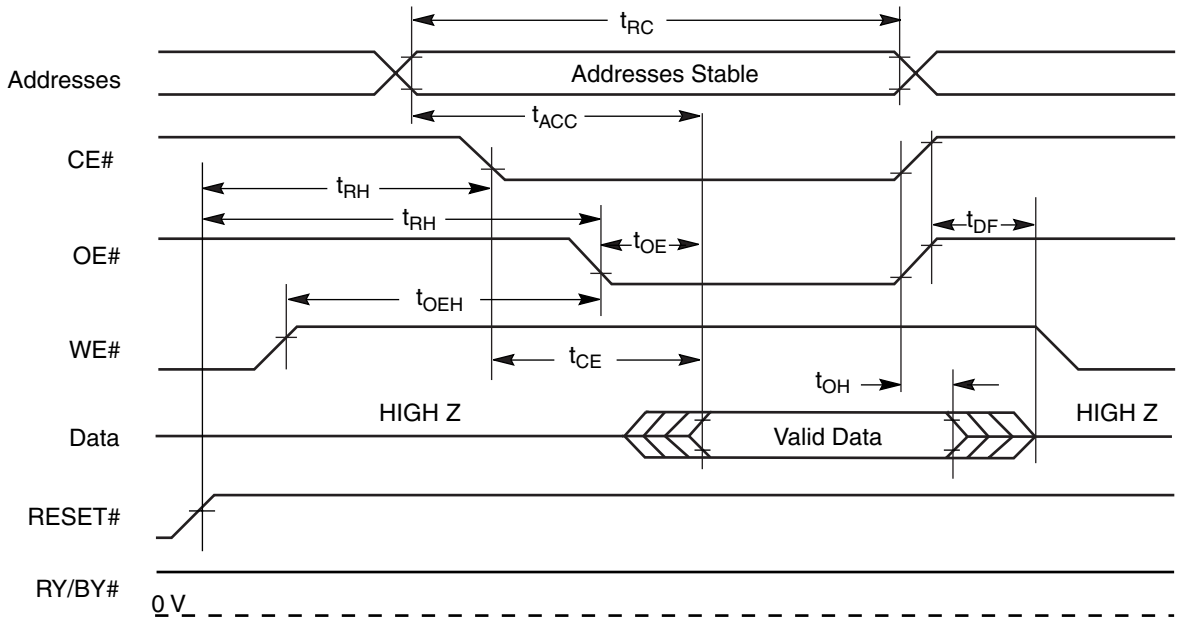


Figure 14. Read Operation Timings

Hardware Reset (RESET#)

Parameter		Description		All Speed Options	Unit
JEDEC	Std				
	t_{Ready}	RESET# Pin Low (During Embedded Algorithms) to Read Mode (See Note)	Max	20	µs
	t_{Ready}	RESET# Pin Low (NOT During Embedded Algorithms) to Read Mode (See Note)	Max	500	ns
	t_{RP}	RESET# Pulse Width	Min	500	ns
	t_{RH}	Reset High Time Before Read (See Note)	Min	50	ns
	t_{RPD}	RESET# Low to Standby Mode	Min	20	µs
	t_{RB}	RY/BY# Recovery Time	Min	0	ns

Note: *Not 100% tested.*

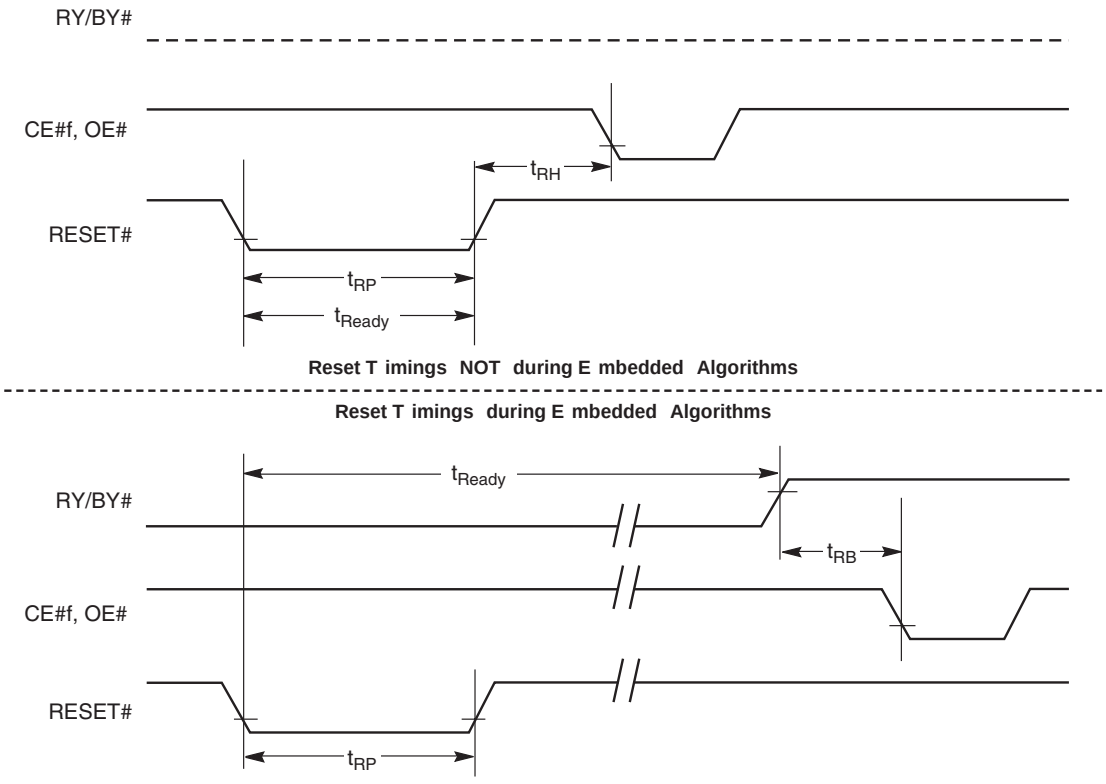


Figure I5. Reset Timings

Word/Byte Configuration (BYTE#)

Parameter		Description		Speed Options			Unit
JEDEC	Std.			55	70	85	
	t_{ELFL}/t_{ELFH}	CE# to BYTE# Switching Low or High	Max	5			ns
	t_{FLQZ}	BYTE# Switching Low to Output HIGH Z	Max	16			ns
	t_{FHQV}	BYTE# Switching High to Output Active	Min	55	70	85	ns

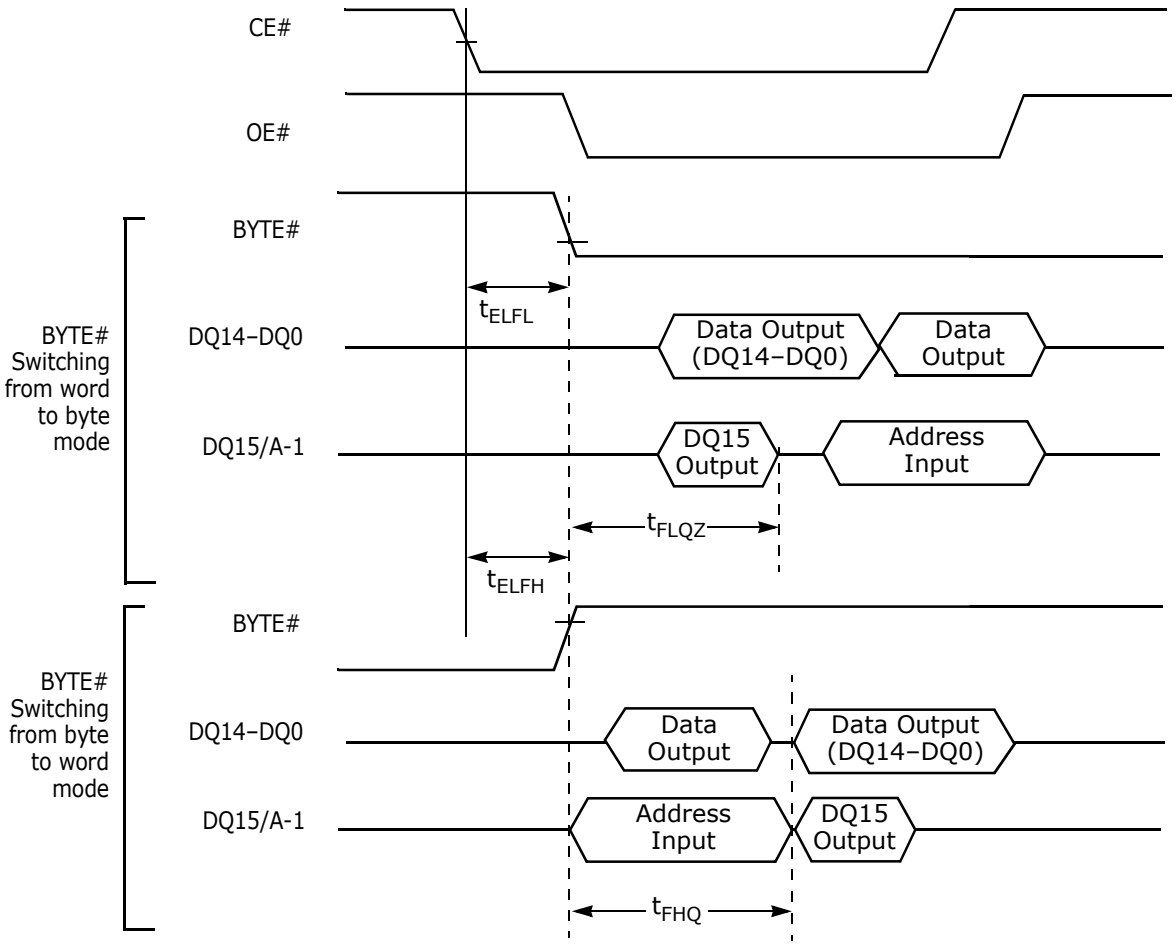
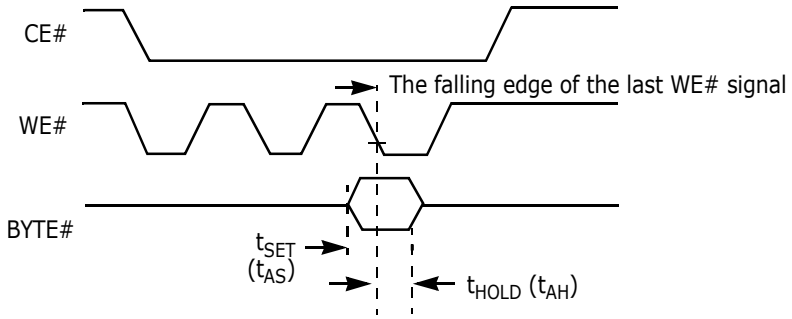


Figure 16. BYTE# Timings for Read Operations



Note: *Refer to the Erase/Program Operations table for t_{AS} and t_{AH} specifications.*

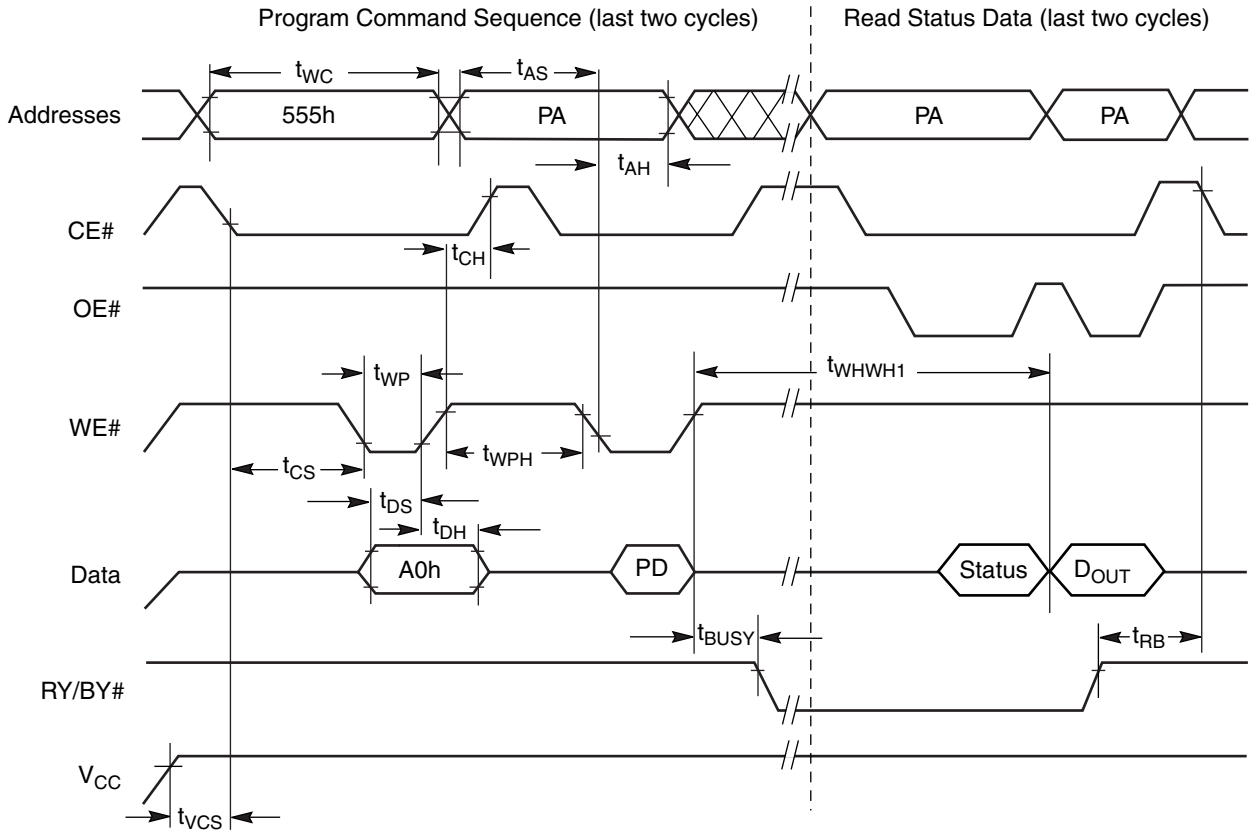
Figure 17. BYTE# Timings for Write Operations

Erase and Program Operations

Parameter					Speed Options			
JEDEC	Std	Description			55	70	85	Unit
t_{AVAV}	t_{WC}	Write Cycle Time (Note 1)		Min	55	70	85	ns
t_{AVWL}	t_{AS}	Address Setup Time		Min	0			ns
	t_{ASO}	Address Setup Time to OE# low during toggle bit polling		Min	15			ns
t_{WLAX}	t_{AH}	Address Hold Time		Min	30	40	45	ns
	t_{AHT}	Address Hold Time From CE# or OE# high during toggle bit polling		Min	0			ns
t_{DVWH}	t_{DS}	Data Setup Time		Min	30	40	45	ns
t_{WHDX}	t_{DH}	Data Hold Time		Min	0			ns
	t_{OEPH}	Output Enable High during toggle bit polling		Min	20			ns
t_{GHWL}	t_{GHWL}	Read Recovery Time Before Write (OE# High to WE# Low)		Min	0			ns
t_{ELWL}	t_{CS}	CE# Setup Time		Min	0			ns
t_{WHEH}	t_{CH}	CE# Hold Time		Min	0			ns
t_{WLWH}	t_{WP}	Write Pulse Width		Min	25	30	35	ns
t_{WHDL}	t_{WPH}	Write Pulse Width High		Min	25	30	30	ns
	$t_{SR/W}$	Latency Between Read and Write Operations		Min	0			ns
t_{WHWH1}	t_{WHWH1}	Programming Operation (Note 2)	Byte	Typ	5			µs
			Word	Typ	7			
t_{WHWH1}	t_{WHWH1}	Accelerated Programming Operation, Word or Byte (Note 2)		Typ	4			µs
t_{WHWH2}	t_{WHWH2}	Sector Erase Operation (Note 2)		Typ	0.4			sec
	t_{VCS}	V_{CC} Setup Time (Note 1)		Min	50			µs
	t_{RB}	Write Recovery Time from RY/BY#		Min	0			ns
	t_{BUSY}	Program/Erase Valid to RY/BY# Delay		Max	90			ns

Notes:

1. *Not 100% tested.*
2. *See the "Erase And Programming Performance" section for more information.*



Notes:

1. *PA = program address, PD = program data, D_{OUT} is the true data at the program address.*
2. *Illustration shows device in word mode*

Figure I8. Program Operation Timings

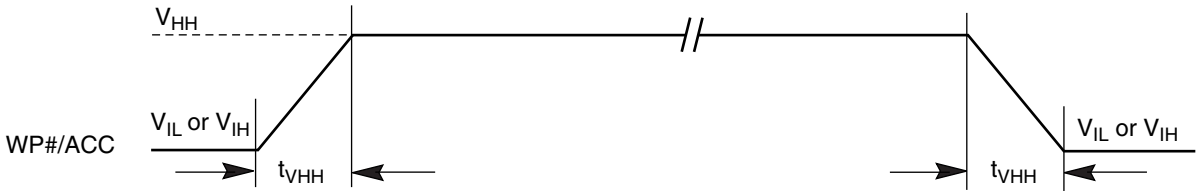
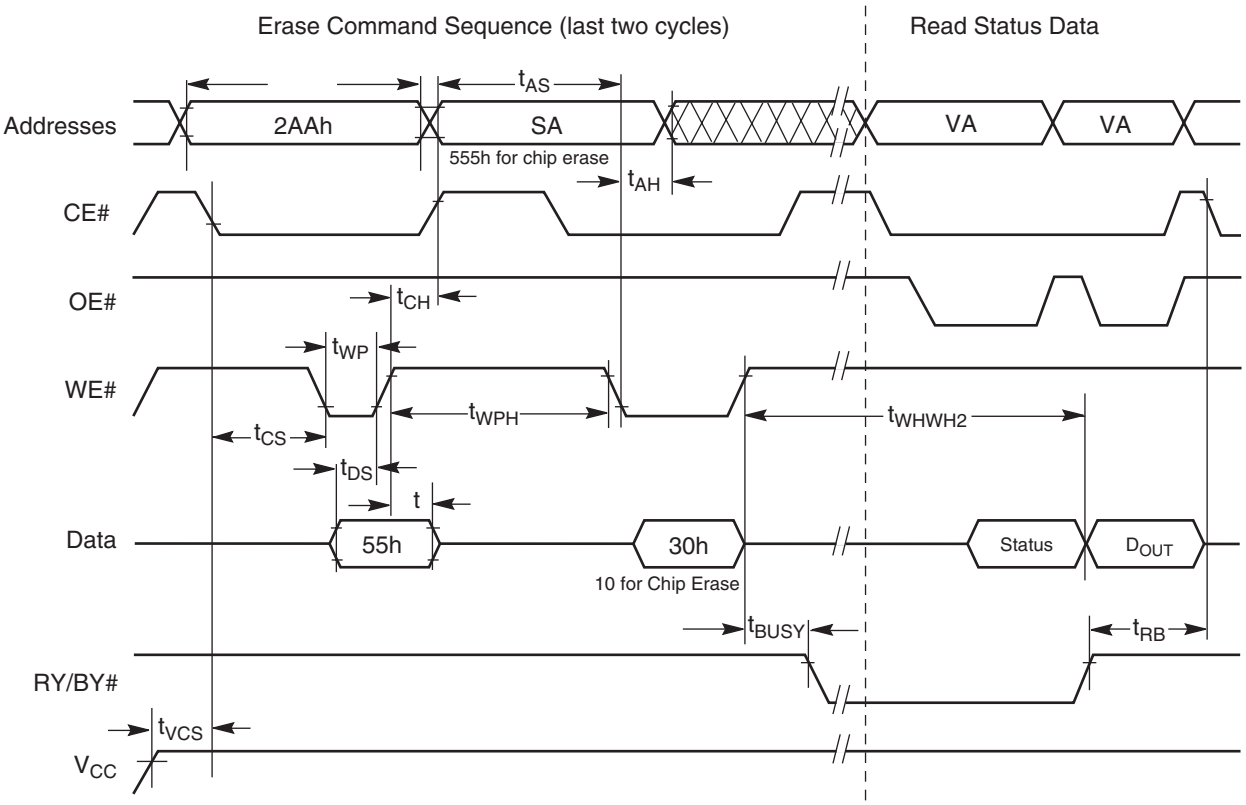


Figure I9. Accelerated Program Timing Diagram



Notes:

1. *SA = sector address (for Sector Erase), VA = Valid Address for reading status data (see "Write Operation Status".*
2. *These waveforms are for the word mode.*

Figure 20. Chip/Sector Erase Operation Timings

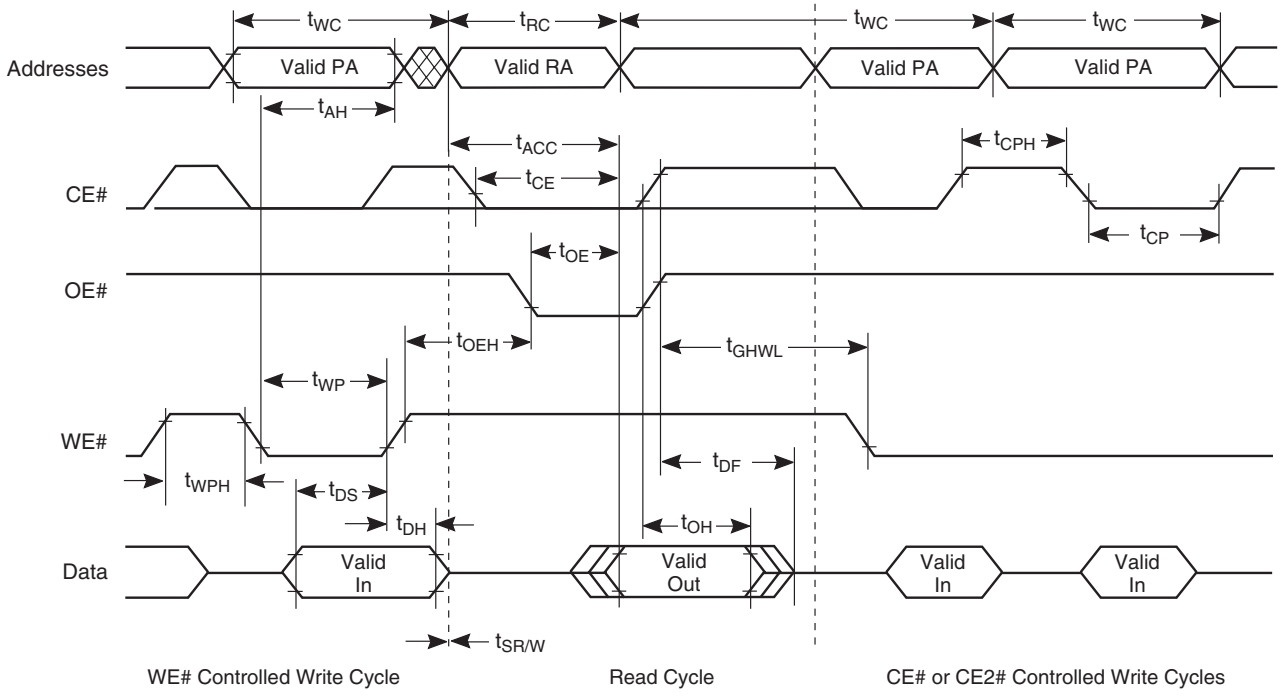
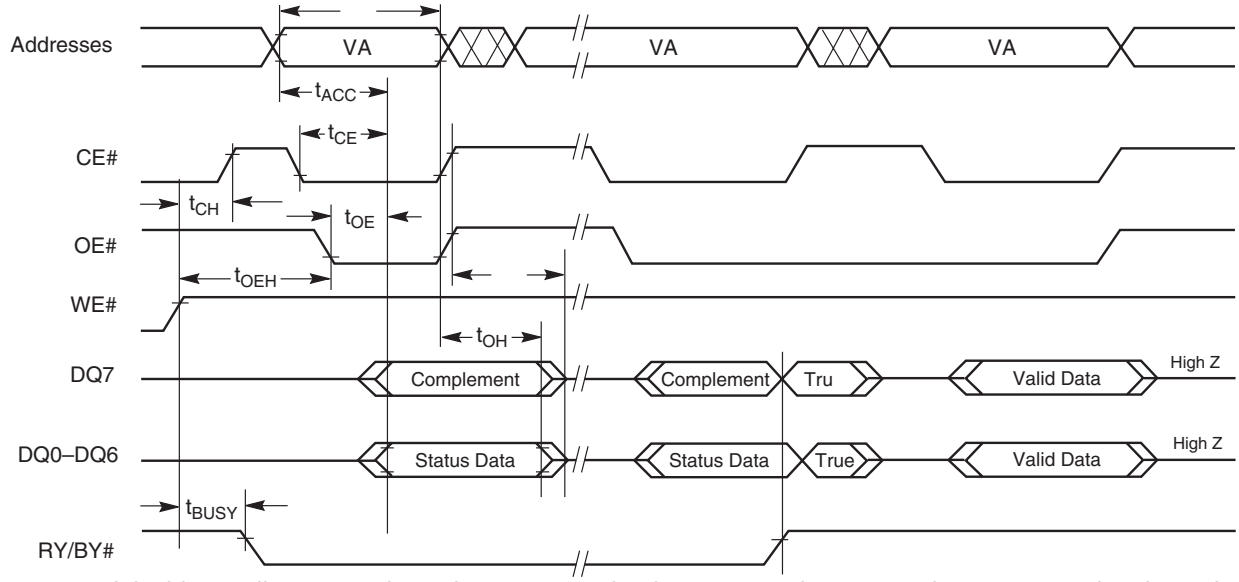
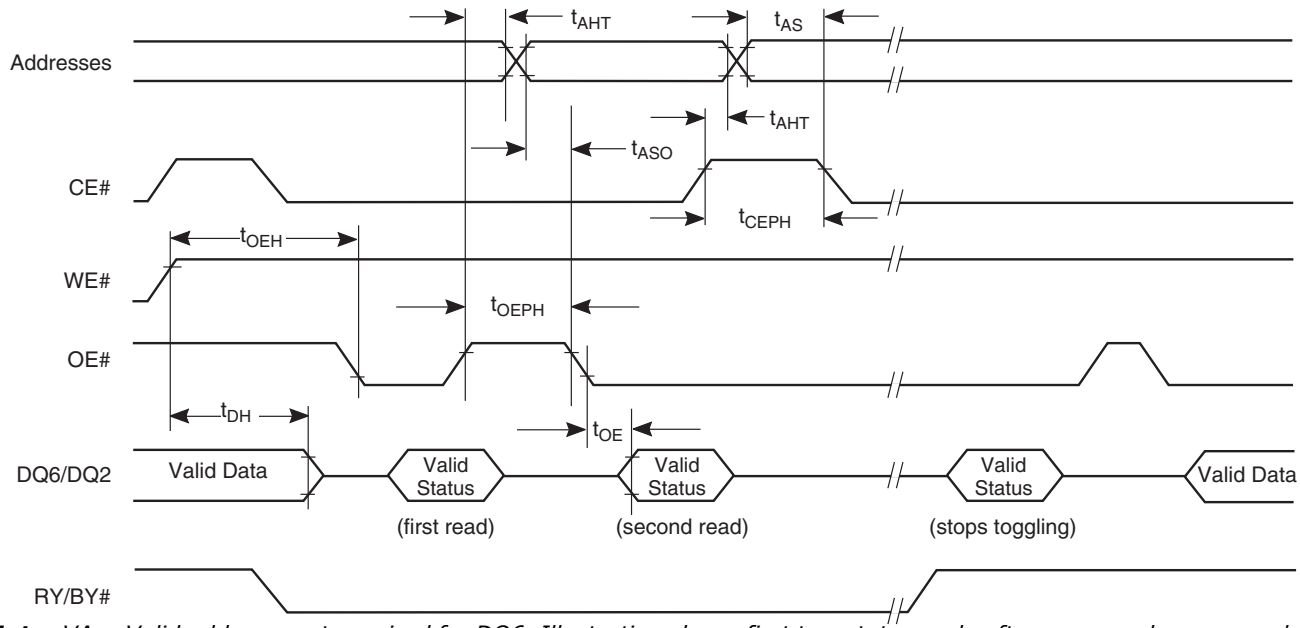


Figure 2I. Back-to-back Read/Write Cycle Timings



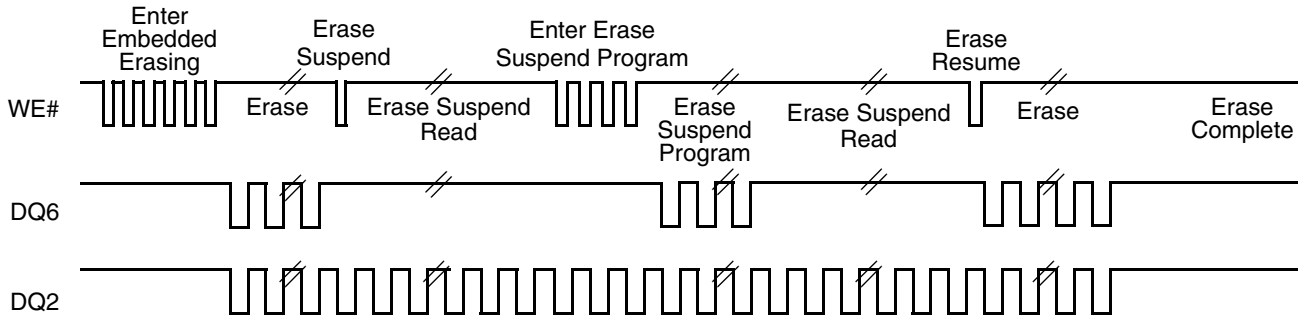
Note: *VA = Valid address. Illustration shows first status cycle after command sequence, last status read cycle, and array data read cycl*

Figure 22. Data# Polling Timings (During Embedded Algorithms)



Note: *VA = Valid address; not required for DQ6. Illustration shows first two status cycle after command sequence, last status read cycle, and array data read cycle*

Figure 23. Toggle Bit Timings (During Embedded Algorithms)



Note: *DQ2 toggles only when read at an address within an erase-suspended sector. The system may use OE# or CE# to toggle DQ2 and DQ6.*

Figure 24. DQ2 vs. DQ6

Temporary Sector Unprotect

Parameter		Description		All Speed Options	Unit
JEDEC	Std				
	t_{VIDR}	V_{ID} Rise and Fall Time (see Note)	Min	500	ns
	t_{VHH}	V_{HH} Rise and Fall Time (see Note)	Min	250	ns
	t_{RSP}	RESET# Setup Time for Temporary Sector Unprotect	Min	4	µs
	t_{RRB}	RESET# Hold Time from RY/BY# High for Temporary Sector Unprotect	Min	4	µs

Note: *Not 100% tested.*

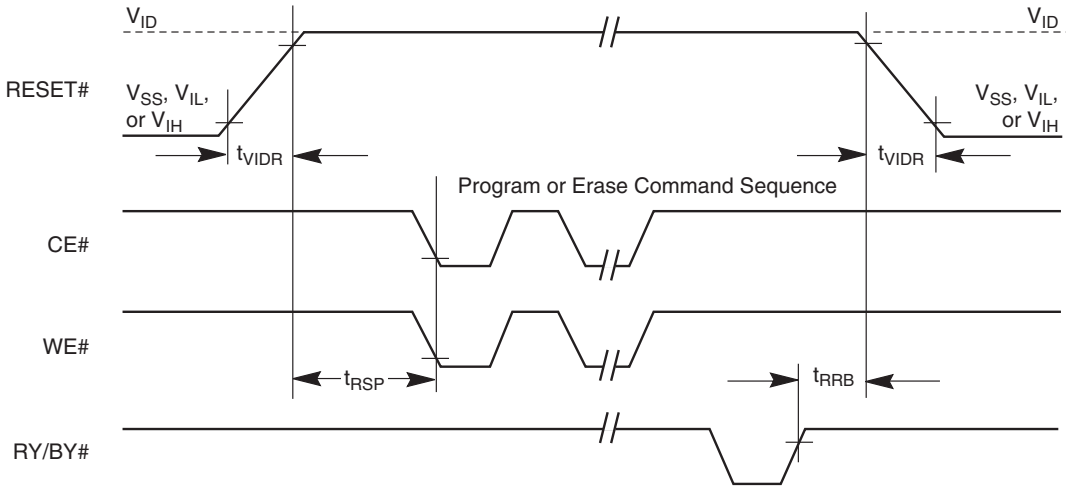


Figure 25. Temporary Sector Unprotect Timing Diagram

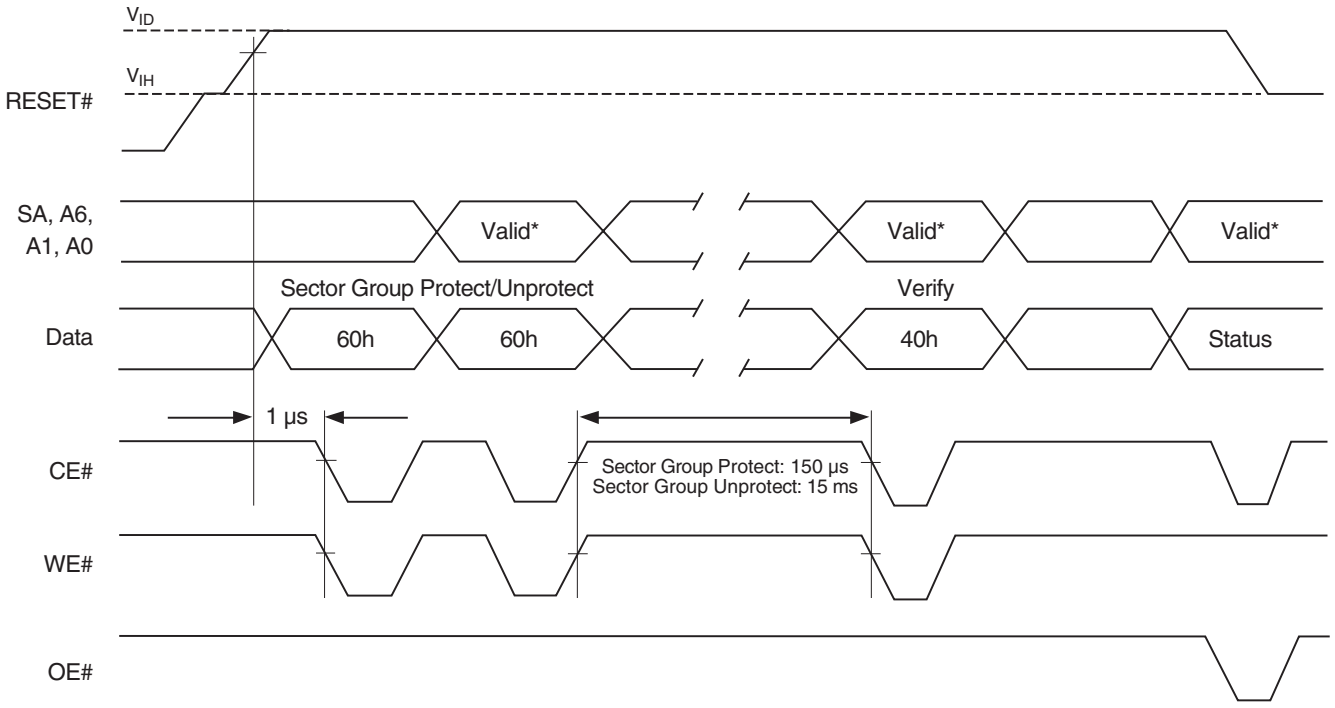


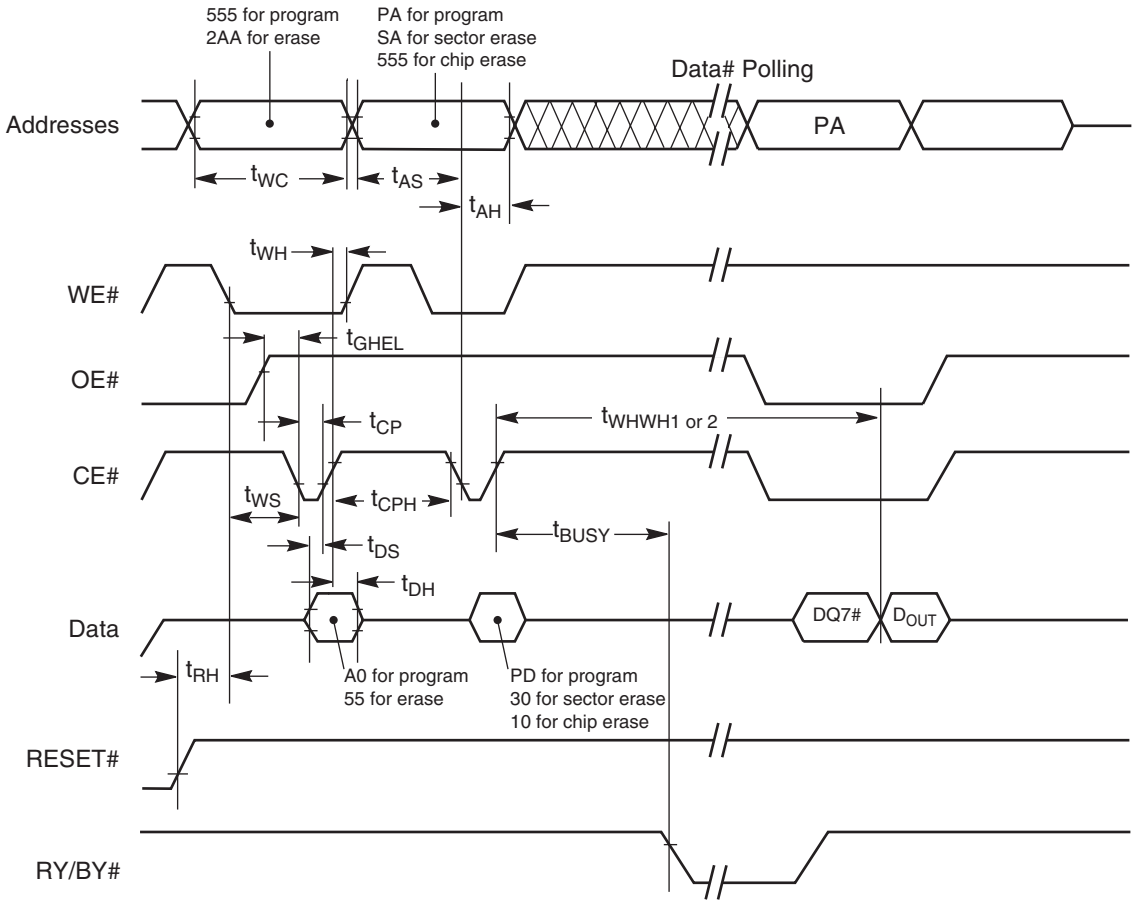
Figure 26. Sector/Sector Block Protect and Unprotect Timing Diagram

Alternate CE# Controlled Erase and Program Operations

Parameter		Description			Speed Options			Unit
JEDEC	Std.				55	70	85	
t_{AVAV}	t_{WC}	Write Cycle Time (Note 1)		Min	55	70	85	ns
t_{AVWL}	t_{AS}	Address Setup Time		Min	0			ns
t_{ELAX}	t_{AH}	Address Hold Time		Min	30	40	45	ns
t_{DVEH}	t_{DS}	Data Setup Time		Min	30	40	45	ns
t_{EHDX}	t_{DH}	Data Hold Time		Min	0			ns
t_{GHEL}	t_{GHEL}	Read Recovery Time Before Write (OE# High to WE# Low)		Min	0			ns
t_{WLEL}	t_{WS}	WE# Setup Time		Min	0			ns
t_{EHWH}	t_{WH}	WE# Hold Time		Min	0			ns
t_{ELEH}	t_{CP}	CE# Pulse Width		Min	25	40	45	ns
t_{EHEL}	t_{CPH}	CE# Pulse Width High		Min	25	30		ns
t_{WHWH1}	t_{WHWH1}	Programming Operation (Note 2)	Byte	Typ	5			µs
			Word	Typ	7			
t_{WHWH1}	t_{WHWH1}	Accelerated Programming Operation, Word or Byte (Note 2)		Typ	4			µs
t_{WHWH2}	t_{WHWH2}	Sector Erase Operation (Note 2)		Typ	0.4			sec

Notes:

1. *Not 100% tested.*
2. *See the "Erase And Programming Performance" section for more information.*



Notes:

1. *Figure indicates last two bus cycles of a program or erase operation.*
2. *PA = program address, SA = sector address, PD = program data.*
3. *DQ7# is the complement of the data written to the device. D_{OUT} is the data written to the device.*
4. *Waveforms are for the word mode.*

Figure 27. Alternate CE# Controlled Write (Erase/Program) Operation Timings

Erase And Programming Performance

Parameter		Typ (Note I)	Max (Note 2)	Unit	Comments
Sector Erase Time		0.4	5	sec	Excludes 00h programming prior to erasure (Note 4)
Chip Erase Time		56		sec	
Word Program Time		7	210	µs	Excludes system level overhead (Note 5)
Accelerated Byte/Word Program Time		4	120	µs	
Accelerated Chip Programming Time		10	30	sec	
Byte Program Time		5	150	µs	
Chip Program Time (Note 3)	Byte Mode	42	126	sec	
	Word Mode	28	84		

Notes:

1. *Typical program and erase times assume the following conditions: 25°C, 3.0 V V_{CC}, 100,000 cycles; checkerboard data pattern.*
2. *Under worst case conditions of 90°C, V_{CC} = 2.7 V, 1,000,000 cycles.*
3. *The typical chip programming time is considerably less than the maximum chip programming time listed, since most bytes program faster than the maximum program times listed.*
4. *In the pre-programming step of the Embedded Erase algorithm, all bytes are programmed to 00h before erasure.*
5. *System-level overhead is the time required to execute the two- or four-bus-cycle sequence for the program command. See Table 11 for further information on command definitions.*
6. *The device has a minimum cycling endurance of 100,000 cycles per sector.*
7. *Contact the local sales office for minimum cycling endurance values in specific applications and operating conditions.*

Latchup Characteristics

Description	Min	Max
Input voltage with respect to V_{SS} on all pins except I/O pins (including OE# and RESET#)	−1.0 V	12.5 V
Input voltage with respect to V_{SS} on all I/O pins	−1.0 V	V_{CC} + 1.0 V
V_{CC} Current	−100 mA	+100 mA

Note: *Includes all pins except V_{CC}. Test conditions: V_{CC} = 3.0 V, one pin at a time.*

16 Mb SRAM (supplier I)

16 Megabit (1Mb x 16 bit) CMOS SRAM

Functional Description

CE1#	CS2	OE#	WE#	LB#	UB#	$IO_{0\sim7}$	$IO_{8\sim15}$	Mode	Power
H	X	X	X	X	X	High-Z	High-Z	Deselected	Standby
X	L	X	X	X	X	High-Z	High-Z	Deselected	Standby
X	X	X	X	H	H	High-Z	High-Z	Deselected	Standby
L	H	H	H	L	X	High-Z	High-Z	Output Disabled	Active
L	H	H	H	X	L	High-Z	High-Z	Output Disabled	Active
L	H	L	H	L	H	D_{out}	High-Z	Lower Byte Read	Active
L	H	L	H	H	L	High-Z	D_{out}	Upper Byte Read	Active
L	H	L	H	L	L	D_{out}	D_{out}	Word Read	Active
L	H	X	L	L	H	D_{in}	High-Z	Lower Byte Write	Active
L	H	X	L	H	L	High-Z	D_{in}	Upper Byte Write	Active
L	H	X	L	L	L	D_{in}	D_{in}	Word Write	Active

Note: *X means don't care (must be low or high state).*

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Voltage on any pin relative to V_{SS}	V_{IN},V_{OUT}	-0.2 to V_{CC}+0.3V (Max. 3.6V)	V
Voltage on V_{CC} supply relative to V_{SS}	V_{CC}	-0.2 to 3.6V	V
Power Dissipation	P_D	1.0	W
Storage Temperature	T_{STG}	-85 to 150	°C
Operating Temperature	T_A	-40 to 85	°C

Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC Characteristics

Recommended DC Operating Conditions (Note 1)

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	2.7	3.0	3.3	V
Ground	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.2	-	V_{CC}+0.2 (Note 2)	V
Input low voltage	V_{IL}	-0.2 (Note 3)	-	0.6	V

Notes:

1. *T_A = -40 to 85°C, otherwise specified.*
2. *Overshoot: Vcc+2.0V in case of pulse width ≤20ns.*
3. *Undershoot: -2.0V in case of pulse width ≤20ns.*
4. *Overshoot and undershoot are sampled, not 100% tested.*

Capacitance (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C_{IN}	V_{IN}=0V	-	8	pF
Input/Output capacitance	C_{IO}	V_{IO}=0V	-	10	pF

Note: *Capacitance is sampled, not 100% tested*

DC Operating Characteristics

Item	Symbol	Test Conditions		Min	Typ (Note)	Max	Unit
Input leakage current	I_{LI}	V_{IN}=V_{SS} to V_{CC}		-1	-	1	µA
Output leakage current	I_{LO}	CE1#=V_{IH}, CS2=V_{IL} or OE#=V_{IH} or WE#=V_{IL} or LB#=UB#=V_{IH}, V_{IO}=V_{SS} to V_{CC}		-1	-	1	µA
Average operating current	I_{CC1}	Cycle time=1µs, 100% duty, I_{IO}=0mA, CE1#≤0.2V, LB#≤0.2V and/or UB#≤0.2V, CS2≥V_{CC}-0.2V, V_{IN}≤0.2V or V_{IN}≥V_{CC}-0.2V		-	-	5	µA
	I_{CC2}	Cycle time=Min, I_{IO}=0mA, 100% duty, CE1#=V_{IL}, CS2=V_{IH}, LB#=V_{IL} and/or UB#=V_{IL}, V_{IN}=V_{IL} or V_{IH}	70ns	-	-	30	mA
Output low voltage	V_{OL}	I_{OL} = 2.1mA		-	-	0.4	V
Output high voltage	V_{OH}	I_{OH} = -1.0mA		2.4	-	-	V
Standby Current (CMOS)	I_{SB1}	Other input = 0-V_{CC} 1. CE1#≥V_{CC}-0.2V, CS2≥V_{CC}-0.2V (CE1# controlled) or 2. 0V≥CS2≤0.2V (CS2 controlled)		-	-5.0	25	µA

Note: *Typical values are measured at V_{CC}=2.0V, T_A=25°C and not 100% tested.*

AC Characteristics

Read/Write Charcteristics (V_{CC}=2.7-3.3V)

	Parameter List	Symbol	Min	Max	Units
Read	Read cycle time	t_{RC}	70	-	ns
	Address access time	t_{AA}	-	70	ns
	Chip select to output	t_{CO1}, t_{CO2}	-	70	ns
	Output enable to valid output	t_{OE}	-	35	ns
	LB#, UB# valid to data output	t_{BA}	-	70	ns
	Chip select to low-Z output	t_{LZ1}, t_{LZ2}	10	-	ns
	Output enable to low-Z output	t_{OLZ}	5	-	ns
	LB#, UB# enable to low-Z output	t_{BLZ}	10	-	ns
	Output hold from address change	t_{OH}	10	-	ns
	Chip disable to high-Z output	t_{HZ1}, t_{HZ2}	0	25	ns
	OE# disable to high-Z output	t_{OHZ}	0	25	ns
	UB#, LB# disable to high-Z output	t_{BHZ}	0	25	ns
Write	Write cycle time	t_{WC}	70	-	ns
	Chip select to end of write	t_{CW1}, t_{CW2}	60	-	ns
	Address set-up time	t_{AS}	0	-	ns
	Address valid to end of write	t_{AW}	60	-	ns
	Write pulse width	t_{WP}	50	-	ns
	Write recovery time	t_{WR}	0	-	ns
	Write to output high-Z	t_{WHZ}	0	20	ns
	Data to write time overlap	t_{DW}	30	-	ns
	Data hold from write time	t_{DH}	0	-	ns
	End write to output low-Z	t_{OW}	5	-	ns
	LB#, UB# valid to end of write	t_{BW}	60	-	ns

Data Retention Characteristics

Item	Symbol	Test Condition	Min	Typ	Max	Unit
V_{CC} for data retention	V_{DR}	CE1#≥V_{CC}-0.2V (Note 1), V_{IN}≥0V	1.5	-	3.3	V
Data retention current	I_{DR}	V_{CC}=1.5V, CE1#≥V-0.2V (Note 1), V_{IN}≥0V	-	1.0 (Note 2)	15	µA
Data retention set-up time	t_{SDR}	See data retention waveform	0	-	-	ns
Recovery time	t_{RDR}		t_{RC}	-	-	

Notes:

1. *CE1#≤VCC-0.2, CS2≤VCC-0.2V (CE1# controlled) or 0≤CS2-0.2V (CS2 controlled)*
2. *Typical values are measured at T_A=26°C and not 100% tested.*

Timing Diagrams

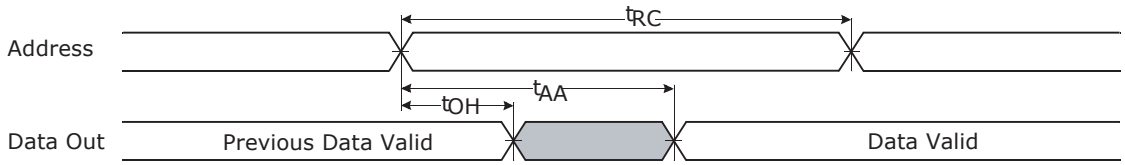
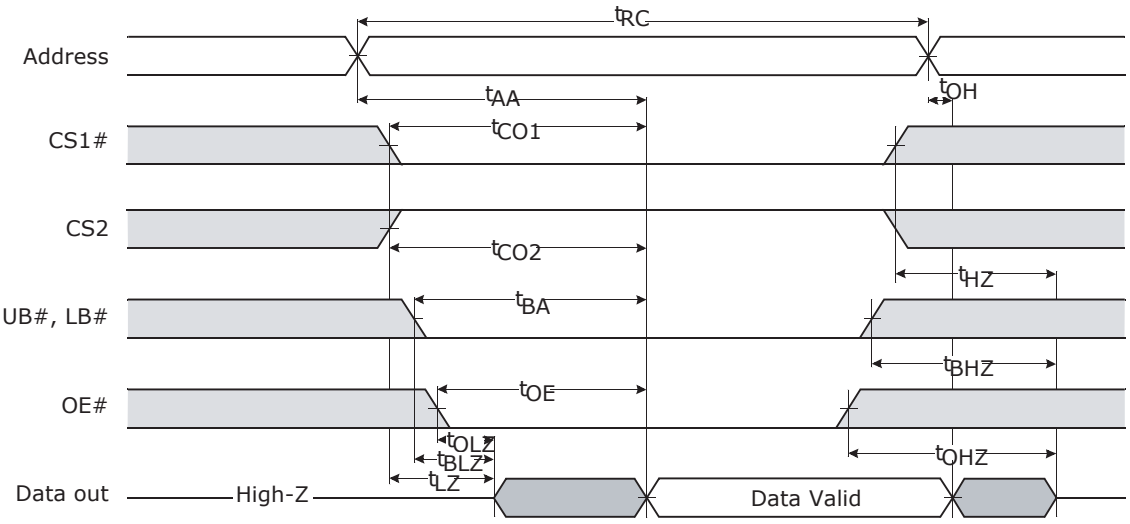


Figure 35. Timing Waveform of Read Cycle(I) (address controlled, CD#I=OE#=V_{IL}, CS2=WE#=V_{IH}, UB# and/or LB#=V_{IL})



Notes:

1. *t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.*
2. *At any given temperature and voltage condition, t_{HZ}(Max.) is less than t_{LZ}(Min.) both for a given device and from device to device interconnection.*

Figure 36. Timing Waveform of Read Cycle(2) (WE#=V_{IH})

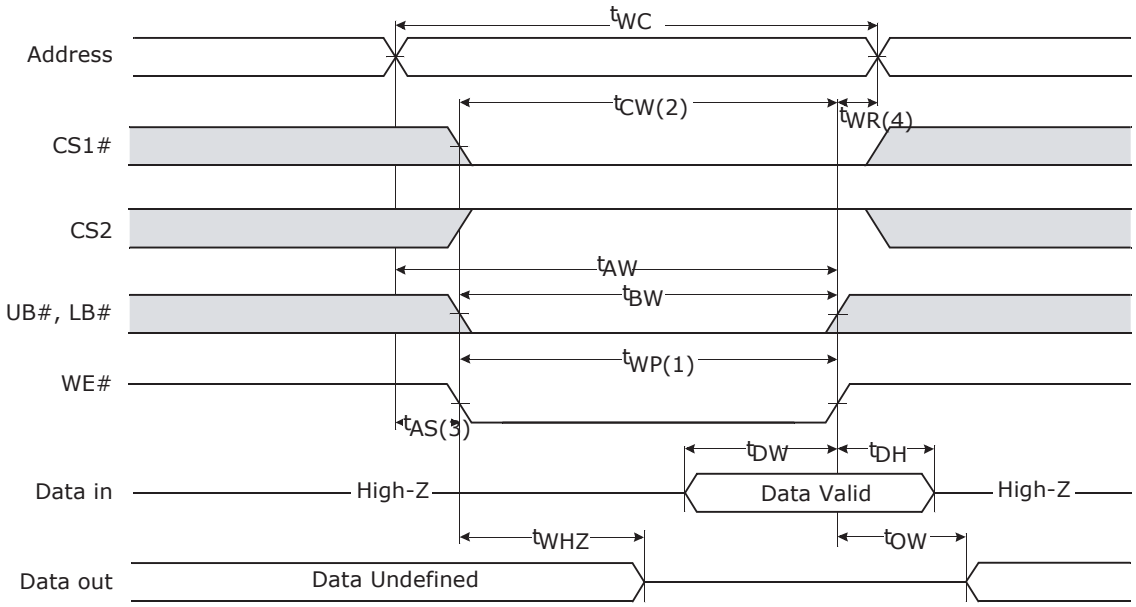


Figure 37. Timing Waveform of Write Cycle(I) (WE# controlled)

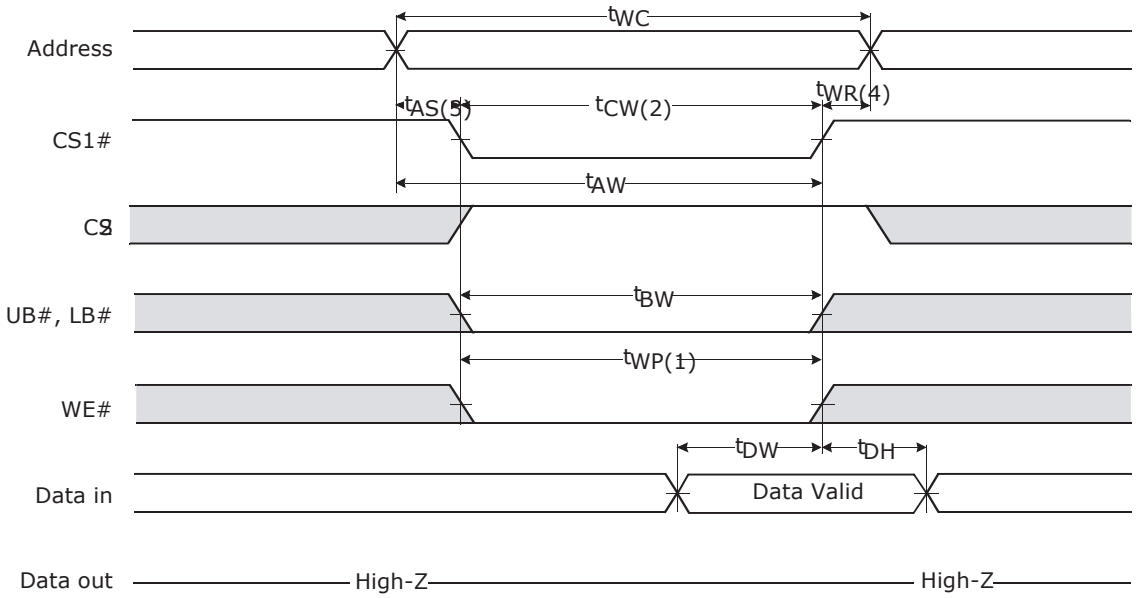
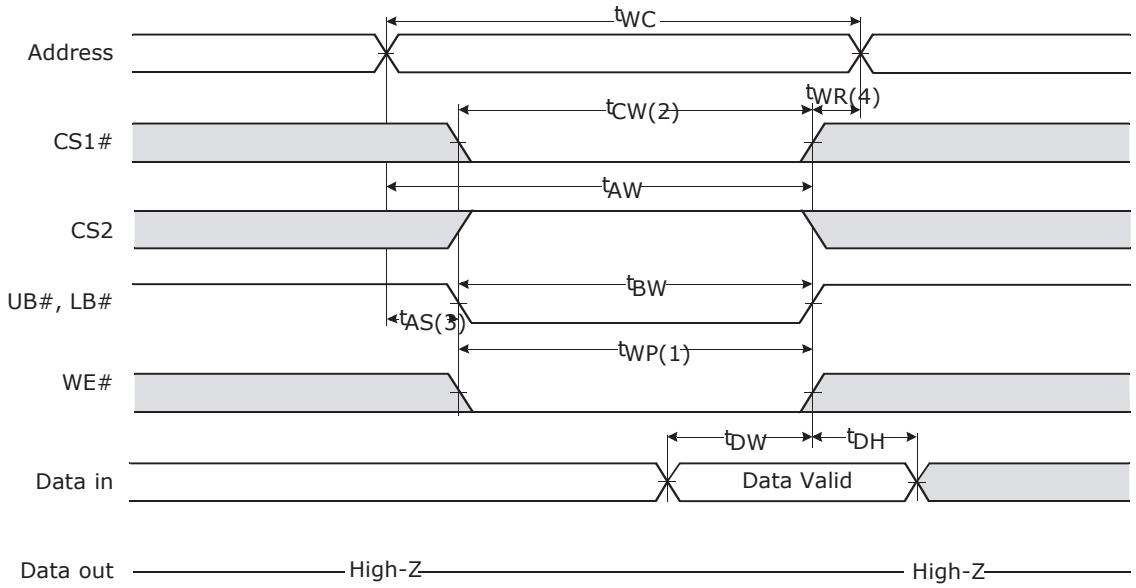


Figure 38. Timing Waveform of Write Cycle(2) (CS# controlled)



Notes:

1. *A write occurs during the overlap(t_{WP}) of low CS1# and low WE#. A write begins when CS1# goes low and WE# goes low with asserting UB# or LB# for single byte operation or simultaneously asserting UB# and LB# for double byte operation. A write ends at the earliest transition when CS1# goes high and WE# goes high. The t_{WP} is measured from the beginning of write to the end of write.*
2. *t_{CW} is measured from the CS1# going low to the end of write.*
3. *t_{AS} is measured from the address valid to the beginning of write.*
4. *t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as CS1# or WE# going high.*

Figure 39. Timing Waveform of Write Cycle(3) (UB#, LB# controlled)

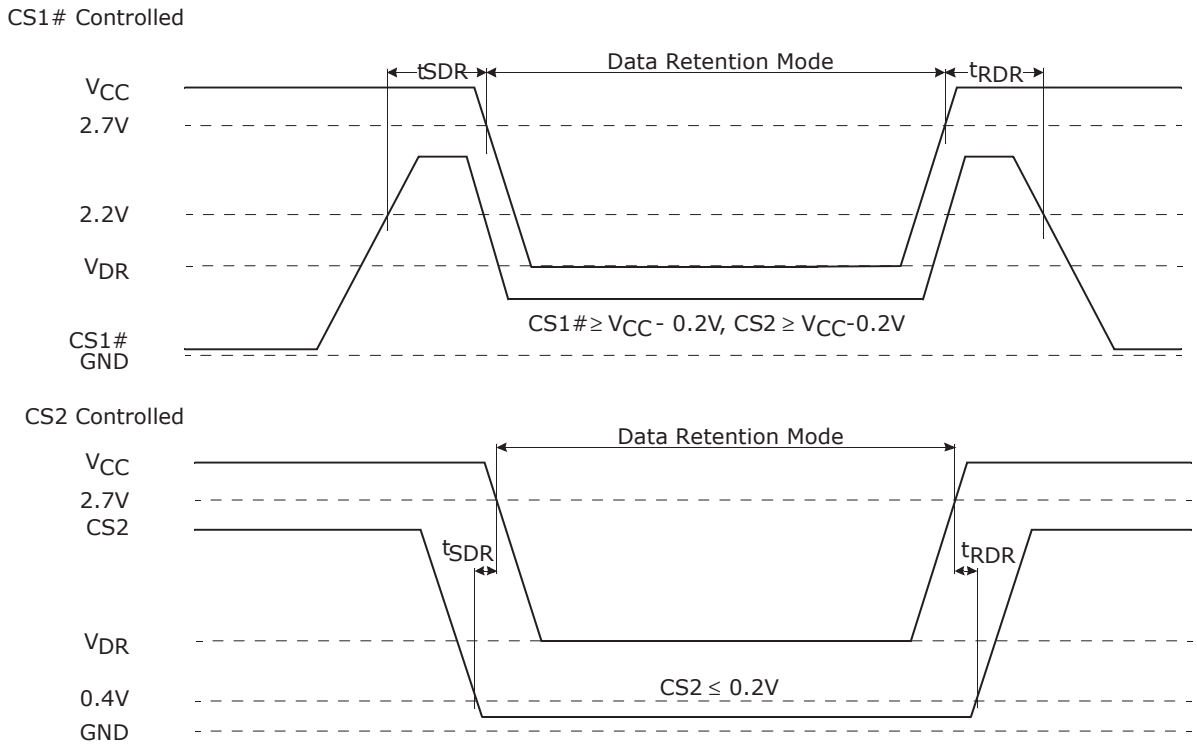


Figure 40. Data Retention Waveform